

SPC564A74B4, SPC564A74L7, SPC564A80B4, SPC564A80L7

32-bit MCU family built on the embedded Power Architecture®

Features

- 150 MHz e200z4 Power Architecture[®] core
 - Variable length instruction encoding (VLE)
 - Superscalar architecture with 2 execution units
 - Up to 2 integer or floating point instructions per cycle
 - Up to 4 multiply and accumulate operations per cycle
- Memory organization
 - 4 MB on-chip flash memory with ECC and Read While Write (RWW)
 - 192 KB on-chip RAM with standby functionality (32 KB) and ECC
 - 8 KB instruction cache (with line locking), configurable as 2- or 4-way
 - 14 + 3 KB eTPU code and data RAM
 - 5 × 4 crossbar switch (XBAR)
 - 24-entry MMU
 - External Bus Interface (EBI) with slave and master port
- Fail Safe Protection
 - 16-entry Memory Protection Unit (MPU)
 - CRC unit with 3 sub-modules
 - Junction temperature sensor
- Interrupts
 - Configurable interrupt controller (with NMI)
 - 64-channel DMA
- Serial channels
 - 3 × eSCI
 - 3 × DSPI (2 of which support downstream Micro Second Channel [MSC])

Table 1. Device summary



- 3 \times FlexCAN with 64 messages each
- 1 × FlexRay module (V2.1) up to 10 Mbit/s with dual or single channel and 128 message objects and ECC
- 1 × eMIOS
- 1 × eTPU2 (second generation eTPU)
- 2 enhanced queued analog-to-digital converters (eQADCs)
- On-chip CAN/SCI/FlexRay Bootstrap loader with Boot Assist Module (BAM)
- Nexus: Class 3+ for core; Class 1 for the eTPU
- JTAG (5-pin)
- Development Trigger Semaphore (DTS)
- Clock generation
 - On-chip 4-40 MHz main oscillator
 - On-chip FMPLL (frequency-modulated phase-locked loop)
- Up to 120 general purpose I/O lines
- Power reduction mode: slow, stop and standby modes
- Flexible supply scheme
 - 5 V single supply with external ballast
 - Multiple external supply: 5 V, 3.3 V and 1.2 V
- Designed for LQFP176, LBGA208, PBGA324 and Known Good Die (KGD)

Memory Flash		Part num	ber	
size	Package LQFP176	Package: LBGA208	Package: PBGA324	KGD
4MB	SPC564A80L7	-	SPC564A80B4	-
3MB	SPC564A74L7	-	SPC564A74B4	-

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1 Introduction

1.1 Document Overview

This document provides electrical specifications, pin assignments, and package diagrams for the SPC564A80 series of microcontroller units (MCUs). For functional characteristics, refer to the *SPC564A80 Microcontroller Reference Manual*.

1.2 Description

The microcontroller's e200z4 host processor core is built on Power Architecture technology and designed specifically for embedded applications. In addition to the Power Architecture technology, this core supports instructions for digital signal processing (DSP).

The SPC564A80 has two levels of memory hierarchy consisting of 8 KB of instruction cache, backed by 192 KB on-chip SRAM and 4 MB of internal flash memory. The SPC564A80 includes an external bus interface, and also a calibration bus that is only accessible when using the calibration tools.

This document describes the features of the SPC564A80 and highlights important electrical and physical characteristics of the device.



1.3 Device comparison

Table 2 summarizes the SPC564A80 and compares it to the SPC563M64.

Table 2.	SPC564A80, SPC563M64 and SPC564A70 comparison
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Feature	SPC564A80	SPC563M64	SPC564A70	
Process		90 nm		
Core	e200z4	e200z3	e200z4	
SIMD		Yes	l	
VLE		Yes		
Cache	8 KB instruction	No	8 KB instruction	
Non-Maskable Interrupt (NMI)	1	NMI & Critical Interrupt		
MMU	24 entry	16 entry	24 entry	
MPU	16 entry	No	16 entry	
Crossbar switch	5 × 4	3 × 4	4 × 4	
Core performance	0–150 MHz	0–80 MHz	0–150 MHz	
Windowing software watchdog		Yes	·	
Core Nexus	Class 3+	Class 2+	Class 3+	
SRAM	192 KB	94 KB	128 KB	
Flash	4 MB	1.5 MB	2 MB	
Flash fetch accelerator	4 × 256-bit	4 × 128-bit		
External bus	16-bit (incl 32-bit muxed)	None		
Calibration bus	16-bit (incl 32-bit muxed)	16-bit	16-bit (incl 32-bit muxed)	
DMA	64 ch.	32 ch.	64 ch.	
DMA Nexus		None		
Serial	3	2	3	
eSCI_A		Yes (MSC Uplink)	·	
eSCI_B		Yes (MSC Uplink)		
eSCI_C	Yes	No	Yes	
CAN	3	2	3	
CAN_A		64 buf		
CAN_B	64 buf	No	64 buf	
CAN_C	64 buf	32 buf	64 buf	
SPI	3	2	3	



Feature	SPC564A80	SPC563M64	SPC564A70	
Micro Second Channel (MSC) bus downlink		Yes		
DSPI_A		No		
DSPI_B		Yes (with LVDS)		
DSPI_C		Yes (with LVDS)		
DSPI_D	Yes	No	Yes	
FlexRay	Yes	No	Yes	
System timers		5 PIT channels 4 STM channels 1 Software Watchdog		
eMIOS	24 ch.	16 ch.	24 ch.	
eTPU		32 ch. eTPU2		
Code memory		14 KB		
Data memory		3 KB		
Interrupt controller	486 ch. ⁽¹⁾	307 ch.	486 ch. ⁽¹⁾	
ADC	40 ch.	34 ch.	40 ch.	
ADC_A		Yes		
ADC_B	Yes			
Temp sensor	Yes			
Variable gain amp.		Yes		
Decimation filter	2	1	2	
Sensor diagnostics		Yes		
CRC	Yes	No	Yes	
FMPLL	Yes			
VRC		Yes		
Supplies	5 V, 3.3 V ⁽²⁾	5 V, 3.3 V ⁽³⁾	5 V, 3.3 V ⁽²⁾	
Low-power modes		Stop Mode Slow Mode		
Packages	LQFP176 ⁽⁴⁾ LBGA208 ⁽⁴⁾ PBGA Known Good Die (KGD) 496-pin CSP ⁽⁵⁾	LQFP100 LQFP144 LQFP176 LBGA208 496-pin CSP ⁽⁵⁾	LQFP176 ⁽⁴⁾ LBGA208 ⁽⁴⁾ PBGAKnown Good Die (KGD) 496-pin CSP ⁽⁵⁾	

Table 2.SPC564A80, SPC563M64 and SPC564A70 comparison (continued)

1. 199 interrupt vectors are reserved.

 $\ \ 2. \ \ 5 \ V \ single \ supply \ only \ for \ LQFP176.$

3. 5 V single supply only for LQFP144 and LQFP100.

4. Pinout compatible with STMicroelectronics' SPC563M64 devices.

5. For ST calibration tool only.



1.4 SPC564A80 feature list

- 150 MHz e200z4 Power Architecture core
 - Variable length instruction encoding (VLE)
 - Superscalar architecture with 2 execution units
 - Up to 2 integer or floating point instructions per cycle
 - Up to 4 multiply and accumulate operations per cycle
- Memory organization
 - 4 MB on-chip flash memory with ECC and Read While Write (RWW)
 - 192 KB on-chip SRAM with standby functionality (32 KB) and ECC
 - 8 KB instruction cache (with line locking), configurable as 2- or 4-way
 - 14 + 3 KB eTPU code and data RAM
 - 5 × 4 crossbar switch (XBAR)
 - 24-entry MMU
 - External Bus Interface (EBI) with slave and master port
- Fail Safe Protection
 - 16-entry Memory Protection Unit (MPU)
 - CRC unit with 3 sub-modules
 - Junction temperature sensor
- Interrupts
 - Configurable interrupt controller (with NMI)
 - 64-channel DMA
- Serial channels
 - 3 × eSCI
 - 3 × DSPI (2 of which support downstream Micro Second Channel [MSC])
 - 3 × FlexCAN with 64 messages each
 - 1 × FlexRay module (V2.1) up to 10 Mbit/s with dual or single channel and 128 message objects and ECC
- 1 × eMIOS: 24 unified channels
- 1 × eTPU2 (second generation eTPU)
 - 32 standard channels
 - 1 × reaction module (6 channels with three outputs per channel)
- 2 enhanced queued analog-to-digital converters (eQADCs)
 - Forty 12-bit input channels (multiplexed on 2 ADCs); expandable to 56 channels with external multiplexers
 - 6 command queues
 - Trigger and DMA support
 - 688 ns minimum conversion time
- On-chip CAN/SCI/FlexRay Bootstrap loader with Boot Assist Module (BAM)
- Nexus
 - Class 3+ for the e200z4 core
 - Class 1 for the eTPU
- JTAG (5-pin)



- Development Trigger Semaphore (DTS)
 - Register of semaphores (32-bits) and an identification register
 - Used as part of a triggered data acquisition protocol
 - EVTO pin is used to communicate to the external tool
- Clock generation
 - On-chip 4–40 MHz main oscillator
 - On-chip FMPLL (frequency-modulated phase-locked loop)
- Up to 120 general purpose I/O lines
 - Individually programmable as input, output or special function
 - Programmable threshold (hysteresis)
- Power reduction mode: slow, stop and stand-by modes
- Flexible supply scheme
 - 5 V single supply with external ballast
 - Multiple external supply: 5 V, 3.3 V and 1.2 V
- Packages
 - LQFP176
 - LBGA208
 - PBGA324
 - Known Good Die (KGD)
 - 496-pin CSP (calibration tool only)





1.5 Feature details

1.5.1 e200z4 core

SPC564A80 devices have a high performance e200z448n3 core processor:

- Dual issue, 32-bit Power Architecture embedded category CPU
- Variable Length Encoding Enhancements
- 8 KB instruction cache: 2- or 4- way set associative instruction cache
- Thirty-two 64-bit general purpose registers (GPRs)
- Memory management unit (MMU) with 24-entry fully-associative translation look-aside buffer (TLB)
- Harvard Architecture: Separate instruction bus and load/store bus
- Vectored interrupt support
- Non-maskable interrupt input
- Critical Interrupt input
- New 'Wait for Interrupt' instruction, to be used with new low power modes
- Reservation instructions for implementing read-modify-write accesses
- Signal processing extension (SPE) APU
- Single Precision Floating point (scalar and vector)
- Nexus Class 3+ debug
- Process ID manipulation for the MMU using an external tool

1.5.2 Crossbar Switch (XBAR)

The XBAR multiport crossbar switch supports simultaneous connections between five master ports and four slave ports. The crossbar supports a 32-bit address bus width and a 64-bit data bus width.

The crossbar allows three concurrent transactions to occur from the master ports to any slave port but each master must access a different slave. If a slave port is simultaneously requested by more than one master port, arbitration logic selects the higher priority master and grants it ownership of the slave port. All other masters requesting that slave port are stalled until the higher priority master completes its transactions. Requesting masters are treated with equal priority and are granted access to a slave port in round-robin fashion, based upon the ID of the last master to be granted access. The crossbar provides the following features:

- 5 master ports
 - CPU instruction bus
 - CPU data bus
 - eDMA
 - FlexRay
 - External Bus Interface



- 4 slave ports
 - Flash
 - Calibration and EBI bus
 - SRAM
 - Peripheral bridge
- 32-bit internal address, 64-bit internal data paths

1.5.3 eDMA

The enhanced direct memory access (eDMA) controller is a second-generation module capable of performing complex data movements via 64 programmable channels, with minimal intervention from the host processor. The hardware micro-architecture includes a DMA engine which performs source and destination address calculations, and the actual data movement operations, along with an SRAM-based memory containing the transfer control descriptors (TCD) for the channels. This implementation is utilized to minimize the overall block size. The eDMA module provides the following features:

- All data movement via dual-address transfers: read from source, write to destination
- Programmable source and destination addresses, transfer size, plus support for enhanced addressing modes
- Transfer control descriptor organized to support two-deep, nested transfer operations
- An inner data transfer loop defined by a "minor" byte transfer count
- An outer data transfer loop defined by a "major" iteration count
- Channel activation via one of three methods:
 - Explicit software initiation
 - Initiation via a channel-to-channel linking mechanism for continuous transfers
 - Peripheral-paced hardware requests (one per channel)
- Support for fixed-priority and round-robin channel arbitration
- Channel completion reported via optional interrupt requests
- One interrupt per channel, optionally asserted at completion of major iteration count
- Error termination interrupts optionally enabled
- Support for scatter/gather DMA processing
- Ability to suspend channel transfers by a higher priority channel

1.5.4 Interrupt controller

The INTC (interrupt controller) provides priority-based preemptive scheduling of interrupt requests, suitable for statically scheduled hard real-time systems.

For high priority interrupt requests, the time from the assertion of the interrupt request from the peripheral to when the processor is executing the interrupt service routine (ISR) has been minimized. The INTC provides a unique vector for each interrupt request source for quick determination of which ISR needs to be executed. It also provides an ample number of priorities so that lower priority ISRs do not delay the execution of higher priority ISRs. To allow the appropriate priorities for each source of interrupt request, the priority of each interrupt request is software configurable.

When multiple tasks share a resource, coherent accesses to that resource need to be supported. The INTC supports the priority ceiling protocol for coherent accesses. By



providing a modifiable priority mask, the priority can be raised temporarily so that all tasks which share the resource cannot preempt each other.

The INTC provides the following features:

- 9-bit vector addresses
- Unique vector for each interrupt request source
- Hardware connection to processor or read from register
- Each interrupt source can assigned a specific priority by software
- Preemptive prioritized interrupt requests to processor
- ISR at a higher priority preempts executing ISRs or tasks at lower priorities
- Automatic pushing or popping of preempted priority to or from a LIFO
- Ability to modify the ISR or task priority to implement the priority ceiling protocol for accessing shared resources
- Low latency—three clocks from receipt of interrupt request from peripheral to interrupt request to processor

This device also includes a non-maskable interrupt (NMI) pin that bypasses the INTC and multiplexing logic.

1.5.5 Memory protection unit (MPU)

The Memory Protection Unit (MPU) provides hardware access control for all memory references generated in a device. Using preprogrammed region descriptors, which define memory spaces and their associated access rights, the MPU concurrently monitors all system bus transactions and evaluates the appropriateness of each transfer. Memory references with sufficient access control rights are allowed to complete; references that are not mapped to any region descriptor or have insufficient rights are terminated with a protection error response.

The MPU has these major features:

- Support for 16 memory region descriptors, each 128 bits in size
 - Specification of start and end addresses provide granularity for region sizes from 32 bytes to 4 GB
 - MPU is invalid at reset, thus no access restrictions are enforced
 - Two types of access control definitions: processor core bus master supports the traditional {read, write, execute} permissions with independent definitions for supervisor and user mode accesses; the remaining non-core bus masters (eDMA, FlexRay, and EBI¹) support {read, write} attributes
 - Automatic hardware maintenance of the region descriptor valid bit removes issues associated with maintaining a coherent image of the descriptor
 - Alternate memory view of the access control word for each descriptor provides an
 efficient mechanism to dynamically alter the access rights of a descriptor only^(a)
 - For overlapping region descriptors, priority is given to permission granting over access denying as this approach provides more flexibility to system software
- Support for two XBAR slave port connections (SRAM and PBRIDGE)
 - For each connected XBAR slave port (SRAM and PBRIDGE), MPU hardware monitors every port access using the pre-programmed memory region descriptors



- An access protection error is detected if a memory reference does not hit in any memory region or the reference is flagged as illegal in all memory regions where it does hit. In the event of an access error, the XBAR reference is terminated with an error response and the MPU inhibits the bus cycle being sent to the targeted slave device
- 64-bit error registers, one for each XBAR slave port, capture the last faulting address, attributes, and detail information

1.5.6 FMPLL

The FMPLL allows the user to generate high speed system clocks from a 4 MHz to 40 MHz crystal oscillator or external clock generator. Further, the FMPLL supports programmable frequency modulation of the system clock. The PLL multiplication factor, output clock divider ratio are all software configurable. The PLL has the following major features:

- Input clock frequency from 4 MHz to 40 MHz
- Reduced frequency divider (RFD) for reduced frequency operation without forcing the PLL to relock
- Three modes of operation
 - Bypass mode with PLL off
 - Bypass mode with PLL running (default mode out of reset)
 - PLL normal mode
- Each of the three modes may be run with a crystal oscillator or an external clock reference
- Programmable frequency modulation
 - Modulation enabled/disabled through software
 - Triangle wave modulation up to 100 kHz modulation frequency
 - Programmable modulation depth (0% to 2% modulation depth)
 - Programmable modulation frequency dependent on reference frequency
- Lock detect circuitry reports when the PLL has achieved frequency lock and continuously monitors lock status to report loss of lock conditions
- Clock Quality Module
 - Detects the quality of the crystal clock and causes interrupt request or system reset if error is detected
 - Detects the quality of the PLL output clock; if error detected, causes system reset or switches system clock to crystal clock and causes interrupt request
- Programmable interrupt request or system reset on loss of lock
- Self-clocked mode (SCM) operation

1.5.7 SIU

The SPC564A80 SIU controls MCU reset configuration, pad configuration, external interrupt, general purpose I/O (GPIO), internal peripheral multiplexing, and the system reset operation. The reset configuration block contains the external pin boot configuration logic. The pad configuration block controls the static electrical characteristics of I/O pins. The



a. EBI not available on all packages and is not available, as a master, for customer.

GPIO block provides uniform and discrete input/output control of the I/O pins of the MCU. The reset controller performs reset monitoring of internal and external reset sources, and drives the RSTOUT pin. Communication between the SIU and the e200z4 CPU core is via the crossbar switch. The SIU provides the following features:

- System configuration
 - MCU reset configuration via external pins
 - Pad configuration control for each pad
 - Pad configuration control for virtual I/O via DSPI serialization
- System reset monitoring and generation
 - Power-on reset support
 - Reset status register provides last reset source to software
 - Glitch detection on reset input
 - Software controlled reset assertion
- External interrupt
 - Rising or falling edge event detection
 - Programmable digital filter for glitch rejection
 - Critical Interrupt request
 - Non-Maskable Interrupt request
- GPIO
 - Centralized control of I/O and bus pins
 - Virtual GPIO via DSPI serialization (requires external deserialization device)
 - Dedicated input and output registers for setting each GPIO and Virtual GPIO pin
- Internal multiplexing
 - Allows serial and parallel chaining of DSPIs
 - Allows flexible selection of eQADC trigger inputs
 - Allows selection of interrupt requests between external pins and DSPI

1.5.8 Flash memory

The SPC564A80 provides up to 4 MB of programmable, non-volatile, flash memory. The non-volatile memory (NVM) can be used to store instructions or data, or both. The flash module includes a Fetch Accelerator that optimizes the performance of the flash array to match the CPU architecture. The flash module interfaces the system bus to a dedicated flash memory array controller. For CPU 'loads', DMA transfers and CPU instruction fetch, it supports a 64-bit data bus width at the system bus port, and 128- and 256-bit read data interfaces to flash memory. The module contains a prefetch controller which prefetches sequential lines of data from the flash array into the buffers. Prefetch buffer hits allow no-wait responses.

The flash memory provides the following features:

- Supports a 64-bit data bus for instruction fetch, CPU loads and DMA access. Byte, halfword, word and doubleword reads are supported. Only aligned word and doubleword writes are supported.
- Fetch Accelerator
 - Architected to optimize the performance of the flash
 - Configurable read buffering and line prefetch support



- Four-entry 256-bit wide line read buffer
- Prefetch controller
- Hardware and software configurable read and write access protections on a per-master basis
- Interface to the flash array controller pipelined with a depth of one, allowing overlapped accesses to proceed in parallel for interleaved or pipelined flash array designs
- Configurable access timing usable in a wide range of system frequencies
- Multiple-mapping support and mapping-based block access timing (0-31 additional cycles) usable for emulation of other memory types
- Software programmable block program/erase restriction control
- Erase of selected block(s)
- Read page size of 128 bits (four words)
- ECC with single-bit correction, double-bit detection
- Program page size of 128 bits (four words) to accelerate programming
- ECC single-bit error corrections are visible to software
- Minimum program size is two consecutive 32-bit words, aligned on a 0-modulo-8 byte address, due to ECC
- Embedded hardware program and erase algorithm
- Erase suspend, program suspend and erase-suspended program
- Shadow information stored in non-volatile shadow block
- Independent program/erase of the shadow block

1.5.9 BAM

The BAM (Boot Assist Module) is a block of read-only memory that is programmed once by ST and is identical for all SPC564A80 MCUs. The BAM program is executed every time the MCU is powered-on or reset in normal mode. The BAM supports different modes of booting. They are:

- Booting from internal flash memory
- Serial boot loading (A program is downloaded into RAM via eSCI or the FlexCAN and then executed)
- Booting from external memory on external bus

The BAM also reads the reset configuration half word (RCHW) from internal flash memory and configures the SPC564A80 hardware accordingly. The BAM provides the following features:

- Sets up MMU to cover all resources and mapping of all physical addresses to logical addresses with minimum address translation
- Sets up MMU to allow user boot code to execute as either Power Architecture embedded category (default) or as VLE code
- Location and detection of user boot code
- Automatic switch to serial boot mode if internal flash is blank or invalid
- Supports user programmable 64-bit password protection for serial boot mode
- Supports serial bootloading via FlexCAN bus and eSCI using standard protocol
- Supports serial bootloading via FlexCAN bus and eSCI with auto baud rate sensing
- Supports serial bootloading of either Power Architecture code (default) or VLE code



- Supports booting from calibration bus interface
- Supports censorship protection for internal flash memory
- Provides an option to enable the core watchdog timer
- Provides an option to disable the system watchdog timer

1.5.10 eMIOS

The eMIOS timer module provides the capability to generate or measure events in hardware.

The eMIOS module features include:

- Twenty-four 24-bit wide channels
- 3 channels' internal timebases can be shared between channels
- 1 Timebase from eTPU2 can be imported and used by the channels
- Global enable feature for all eMIOS and eTPU timebases
- Dedicated pin for each channel (not available on all package types)

Each channel (0–23) supports the following functions:

- General-purpose input/output (GPIO)
- Single-action input capture (SAIC)
- Single-action output compare (SAOC)
- Output pulse-width modulation buffered (OPWMB)
- Input period measurement (IPM)
- Input pulse-width measurement (IPWM)
- Double-action output compare (DAOC)
- Modulus counter buffered (MCB)
- Output pulse width and frequency modulation buffered (OPWFMB)

1.5.11 eTPU2

The eTPU2 is an enhanced co-processor designed for timing control. Operating in parallel with the host CPU, the eTPU2 processes instructions and real-time input events, performs output waveform generation, and accesses shared data without host intervention. Consequently, for each timer event, the host CPU setup and service times are minimized or eliminated. A powerful timer subsystem is formed by combining the eTPU2 with its own instruction and data RAM. High-level assembler/compiler and documentation allows customers to develop their own functions on the eTPU2.

SPC564A80 devices feature the second generation of the eTPU, called eTPU2. Enhancements of the eTPU2 over the standard eTPU include:

- The Timer Counter (TCR1), channel logic and digital filters (both channel and the external timer clock input [TCRCLK]) now have an option to run at full system clock speed or system clock / 2.
- Channels support unordered transitions: transition 2 can now be detected before transition 1. Related to this enhancement, the transition detection latches (TDL1 and TDL2) can now be independently negated by microcode.
- A new User Programmable Channel Mode has been added: the blocking, enabling, service request and capture characteristics of this channel mode can be programmed via microcode.



- Microinstructions now provide an option to issue Interrupt and Data Transfer requests selected by channel. They can also be requested simultaneously at the same instruction.
- Channel Flags 0 and 1 can now be tested for branching, in addition to selecting the entry point.
- Channel digital filters can be bypassed.

The eTPU2 includes these distinctive features:

- 32 channels; each channel associated with one input and one output signal
 - Enhanced input digital filters on the input pins for improved noise immunity
 - Identical, orthogonal channels: each channel can perform any time function. Each time function can be assigned to more than one channel at a given time, so each signal can have any functionality.
 - Each channel has an event mechanism which supports single and double action functionality in various combinations. It includes two 24-bit capture registers, two 24-bit match registers, 24-bit greater-equal and equal-only comparators.
 - Input and output signal states visible from the host
- 2 independent 24-bit time bases for channel synchronization:
 - First time base clocked by system clock with programmable prescale division from 2 to 512 (in steps of 2), or by output of second time base prescaler
 - Second time base counter can work as a continuous angle counter, enabling angle based applications to match angle instead of time
 - Both time bases can be exported to the eMIOS timer module
 - Both time bases visible from the host
- Event-triggered microengine:
 - Fixed-length instruction execution in two-system-clock microcycle
 - 14 KB of code memory (SCM)
 - 3 KB of parameter (data) RAM (SPRAM)
 - Parallel execution of data memory, ALU, channel control and flow control subinstructions in selected combinations
 - 32-bit microengine registers and 24-bit wide ALU, with 1 microcycle addition and subtraction, absolute value, bitwise logical operations on 24-bit, 16-bit, or byte operands, single-bit manipulation, shift operations, sign extension and conditional execution
 - Additional 24-bit Multiply/MAC/Divide unit which supports all signed/unsigned Multiply/MAC combinations, and unsigned 24-bit divide. The MAC/Divide unit works in parallel with the regular microcode commands.
- Resource sharing features support channel use of common channel registers, memory and microengine time:
 - Hardware scheduler works as a "task management" unit, dispatching event service routines by predefined, host-configured priority
 - Automatic channel context switch when a "task switch" occurs, that is, one function thread ends and another begins to service a request from other channel: channelspecific registers, flags and parameter base address are automatically loaded for the next serviced channel



- SPRAM shared between host CPU and eTPU2, supporting communication either between channels and host or inter-channel
- Hardware implementation of four semaphores support coherent parameter sharing between both eTPU engines
- Dual-parameter coherency hardware support allows atomic access to two parameters by host
- Test and development support features:
 - Nexus Class 1 debug, supporting single-step execution, arbitrary microinstruction execution, hardware breakpoints and watchpoints on several conditions
 - Software breakpoints
 - SCM continuous signature-check built-in self test (MISC multiple input signature calculator), runs concurrently with eTPU2 normal operation

1.5.12 Reaction module

The reaction module provides the ability to modulate output signals to manage closed loop control without CPU assistance. It works in conjunction with the eQADC and eTPU2 to increase system performance by removing the CPU from the current control loop.

The reaction module has the following features:

- Six reaction channels
- Each channel output is a bus of three signals, providing ability to control 3 inputs.
- Each channel can implement a peak and hold waveform, making it possible to implement up to six independent peak and hold control channels

Target applications include solenoid control for direct injection systems and valve control in automatic transmissions

1.5.13 eQADC

The enhanced queued analog to digital converter (eQADC) block provides accurate and fast conversions for a wide range of applications. The eQADC provides a parallel interface to two on-chip analog to digital converters (ADC), and a single master to single slave serial interface to an off-chip external device. Both on-chip ADCs have access to all the analog channels.

The eQADC prioritizes and transfers commands from six command conversion command 'queues' to the on-chip ADCs or to the external device. The block can also receive data from the on-chip ADCs or from an off-chip external device into the six result queues, in parallel, independently of the command queues. The six command queues are prioritized with Queue_0 having the highest priority and Queue_5 the lowest. Queue_0 also has the added ability to bypass all buffering and queuing and abort a currently running conversion on either ADC and start a Queue_0 conversion. This means that Queue_0 will always have a deterministic time from trigger to start of conversion, irrespective of what tasks the ADCs were performing when the trigger occurred. The eQADC supports software and external hardware triggers from other blocks to initiate transfers of commands from the queues to the on-chip ADCs or to the external device. It also monitors the fullness of command queues and result queues, and accordingly generates DMA or interrupt requests to control data movement between the queues and the system memory, which is external to the eQADC.

The ADCs also support features designed to allow the direct connection of high impedance acoustic sensors that might be used in a system for detecting engine knock. These features



include differential inputs; integrated variable gain amplifiers for increasing the dynamic range; programmable pull-up and pull-down resistors for biasing and sensor diagnostics.

The eQADC also integrates a programmable decimation filter capable of taking in ADC conversion results at a high rate, passing them through a hardware low pass filter, then down-sampling the output of the filter and feeding the lower sample rate results to the result FIFOs. This allows the ADCs to sample the sensor at a rate high enough to avoid aliasing of out-of-band noise; while providing a reduced sample rate output to minimize the amount DSP processing bandwidth required to fully process the digitized waveform.

The eQADC provides the following features:

- Dual on-chip ADCs
 - 2 × 12-bit ADC resolution
 - Programmable resolution for increased conversion speed (12-bit, 10-bit, 8-bit)
 12-bit conversion time: 938 ns (1 M sample/sec)
 10-bit conversion time: 813 ns (1.2 M sample/second)
 - 8-bit conversion time: 688 ns (1.4 M sample/second)
 - Up to 10-bit accuracy at 500 KSample/s and 8-bit accuracy at 1 MSample/s
 - Differential conversions
 - Single-ended signal range from 0 to 5 V
 - Variable gain amplifiers on differential inputs (\times 1, \times 2, \times 4)
 - Sample times of 2 (default), 8, 64 or 128 ADC clock cycles
 - Provides time stamp information when requested
 - Allows time stamp information relative to eTPU clock sources, such as an angle clock
 - Parallel interface to eQADC CFIFOs and RFIFOs
 - Supports both right-justified unsigned and signed formats for conversion results
- 40 single-ended input channels, expandable to 56 channels with external multiplexers (supports four external 8-to-1 muxes)
- 8 channels can be used as 4 pairs of differential analog input channels
- Differential channels include variable gain amplifier for improved dynamic range
- Differential channels include programmable pull-up and pull-down resistors for biasing and sensor diagnostics (200 kΩ, 100 kΩ, 5 kΩ)
- Additional internal channels for monitoring voltages (such as core voltage, I/O voltage, LVI voltages, etc.) inside the device
- An internal bandgap reference to allow absolute voltage measurements
- Silicon die temperature sensor
 - Provides temperature of silicon as an analog value
 - Read using an internal ADC analog channel
 - May be read with either ADC
- 2 Decimation Filters
 - Programmable decimation factor (1 to 16)
 - Selectable IIR or FIR filter
 - Up to 4th order IIR or 8th order FIR
 - Programmable coefficients



- Saturated or non-saturated modes
- Programmable Rounding (Convergent; Two's Complement; Truncated)
- Prefill mode to precondition the filter before the sample window opens
- Supports Multiple Cascading Decimation Filters to implement more complex filter designs
- Optional Absolute Integrators on the output of Decimation Filters
- Full duplex synchronous serial interface to an external device
 - Free-running clock for use by an external device
 - Supports a 26-bit message length
- Priority based queues
 - Supports six queues with fixed priority. When commands of distinct queues are bound for the same ADC, the higher priority queue is always served first
 - Queue_0 can bypass all prioritization, buffering and abort current conversions to start a Queue_0 conversion a deterministic time after the queue trigger
 - Supports software and hardware trigger modes to arm a particular queue
 - Generates interrupt when command coherency is not achieved
- External hardware triggers
 - Supports rising edge, falling edge, high level and low level triggers
 - Supports configurable digital filter

1.5.14 DSPI

The deserial serial peripheral interface (DSPI) block provides a synchronous serial interface for communication between the SPC564A80 MCU and external devices. The DSPI supports pin count reduction through serialization and deserialization of eTPU and eMIOS channels and memory-mapped registers. The channels and register content are transmitted using a SPI-like protocol. This SPI-like protocol is completely configurable for baud rate, polarity and phase, frame length, chip select assertion, etc. Each bit in the frame may be configured to serialize either eTPU channels, eMIOS channels or GPIO signals. The DSPI can be configured to serialize data to an external device that implements the Microsecond Bus protocol. There are three identical DSPI blocks on the SPC564A80 MCU. The DSPI pins support 5 V logic levels or Low Voltage Differential Signalling (LVDS) to improve high speed operation.

DSPI module features include:

- Selectable LVDS pads working at 40 MHZ for SOUT and SCK pins for DSPI_B and DSPI_C
- 3 sources of serialized data: eTPU_A, eMIOS output channels and memory-mapped register in the DSPI
- 4 destinations for deserialized data: eTPU_A and eMIOS input channels, SIU external Interrupt input request, memory-mapped register in the DSPI
- 32-bit DSI and TSB modes require 32 PCR registers, 32 GPO and GPI registers in the SIU to select either GPIO, eTPU or eMIOS bits for serialization
- The DSPI Module can generate and check parity in a serial frame



1.5.15 eSCI

Three enhanced serial communications interface (eSCI) modules provide asynchronous serial communications with peripheral devices and other MCUs, and include support to interface to Local Interconnect Network (LIN) slave devices. Each eSCI block provides the following features:

- Full-duplex operation
- Standard mark/space non-return-to-zero (NRZ) format
- 13-bit baud rate selection
- Programmable 8-bit or 9-bit, data format
- Programmable 12-bit or 13-bit data format for Timed Serial Bus (TSB) configuration to support the Microsecond bus standard
- Automatic parity generation
- LIN support
 - Autonomous transmission of entire frames
 - Configurable to support all revisions of the LIN standard
 - Automatic parity bit generation
 - Double stop bit after bit error
 - 10- or 13-bit break support
- Separately enabled transmitter and receiver
- Programmable transmitter output parity
- 2 receiver wake-up methods:
 - Idle line wake-up
 - Address mark wake-up
- Interrupt-driven operation with flags
- Receiver framing error detection
- Hardware parity checking
- 1/16 bit-time noise detection
- DMA support for both transmit and receive data
 - Global error bit stored with receive data in system RAM to allow post processing of errors

1.5.16 FlexCAN

The SPC564A80 MCU includes three controller area network (FlexCAN) blocks. The FlexCAN module is a communication controller implementing the CAN protocol according to Bosch Specification version 2.0B. The CAN protocol was designed to be used primarily as a vehicle serial data bus, meeting the specific requirements of this field: real-time processing, reliable operation in the EMI environment of a vehicle, cost-effectiveness and required bandwidth. Each FlexCAN module contains 64 message buffers.



The FlexCAN modules provide the following features:

- Full Implementation of the CAN protocol specification, Version 2.0B
 - Standard data and remote frames
 - Extended data and remote frames
 - Zero to eight bytes data length
 - Programmable bit rate up to 1 Mbit/s
- Content-related addressing
- 64 message buffers of zero to eight bytes data length
- Individual Rx Mask Register per message buffer
- Each message buffer configurable as Rx or Tx, all supporting standard and extended messages
- Includes 1088 bytes of embedded memory for message buffer storage
- Includes 256-byte memory for storing individual Rx mask registers
- Full featured Rx FIFO with storage capacity for six frames and internal pointer handling
- Powerful Rx FIFO ID filtering, capable of matching incoming IDs against 8 extended, 16 standard or 32 partial (8 bits) IDs, with individual masking capability
- Selectable backwards compatibility with previous FlexCAN versions
- Programmable clock source to the CAN Protocol Interface, either system clock or oscillator clock
- Listen only mode capability
- Programmable loop-back mode supporting self-test operation
- 3 programmable Mask Registers
- Programmable transmit-first scheme: lowest ID, lowest buffer number or highest priority
- Time Stamp based on 16-bit free-running timer
- Global network time, synchronized by a specific message
- Maskable interrupts
- Warning interrupts when the Rx and Tx Error Counters reach 96
- Independent of the transmission medium (an external transceiver is assumed)
- Multi-master concept
- High immunity to EMI
- Short latency time due to an arbitration scheme for high-priority messages
- Low power mode, with programmable wake-up on bus activity



1.5.17 FlexRay

The SPC564A80 includes one dual-channel FlexRay module that implements the FlexRay Communications System Protocol Specification, Version 2.1 Rev A. Features include:

- Single channel support
- FlexRay bus data rates of 10 Mbit/s, 8 Mbit/s, 5 Mbit/s, and 2.5 Mbit/s supported
- 128 message buffers, each configurable as:
 - Receive message buffer
 - Single buffered transmit message buffer
 - Double buffered transmit message buffer (combines two single buffered message buffer)
- 2 independent receive FIFOs
 - 1 receive FIFO per channel
 - Up to 255 entries for each FIFO
- ECC support

1.5.18 System timers

The system timers include two distinct types of system timer:

- Periodic interrupts/triggers using the Periodic Interrupt Timer (PIT)
- Operating system task monitors using the System Timer Module (STM)

Periodic interrupt timer (PIT)

The PIT provides five independent timer channels, capable of producing periodic interrupts and periodic triggers. The PIT has no external input or output pins and is intended to provide system 'tick' signals to the operating system, as well as periodic triggers for eQADC queues. Of the five channels in the PIT, four are clocked by the system clock and one is clocked by the crystal clock. This one channel is also referred to as Real-Time Interrupt (RTI) and is used to wake up the device from low power stop mode.

The following features are implemented in the PIT:

- 5 independent timer channels
- Each channel includes 32-bit wide down counter with automatic reload
- 4 channels clocked from system clock
- 1 channel clocked from crystal clock (wake-up timer)
- Wake-up timer remains active when System STOP mode is entered; used to restart system clock after predefined time-out period
- Each channel optionally able to generate an interrupt request or a trigger event (to trigger eQADC queues) when timer reaches zero

System timer module (STM)

The System Timer Module (STM) is designed to implement the software task monitor as defined by AUTOSAR^(b). It consists of a single 32-bit counter, clocked by the system clock,



b. AUTOSAR: AUTomotive Open System ARchitecture (see www.autosar.org)

and four independent timer comparators. These comparators produce a CPU interrupt when the timer exceeds the programmed value.

The following features are implemented in the STM:

- One 32-bit up counter with 8-bit prescaler
- Four 32-bit compare channels
- Independent interrupt source for each channel
- Counter can be stopped in debug mode

1.5.19 Software watchdog timer (SWT)

The Software Watchdog Timer (SWT) is a second watchdog module to complement the standard Power Architecture watchdog integrated in the CPU core. The SWT is a 32-bit modulus counter, clocked by the system clock or the crystal clock, that can provide a system reset or interrupt request when the correct software key is not written within the required time window.

The following features are implemented:

- 32-bit modulus counter
- Clocked by system clock or crystal clock
- Optional programmable watchdog window mode
- Can optionally cause system reset or interrupt request on timeout
- Reset by writing a software key to memory mapped register
- Enabled out of reset
- Configuration is protected by a software key or a write-once register

1.5.20 Cyclic redundancy check (CRC) module

The CRC computing unit is dedicated to the computation of CRC off-loading the CPU. The CRC features:

- Support for CRC-16-CCITT (x25 protocol):
 - $X^{16} + X^{12} + X^5 + 1$
- Support for CRC-32 (Ethernet protocol):
 - $X^{32} + X^{26} + X^{23} + X^{22} + X^{16} + X^{12} + X^{11} + X^{10} + X^8 + X^7 + X^5 + X^4 + X^2 + X + 1$
- Zero wait states for each write/read operations to the CRC_CFG and CRC_INP registers at the maximum frequency

1.5.21 Error correction status module (ECSM)

The ECSM provides a myriad of miscellaneous control functions regarding program-visible information about the platform configuration and revision levels, a reset status register, a software watchdog timer, wakeup control for exiting sleep modes, and information on platform memory errors reported by error-correcting codes and/or generic access error information for certain processor cores.



The Error Correction Status Module supports a number of miscellaneous control functions for the platform. The ECSM includes these features:

- Registers for capturing information on platform memory errors if error-correcting codes (ECC) are implemented
- For test purposes, optional registers to specify the generation of double-bit memory errors are enabled on the SPC564A80.

The sources of the ECC errors are:

- Flash
- SRAM
- Peripheral RAM (FlexRay, CAN, eTPU2 Parameter RAM)

1.5.22 External bus interface (EBI)

The SPC564A80 device features an external bus interface that is available in PBGA324 and calibration packages.

The EBI supports operation at frequencies of system clock /1, /2 and /4, with a maximum frequency support of 80 MHz. Customers running the device at 120 MHz or 132 MHz will use the /2 divider, giving an EBI frequency of 60 MHz or 66 MHz. Customers running the device at 80 MHz will be able to use the /1 divider to have the EBI run at the full 80 MHz frequency.

Features include:

- 1.8 V to 3.3 V ± 10% I/O (1.6 V to 3.6 V)
- Memory controller with support for various memory types
- 16-bit data bus, up to 22-bit address bus
- Pin muxing included to support 32-bit muxed bus
- Selectable drive strength
- Configurable bus speed modes
- Bus monitor
- Configurable wait states

1.5.23 Calibration EBI

The Calibration EBI controls data transfer across the crossbar switch to/from memories or peripherals attached to the calibration tool connector in the calibration address space. The Calibration EBI is only available in the calibration tool.

Features include:

- 1.8 V to 3.3 V ± 10% I/O (1.6 V to 3.6 V)
- Memory controller supports various memory types
- 16-bit data bus, up to 22-bit address bus
- Pin muxing supports 32-bit muxed bus
- Selectable drive strength
- Configurable bus speed modes
- Bus monitor
- Configurable wait states



1.5.24 Power management controller (PMC)

The power management controller contains circuitry to generate the internal 3.3 V supply and to control the regulation of 1.2 V supply with an external NPN ballast transistor. It also contains low voltage inhibit (LVI) and power-on reset (POR) circuits for the 1.2 V supply, the 3.3 V supply, the 3.3 V/5 V supply of the closest I/O segment (VDDEH1) and the 5 V supply of the regulators (VDDREG).

1.5.25 Nexus port controller

The NPC (Nexus Port Controller) block provides real-time Nexus Class3+ development support capabilities for the SPC564A80 Power Architecture-based MCU in compliance with the IEEE-ISTO 5001-2003 and 2010 standards. MDO port widths of 4 pins and 12 pins are available in all packages.

1.5.26 JTAG

The JTAGC (JTAG Controller) block provides the means to test chip functionality and connectivity while remaining transparent to system logic when not in test mode. Testing is performed via a boundary scan technique, as defined in the IEEE 1149.1-2001 standard. All data input to and output from the JTAGC block is communicated in serial format. The JTAGC block is compliant with the IEEE 1149.1-2001 standard and supports the following features:

- IEEE 1149.1-2001 Test Access Port (TAP) interface 4 pins (TDI, TMS, TCK, and TDO)
- A 5-bit instruction register that supports the following IEEE 1149.1-2001 defined instructions:
 - BYPASS, IDCODE, EXTEST, SAMPLE, SAMPLE/PRELOAD, HIGHZ, CLAMP
- A 5-bit instruction register that supports the additional following public instructions:
 - ACCESS_AUX_TAP_NPC
 - ACCESS_AUX_TAP_ONCE
 - ACCESS_AUX_TAP_eTPU
 - ACCESS_CENSOR
- 3 test data registers to support JTAG Boundary Scan mode
 - Bypass register
 - Boundary scan register
 - Device identification register
- A TAP controller state machine that controls the operation of the data registers, instruction register and associated circuitry
- Censorship Inhibit Register
 - 64-bit Censorship password register
 - If the external tool writes a 64-bit password that matches the Serial Boot password stored in the internal flash shadow row, Censorship is disabled until the next system reset.

1.5.27 Development Trigger Semaphore (DTS)

SPC564A80 devices include a system development feature, the Development Trigger Semaphore (DTS) module, that enables software to signal an external tool by driving a persistent (affected only by reset or an external tool) signal on an external device pin. There



is a variety of ways this module can be used, including as a component of an external realtime data acquisition system

1.6 SPC564A80 series architecture

1.6.1 Block diagram

Figure 1 shows a top-level block diagram of the SPC564A80 series.









1.6.2 Block summary

Table 3 summarizes the functions of the blocks present on the SPC564A80 series microcontrollers.

Table 3.	SPC564A80 series block summary	
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Block	Function
Boot assist module (BAM)	Block of read-only memory containing executable code that searches for user-supplied boot code and, if none is found, executes the BAM boot code resident in device ROM.
Calibration Bus interface	Transfers data across the crossbar switch to/from peripherals attached to the calibration tool connector.
Controller area network (FlexCAN)	Supports the standard CAN communications protocol.
Crossbar switch (XBAR)	Internal busmaster.
Cyclic redundancy check (CRC)	CRC checksum generator.
Deserial serial peripheral interface (DSPI)	Provides a synchronous serial interface for communication with external devices.
e200z4 core	Executes programs and interrupt handlers.
Enhanced direct memory access (eDMA)	Performs complex data movements with minimal intervention from the core.
Enhanced modular input-output system (eMIOS)	Provides the functionality to generate or measure events.
Enhanced queued analog-to-digital converter (eQADC)	Provides accurate and fast conversions for a wide range of applications.
Enhanced serial communication interface (eSCI)	Provides asynchronous serial communication capability with peripheral devices and other microcontroller units.
Enhanced time processor unit (eTPU2)	Second-generation co-processor processes real-time input events, performs output waveform generation, and accesses shared data without host intervention.
Error Correction Status Module (ECSM)	The Error Correction Status Module supports a number of miscellaneous control functions for the platform, and includes registers for capturing information on platform memory errors if error-correcting codes (ECC) are implemented
External bus interface (EBI)	Enables expansion of internal bus to enable connection of external memory or peripherals.
Flash memory	Provides storage for program code, constants, and variables.
FlexRay	Provides high-speed distributed control for advanced automotive applications.
Interrupt controller (INTC)	Provides priority-based preemptive scheduling of interrupt requests.
JTAG controller	Provides the means to test chip functionality and connectivity while remaining transparent to system logic when not in test mode.
Memory protection unit (MPU)	Provides hardware access control for all memory references generated.
Nexus port controller (NPC)	Provides real-time development support capabilities in compliance with the IEEE-ISTO 5001-2003 standard.



Block	Function						
Reaction Module (REACM)	Works in conjunction with the eQADC and eTPU2 to increase system performance by removing the CPU from the current control loop.						
System Integration Unit (SIU)	Controls MCU reset configuration, pad configuration, external interrupt, general purpose I/O (GPIO), internal peripheral multiplexing, and the system reset operation.						
Static random-access memory (SRAM)	Provides storage for program code, constants, and variables.						
System timers	Includes periodic interrupt timer with real-time interrupt; output compare timer and system watchdog timer.						
Temperature sensor	Provides the temperature of the device as an analog value.						



2 Pinout and signal description

This section contains the pinouts for all production packages for the SPC564A80 family of devices.

Caution: Any pins labeled "NC" are to be left unconnected. Any connection to an external circuit or voltage may cause unpredictable device behavior or damage.



2.1 LQFP176 pinout



Note: Pin 96 (VSS) should be tied low.

Figure 2. 176-pin LQFP pinout (top view)



SPC564A74L7, SPC564A80B4, SPC564A80L7

N

LBGA208 ballmap

		Figur	e3. 2	208-pin L	.BGA pa	ackage l	ballmap	(viewed	from abo	ove)						
	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16
4	VSS	AN9	AN11	VDDA1	VSSA1	AN1	AN5	VRH	VRL	AN27	VSSA0	AN12-SDS	MDO2	MDO0	VRC33	VSS
З	VDD	VSS	AN8	AN21	AN0	AN4	REFBYPC	AN22	AN25	AN28	VDDA0	AN13-SDO	MDO3	MDO1	VSS	VDD
5	VSTBY	VDD	VSS	AN17	AN34	AN16	AN3	AN7	AN23	AN32	AN33	AN14-SDI	AN15-FCK	VSS	MSEO0	тск
)	VRC33	AN39	VDD	VSS	AN18	AN2	AN6	AN24	AN30	AN31	AN35	VDDEH7	VSS	TMS	EVTO	NC
=	ETPUA30	ETPUA31	AN37	VDD		1	1	1	1	1	1	1	NC	TDI	EVTI	MSEO1
F	ETPUA28	ETPUA29	ETPUA26	AN36									VDDEH6AB	TDO	МСКО	JCOMP
G	ETPUA24	ETPUA27	ETPUA25	ETPUA21			VSS	VSS	VSS	VSS			DSPI_B_ SOUT	DSPI_B_ PCS3	DSPI_B_ SIN	DSPI_B_ PCS0
H	ETPUA23	ETPUA22	ETPUA17	ETPUA18			VSS	VSS	VSS	VSS			GPIO99	DSPI_B_ PCS4	DSPI_B_ PCS2	DSPI_B_ PCS1
J	ETPUA20	ETPUA19	ETPUA14	ETPUA13			VSS	VSS	VSS	VSS			DSPI_B_ PCS5	SCI_A_TX	GPIO98	DSPI_B_ SCK
<	ETPUA16	ETPUA15	ETPUA7	VDDEH1AB			VSS	VSS	VSS	VSS			CAN_C_TX	SCI_A_R X	RSTOUT	VDDREG
L	ETPUA12	ETPUA11	ETPUA6	TCRCLKA							1		SCI_B_TX	CAN_C_ RX	WKPCFG	RESET
N	ETPUA10	ETPUA9	ETPUA1	ETPUA5									SCI_B_RX	PLLREF	BOOTCFG1	VSS
N	ETPUA8	ETPUA4	ETPUA0	VSS	VDD	VRC33	EMIOS2	EMIOS10	VDDEH4AB	EMIOS12	MDO7_ ETPUA19_ O	VRC33	VSS ⁽¹⁾	VRCCTL	NC	EXTAL
Ρ	ETPUA3	ETPUA2	VSS	VDD	GPIO207	NC	EMIOS6	EMIOS8	MDO11_ ETPUA29_ O	MDO4_ ETPUA2_O	MDO8_ ETPUA21_ O	CAN_A_TX	VDD	VSS	NC	XTAL
R	NC	VSS	VDD	GPIO206	EMIOS4	EMIOS3	EMIOS9	EMIOS11	EMIOS14	MDO10_ ETPUA27_ O	EMIOS23	CAN_A_RX	CAN_B_RX	VDD	VSS	VDDPLL
Г	VSS	VDD	NC	EMIOS0	EMIOS1	GPIO219	MDO9_ ETPUA25_ O	EMIOS13	EMIOS15	MDO5_ ETPUA4_O	MDO6_ ETPUA13_ O	CAN_B_TX	VDDE5	ENGCLK	VDD	VSS
	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16

1. This pin (N13) should be tied low.

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2.3

PBGA324 ballmap

	1	2	3	4	5	6	7	8	9	10	11
А	VSS	VDD	VSTBY	AN37	AN11	VDDA0	VSSA0	AN1	AN5	VRH	VRL
в	VRC33	VSS	VDD	AN36	AN39	AN19	AN16	ANO	AN4	REFBYPC	AN23
с	ETPUA30	ETPUA31	VSS	VDD	AN38	AN17	AN20	AN21	AN3	AN7	AN22
D	ETPUA28	ETPUA29	ETPUA26	VSS	VDD	AN8 ANW	AN9	AN10 ANY	AN18	AN2	AN6
Е	ETPUA24	ETPUA27	ETPUA25	ETPUA21			·	·			
F	ETPUA23	ETPUA22	ETPUA17	ETPUA18							
G	ETPUA20	ETPUA19	ETPUA14	ETPUA13							
н	ETPUA16	ETPUA15	ETPUA10	VDDEH1AB							
J	ETPUA12	ETPUA11	ETPUA6	ETPUA9					VSS	VSS	VSS
к	ETPUA8	ETPUA7	ETPUA2	ETPUA5					VSS	VSS	VSS
L	ETPUA4	ETPUA3	ETPUA0	ETPUA1					VSS	VSS	VSS

Figure 4. 324-pin PBGA package ballmap (northwest, viewed from above)

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Pinout and signal description

.

м	BDIP	TCRCLKA	CS1	CS0					VDDE2	VDDE2	VSS
N	CS3	CS2	WE1	WE0					VSS	VSS	VDDE2
Р	ADDR16	ADDR17	RD_WR	VRC33					VSS	VSS	VDDE2
R	ADDR18	ADDR19	VDDE-EH	ТА							
т	ADDR20	ADDR21	ADDR12	TS							
U	ADDR22	ADDR23	ADDR13	ADDR14							
v	ADDR24	ADDR25	ADDR15	ADDR31							
w	ADDR26	VDDE-EH	ADDR30	VSS	VDD	VDDE2	VRC33	VDDE2	DATA11	DATA12	DATA14
Y	ADDR28	ADDR27	VSS	VDD	VDDE2	DATA8	DATA9	DATA10	GPIO207	DATA13	DATA15
AA	ADDR29	VSS	VDD	VDDE2	DATA1	VDDE2	GPIO206	DATA5	DATA7	VDDE2	EMIOS3
AB	VSS	VDD	VDDE2	DATA0	DATA2	DATA3	DATA4	DATA6	OE	EMIOS0	EMIOS1
	1	2	3	4	5	6	7	8	9	10	11

Figure 5. 324-pin PBGA package ballmap (southwest, viewed from above)

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SPC564A74L7, SPC564A80B4, SPC564A80L7

Pinout and signal description

	22	21	20	19	18	17	16	15	14	13	12
A	VSS	VRC33	VDD	MDO8_ ETPUA21_O	MDO10_ ETPUA27_O	MDO11_ ETPUA29_O	AN12_ SDS	VSSA1	AN35	AN28	AN27
В	NIC ^{(1),(2)}	VSS	MDO0	MDO4_ ETPUA2_O	MDO7_ ETPUA19_O	MDO9_ ETPUA25_O	AN13_ SDO	VSSA1	AN32	AN31	AN26
С	VDD	NIC ^{(1),(2)}	VSS	MDO1	MDO2	MDO5_ ETPUA4_O	AN14_ SDI	VDDA1	AN33	AN30	AN25
D	TDI	тск	NIC ^{(1),(2)}	VSS	MDO3	MDO6_ ETPUA13_O	AN15_ FCK	VDDEH7	AN34	AN29	AN24
E	NIC ⁽¹⁾	TDO	TMS	NIC ^{(1),(2)}							
F	EVTO	EVTI	JCOMP	NIC ^{(1),(2)}							
G	MSEO1	MSEO0	МСКО	RDY							
н	DSPI_B_ SIN	GPIO204	GPIO203	VDDEH6AB							
J	DSPI_B_ PCS1	DSPI_B_ PCS0	DSPI_B_ PCS3	DSPI_B_ SOUT					NIC ^{(1),(2)}	VSS	VSS
к	DSPI_B_ PCS2	DSPI_B_ SCK	DSPI_B_ PCS4	GPIO99					VSS	VSS	VSS
L	DSPI_A_ SCK	DSPI_A_ SIN	DSPI_A_ SOUT	DSPI_B_ PCS5					VSS	VSS	VSS

1. Pins marked "NIC" have no internal connection.

2. Balls B22, C21, D20, E19, F19 and J14 are shorted together inside the package.

Figure 6. 324-pin PBGA package ballmap (northeast, viewed from above)

Pinout and signal description



	VSS	VSS	VSS					DSPI_A_ PCS1	DSPI_A_ PCS0	GPIO98	VDDREG	м
	VSS	VSS	VSS					DSPI_A_ PCS4	SCI_A_TX	DSPI_A_ PCS5	NIC ⁽¹⁾	N
	VSS	VSS	VSS					CAN_C_TX	SCI_A_RX	RSTOUT	RSTCFG	Р
	<u> </u>	1	1					WKPCFG	CAN_C_RX	SCI_B_TX	RESET	R
								SCI_B_RX	BOOTCFG1	VSS ⁽²⁾	VSS	т
								VDDEH6AB	PLLCFG1	BOOTCFG0	EXTAL	U
								VDD	VRCCTL	PLLREF	XTAL	v
	EMIOS2	EMIOS8	VDDEH4AB	EMIOS12	EMIOS21	VDDE5	SCI_C_TX	VSS	VDD	NIC ⁽¹⁾	VDDPLL	w
Doc	EMIOS6	EMIOS10	EMIOS15	EMIOS17	EMIOS22	CAN_A_TX	VDDE5	SCI_C_RX	VSS	VDD	VRC33	Y
Ð	EMIOS5	EMIOS9	EMIOS13	EMIOS16	EMIOS19	EMIOS23	CAN_A_RX	VDDE5	CLKOUT	VSS	VDD	AA
15399	EMIOS4	EMIOS7	EMIOS11	EMIOS14	EMIOS18	EMIOS20	CAN_B_TX	CAN_B_RX	VDDE5	ENGCLK	VSS	AB
9 Rev	12	13	14	15	16	17	18	19	20	21	22	

1. Pins marked "NIC" have no internal connection.

2. This pin (T21) should be tied low.

Figure 7. 324-pin PBGA package ballmap (southeast, viewed from above)

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2.4 Signal summary

 Table 4.
 SPC564A80 signal properties

		Р	PCR		I/O		Sta	tus ⁽⁷⁾		Packag	e pin #
Name	Function ⁽¹⁾	A G ⁽²⁾	PA Field (3)	PCR (4)	і/О Туре	Voltage ⁽⁵⁾ / Pad Type ⁽⁶⁾	During Reset	After Reset	176	208	324
					GI	910					
EMIOS14 ⁽⁸⁾ GPIO[203]	eMIOS channel GPIO	P G	01 00	203	0 I/O	VDDEH7 Slow	— / Up	— / Up	_	_	H20
EMIOS15 ⁽⁸⁾ GPIO[204]	eMIOS channel GPIO	P G	01 00	204	0 I/O	VDDEH7 Slow	— / Up	—/ Up	_	_	H21
GPIO[206] ETRIG0	GPIO / eQADC Trigger Input	G	00	206	I/O ⁽⁹⁾	VDDEH7 Slow ⁽¹⁰⁾	— / Up	— / Up	143	R4	AA7
GPIO[207] ETRIG1	GPIO / eQADC Trigger Input	G	00	207	I/O ⁽⁹⁾	VDDEH7 Slow	— / Up	— / Up	144	P5	Y9
GPIO[219]	GPIO	G	_	219 (11)	I/O	VDDEH7 MultiV ⁽¹²⁾	— / Up	— / Up	122	Т6	_
				Re	eset / Co	nfiguration					
RESET	External Reset Input	Р	_	_	I	VDDEH6 Slow	RESET / Up	RESET / Up	97	L16	R22
RSTOUT	External Reset Output	Р	01	230	0	VDDEH6 Slow	RSTOUT / Down	RSTOUT / Down	102	K15	P21
PLLREF IRQ[4] ETRIG2 GPIO[208]	FMPLL Mode Selection External Interrupt Request eQADC Trigger Input GPIO	P A1 A2 G	001 010 100 000	208	 /O	VDDEH6 Slow	— / Up	PLLREF / Up	83	M14	V21
PLLCFG1 ⁽¹³⁾ IRQ[5] DSPI_D_SOUT GPIO[209]	— External interrupt request DSPI D data output GPIO	— A1 A2 G	— 010 100 000	209	— I 0 I/O	VDDEH6 Medium	— / Up	— / Up	_	_	U20
RSTCFG GPIO[210]	RSTCFG GPIO	P G	01 00	210	I I/О	VDDEH6 Slow	— / Down		_	—	P22

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		Р	PCR		I/O		Sta	tus ⁽⁷⁾		Packag	e pin #
Name	Function ⁽¹⁾	A G ⁽²⁾	PA Field (3)	PCR (4)	Туре	Voltage ⁽⁵⁾ / Pad Type ⁽⁶⁾	During Reset	After Reset	176	208	324
BOOTCFG[0] IRQ[2] GPIO[211]	Boot Config. Input External Interrupt Request GPIO	P A1 G	01 10 00	211	 /O	VDDEH6 Slow	— / Down	BOOTCFG[0] / Down	_	-	U21
BOOTCFG[1] IRQ[3] ETRIG3 GPIO[212]	Boot Config. Input External Interrupt Request eQADC Trigger Input GPIO	P A1 A2 G	001 010 100 000	212	 /O	VDDEH6 Slow	— / Down	BOOTCFG[1] / Down	85	M15	Т20
WKPCFG NMI DSPI_B_SOUT GPIO[213]	Weak Pull Config. Input Non-Maskable Interrupt DSPI D data output GPIO	P A1 A2 G	001 010 100 000	213	 /O	VDDEH6 Medium	— / Up	WKPCFG / Up	86	L15	R19
				Ex	ternal B	us Interface			•		
CS[0] ADDR[8] GPIO[0]	External chip selects External address bus GPIO	P A1 G	01 10 00	0	0 I/O I/O	VDDE2 Fast	— / Up	— / Up	_	_	M4
CS[1] ADDR9 GPIO[1]	External chip selects External address bus GPIO	P A1 G	01 10 00	1	0 I/O I/O	VDDE2 Fast	— / Up	— / Up	_	_	МЗ
CS[2] ADDR10 WE[2]/BE[2] CAL_WE[2]/BE[2] GPIO[2]	External chip selects External address bus Write/byte enable Cal. bus write/byte enable GPIO	P A1 A2 A3 G	0001 0010 0100 1000 0000	2	0 I/O 0 I/O	VDDE2 Fast	— / Up	— / Up	_	_	N2
CS[3] ADDR11 WE[3]/BE[3] CAL_WE[3]/BE[3] GPIO[3]	External chip selects External address bus Write/byte enable Cal bus write/byte enable GPIO	P A1 A2 A3 G	0001 0010 0100 1000 0000	3	0 I/O 0 I/O	VDDE2 Fast	— / Up	— / Up	_	_	N1

		Р	PCR			(5)	Sta	tus ⁽⁷⁾		Packag	e pin #
Name	Function ⁽¹⁾	A G ⁽²⁾	PA Field (3)	PCR (4)	l/O Type	Voltage ⁽⁵⁾ / Pad Type ⁽⁶⁾	During Reset	After Reset	176	208	32
ADDR12 GPIO[8]	External address bus GPIO	P G	01 00	8	I/O I/O	VDDE3 Fast	— / Up	— / Up	_	_	тз
ADDR13 WE[2] GPIO[9]	External address bus Write/byte enable GPIO	P A2 G	001 100 000	9	I/O O I/O	VDDE3 Fast	— / Up	— / Up	_	_	U3
ADDR14 WE[3] GPIO[10]	External address bus Write/byte enables GPIO	P A2 G	001 100 000	10	I/O O I/O	VDDE3 Fast	— / Up	— / Up	_		U4
ADDR15 GPIO[11]	External address bus GPIO	P G	01 00	11	I/O I/O	VDDE3 Fast	— / Up	— / Up	_	_	V3
ADDR16 FR_A_TX DATA16 GPIO[12]	External address bus Flexray TX data channel A External data bus GPIO	P A1 A2 G	001 010 100 000	12	I/O O I/O I/O	VDDE-EH Medium	— / Up	— / Up	_	_	P1
ADDR17 FR_A_TX_EN DATA17 GPIO[13]	External address bus FlexRay ch. A TX data enable External data bus GPIO	P A1 A2 G	001 010 100 000	13	I/O O I/O I/O	VDDE-EH Medium	— / Up	— / Up	_	_	P2
ADDR18 FR_A_RX DATA18 GPIO[14]	External address bus Flexray RX data ch. A External data bus GPIO	P A1 A2 G	001 010 100 000	14	I/O I I/O I/O	VDDE-EH Medium	— / Up	— / Up	_	_	R1
ADDR19 FR_B_TX DATA19 GPIO[15]	External address bus Flexray TX data ch. B External data bus GPIO	P A1 A2 G	001 010 100 000	15	I/O O I/O I/O	VDDE-EH Medium	— / Up	— / Up	_	_	R2
ADDR20 FR_B_TX_EN DATA20	External address bus Flexray TX data enable for ch. B External data bus	P A1 A2	001 010 100	16	I/O O I/O	VDDE-EH Medium	— / Up	— / Up	_	_	T1

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DATA20

GPIO[16]

External data bus

GPIO

A2

G

100

000

I/O

I/O

324

		Р	PCR		1/0	(5)	Sta	tus ⁽⁷⁾		Packag	e pin #
Name	Function ⁽¹⁾	A G ⁽²⁾	PA Field (3)	PCR (4)	l/O Type	Voltage ⁽⁵⁾ / Pad Type ⁽⁶⁾	During Reset	After Reset	176	208	324
ADDR21 FR_B_RX DATA21 GPIO[17]	External address bus Flexray RX data channel B External data bus GPIO	P A1 A2 G	001 010 100 000	17	I/O I I/O I/O	VDDE-EH Medium	— / Up	— / Up	_	_	T2
ADDR22 DATA22 GPIO[18]	External address bus External data bus GPIO	P A2 G	001 100 000	18	I/O I/O I/O	VDDE-EH Medium	— / Up	— / Up	_	_	U1
ADDR23 DATA23 GPIO[19]	External address bus External data bus GPIO	P A2 G	001 100 000	19	1/0 1/0 1/0	VDDE-EH Medium	— / Up	— / Up	_	_	U2
ADDR24 DATA24 GPIO[20]	External address bus External data bus GPIO	P A2 G	001 100 000	20	I/O I/O I/O	VDDE-EH Medium	— / Up	— / Up	_	_	V1
ADDR25 DATA25 GPIO[21]	External address bus External data bus GPIO	P A2 G	001 100 000	21	I/O I/O I/O	VDDE-EH Medium	— / Up	— / Up	_	_	V2
ADDR26 DATA26 GPIO[22]	External address bus External data bus GPIO	P A2 G	001 100 000	22	I/O I/O I/O	VDDE-EH Medium	— / Up	— / Up	_	_	W1
ADDR27 DATA27 GPIO[23]	External address bus External data bus GPIO	P A2 G	001 100 000	23	I/O I/O I/O	VDDE-EH Medium	— / Up	— / Up	_	_	Y2
ADDR28 DATA28 GPIO[24]	External address bus External data bus GPIO	P A2 G	001 100 000	24	I/O I/O I/O	VDDE-EH Medium	— / Up	— / Up	_	_	Y1
ADDR29 DATA29 GPIO[25]	External address bus External data bus GPIO	P A2 G	001 100 000	25	I/O I/O I/O	VDDE-EH Medium	— / Up	— / Up	_	_	AA1

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		Р	PCR		I/O		Sta	tus ⁽⁷⁾		Packag	e pin #
Name	Function ⁽¹⁾	A G ⁽²⁾	PA Field (3)	PCR (4)	Туре	Voltage ⁽⁵⁾ / Pad Type ⁽⁶⁾	During Reset	After Reset	176	208	324
ADDR30 ADDR6 ⁽⁸⁾ DATA30 GPIO[26]	External address bus External address bus External data bus GPIO	P A1 A2 G	001 010 100 000	26	I/O O I/O I/O	VDDE-EH Medium	— / Up	— / Up	_	_	W3
ADDR31 ADDR7 ⁽⁸⁾ DATA31 GPIO[27]	External address bus External address bus External data bus GPIO	P A1 A2 G	001 010 100 000	27	I/O O I/O I/O	VDDE-EH Medium	— / Up	— / Up	_	_	V4
DATA0 ADDR16 GPIO[28]	External data bus External address bus GPIO	P A1 G	001 010 000	28	I/O I/O I/O	VDDE5 Fast	— / Up	— / Up	_	_	AB4
DATA1 ADDR17 GPIO[29]	External data bus External address bus GPIO	P A1 G	001 010 000	29	I/O I/O I/O	VDDE5 Fast	— / Up	— / Up	_	_	AA5
DATA2 ADDR18 GPIO[30]	External data bus External address bus GPIO	P A1 G	001 010 000	30	I/O I/O I/O	VDDE5 Fast	— / Up	— / Up	_	_	AB5
DATA3 ADDR19 GPIO[31]	External data bus External address bus GPIO	P A1 G	001 010 000	31	1/0 1/0 1/0	VDDE5 Fast	— / Up	— / Up	_	_	AB6
DATA4 ADDR20 GPIO[32]	External data bus External address bus GPIO	P A1 G	001 010 000	32	I/O I/O I/O	VDDE5 Fast	— / Up	— / Up	_	_	AB7
DATA5 ADDR21 GPIO[33]	External data bus External address bus GPIO	P A1 G	001 010 000	33	I/O I/O I/O	VDDE5 Fast	— / Up	— / Up	_	_	AA8
DATA6 ADDR22 GPIO[34]	External data bus External address bus GPIO	P A1 G	001 010 000	34	I/O I/O I/O	VDDE5 Fast	— / Up	— / Up	_	_	AB8

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		Р	PCR		I/O	N II (5) <i>i</i>	Sta	tus ⁽⁷⁾		Packag	e pin #
Name	Function ⁽¹⁾	A G ⁽²⁾	PA Field (3)	PCR (4)	Туре	Voltage ⁽⁵⁾ / Pad Type ⁽⁶⁾	During Reset	After Reset	176	208	324
DATA7 ADDR23 GPIO[35]	External data bus External address bus GPIO	P A1 G	001 010 000	35	1/0 1/0 1/0	VDDE5 Fast	— / Up	— / Up	_	_	AA9
DATA8 ADDR24 GPIO[36]	External data bus External address bus GPIO	P A1 G	001 010 000	36	I/O I/O I/O	VDDE5 Fast	— / Up	— / Up	_	_	Y6
DATA9 ADDR25 GPIO[37]	External data bus External address bus GPIO	P A1 G	001 010 000	37	I/O I/O I/O	VDDE5 Fast	— / Up	— / Up	_	_	Y7
DATA10 ADDR26 GPIO[38]	External data bus External address bus GPIO	P A1 G	001 010 000	38	I/O I/O I/O	VDDE5 Fast	— / Up	— / Up	_	_	Y8
DATA11 ADDR27 GPIO[39]	External data bus External address bus GPIO	P A1 G	001 010 000	39	1/0 1/0 1/0	VDDE5 Fast	— / Up	— / Up	_	_	W9
DATA12 ADDR28 GPIO[40]	External data bus External address bus GPIO	P A1 G	001 010 000	40	I/O I/O I/O	VDDE5 Fast	— / Up	— / Up	_	_	W10
DATA13 ADDR29 GPIO[41]	External data bus External address bus GPIO	P A1 G	001 010 000	41	1/0 1/0 1/0	VDDE5 Fast	— / Up	— / Up	_	_	Y10
DATA14 ADDR30 GPIO[42]	External data bus External address bus GPIO	P A1 G	001 010 000	42	I/O I/O I/O	VDDE5 Fast	— / Up	— / Up	_	_	W11
DATA15 ADDR31 GPIO[43]	External data bus External address bus GPIO	P A1 G	001 010 000	43	I/O I/O I/O	VDDE5 Fast	— / Up	— / Up	_	_	Y11
RD_ WR GPIO[62]	External read/write GPIO	P G	01 00	62	I/O I/O	VDDE2 Fast	— / Up	— / Up	—	_	Р3

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Table 4.	SPC564A80 signal properties (continued)

		Р	PCR		I/O		Sta	tus ⁽⁷⁾		Packag	e pin #
Name	Function ⁽¹⁾	A G ⁽²⁾	PA Field (3)	PCR (4)	Туре	Voltage ⁽⁵⁾ / Pad Type ⁽⁶⁾	During Reset	After Reset	176	208	324
BDIP GPIO[63]	External burst data in progress GPIO	P G	01 00	63	0 I/O	VDDE2 Fast	— / Up	— / Up	_		M1
WE[0]/BE[0] GPIO[64]	External write/byte enable GPIO	P G	01 00	64	0 I/O	VDDE2 Fast	— / Up	— / Up	_	_	N4
WE[1]/BE[1] GPIO[65]	External write/byte enable GPIO	P G	01 00	65	0 I/O	VDDE2 Fast	— / Up	— / Up	_	_	N3
OE GPIO[68]	External output enable GPIO	P G	01 00	68	0 I/O	VDDE2 Fast	— / Up	— / Up	_		AB9
TS ALE GPIO[69]	External transfer start Address latch enable GPIO[69]	P A1 G	001 010 000	69	I/O O I/O	VDDE2 Fast	— / Up	— / Up		_	Τ4
TA TS ⁽⁸⁾ GPIO[70]	External transfer acknowledge External transfer start GPIO	P A1 G	001 010 000	70	I/O O I/O	VDDE2 Fast	— / Up	— / Up	_	_	R4
					Calibra	tion Bus					
CAL_CS0	Calibration chip select	Ρ	01	336	ο	VDDE12 Fast		<i>_/_</i>	_	_	_
CAL_ <u>CS2</u> CAL_ADDR[10] CAL_ <u>WE</u> [2]/ <u>BE</u> [2]	Calibration chip select Calibration address bus Calibration write/byte enable	P A A2	001 010 100	338	0 I/O 0	VDDE12 Fast		<i>_/_</i>	_	_	_
CAL_ CS3 CAL_ADDR[11] CAL_ <u>WE[</u> 3]/ <u>BE</u> [3]	Calibration chip select Calibration address bus Calibration write/byte enable	P A A2	001 010 100	339	0 I/O 0	VDDE12 Fast		_/_	_	_	_
CAL_ADDR[12] CAL_WE[2]/BE[2]	Calibration address bus Calibration write/byte enable	P A	01 10	340	I/O O	VDDE12 Fast		<i>_/_</i>	_	_	_
CAL_ADDR[13] CAL_ <u>WE[</u> 3]/ <u>BE[</u> 3]	Calibration address bus Calibration write/byte enable	P A	01 10	340	I/O O	VDDE12 Fast		<i>_/</i>	_		-

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			Р	PCR		1/0	(5)	Sta	tus ⁽⁷⁾
	Name	Function ⁽¹⁾	A G ⁽²⁾	PA Field (3)	PCR (4)	l/O Type	Voltage ⁽⁵⁾ / Pad Type ⁽⁶⁾	During Reset	
	CAL_ADDR[14] CAL_DATA[31]	Calibration address bus Calibration data bus	P A	01 10	340	I/O I/O	VDDE12 Fast		
	CAL_ADDR[15] CAL_ALE	Calibration address bus Calibration address latch enable	P A1	01 10	340	I/O O	VDDE12 Fast		
	CAL_ADDR[16] CAL_DATA[16]	Calibration address bus Calibration data bus	P A	01 10	345	I/O I/O	VDDE12 Fast		
	CAL_ADDR[17] CAL_DATA[17]	Calibration address bus Calibration data bus	P A	01 10	345	I/O I/O	VDDE12 Fast		
Doc	CAL_ADDR[18] CAL_DATA[18]	Calibration address bus Calibration data bus	P A	01 10	345	I/O I/O	VDDE12 Fast		
c ID 15	CAL_ADDR[19] CAL_DATA[19]	Calibration address bus Calibration data bus	P A	01 10	345	I/O I/O	VDDE12 Fast		

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Table 4. SPC564A80 signal properties (continued)

Calibration address bus

Calibration data bus

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CAL_ADDR[20]

CAL_DATA[20]

CAL_ADDR[21]

CAL_DATA[21]

CAL_ADDR[22]

CAL_DATA[22]

CAL_ADDR[23]

CAL_DATA[23]

CAL_ADDR[24]

CAL_DATA[24]

CAL_ADDR[25]

CAL_DATA[25]

CAL_ADDR[26]

CAL_DATA[26]

CAL_ADDR[27]

CAL_DATA[27]

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Package pin #

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		Р	PCR PA	PCR	I/O		Sta	tus ⁽⁷⁾		Packag	e pin #
Name	Function ⁽¹⁾	A G ⁽²⁾	FA Field (3)		Туре	Voltage ⁽⁵⁾ / Pad Type ⁽⁶⁾	During Reset	After Reset	176	208	324
CAL_ADDR[28] CAL_DATA[28]	Calibration address bus Calibration data bus	P A	01 10	345	I/O I/O	VDDE12 Fast		<i>— / —</i>	_	_	
CAL_ADDR[29] CAL_DATA[29]	Calibration address bus Calibration data bus	P A	01 10	345	I/O I/O	VDDE12 Fast		<i>—/—</i>	_	_	_
CAL_ADDR[30] CAL_DATA[30]	Calibration address bus Calibration data bus	P A	01 10	345	I/O I/O	VDDE12 Fast		<i>—/—</i>	_	_	
CAL_DATA[0]	Calibration data bus	Р	01	341	I/O	VDDE12 Fast	— / Up	— / Up	_	_	_
CAL_DATA[1]	Calibration data bus	Р	01	341	I/O	VDDE12 Fast	— / Up	— / Up	_	_	_
CAL_DATA[2]	Calibration data bus	Р	01	341	I/O	VDDE12 Fast	— / Up	— / Up	_	_	_
CAL_DATA[3]	Calibration data bus	Р	01	341	I/O	VDDE12 Fast	— / Up	— / Up	_	_	_
CAL_DATA[4]	Calibration data bus	Р	01	341	I/O	VDDE12 Fast	— / Up	— / Up	_	_	_
CAL_DATA[5]	Calibration data bus	Р	01	341	I/O	VDDE12 Fast	— / Up	— / Up	_	_	_
CAL_DATA[6]	Calibration data bus	Р	01	341	I/O	VDDE12 Fast	— / Up	— / Up	_	_	
CAL_DATA[7]	Calibration data bus	Р	01	341	I/O	VDDE12 Fast	— / Up	— / Up	_	_	_
CAL_DATA[8]	Calibration data bus	Р	01	341	I/O	VDDE12 Fast	— / Up	— / Up	_		
CAL_DATA[9]	Calibration data bus	Р	01	341	I/O	VDDE12 Fast	— / Up	— / Up	_	_	_
CAL_DATA[10]	Calibration data bus	Р	01	341	I/O	VDDE12 Fast	— / Up	— / Up		_	_

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Table 4.	SPC564A80 signal properties (continued)
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		Р	PCR		I/O		Sta	ntus ⁽⁷⁾	Package pin #		
Name	Function ⁽¹⁾	A G ⁽²⁾	PA Field (3)	PCR (4)	і/О Туре	Voltage ⁽⁵⁾ / Pad Type ⁽⁶⁾	During Reset	After Reset	176	208	324
CAL_DATA[11]	Calibration data bus	Р	01	341	I/O	VDDE12 Fast	— / Up	— / Up	_	_	_
CAL_DATA[12]	Calibration data bus	Р	01	341	I/O	VDDE12 Fast	— / Up	— / Up	_	_	_
CAL_DATA[13]	Calibration data bus	Р	01	341	I/O	VDDE12 Fast	— / Up	— / Up	_	_	_
CAL_DATA[14]	Calibration data bus	Р	01	341	I/O	VDDE12 Fast	— / Up	— / Up		_	—
CAL_DATA[15]	Calibration data bus	Р	01	341	I/O	VDDE12 Fast	— / Up	— / Up	_	_	_
CAL_RD_WR	Calibration read/write enable	Р	01	342	0	VDDE12 Fast		_/_	_	_	_
CAL_WE[0]/BE[0]	Calibration write/byte enable	Ρ	01	342	0	VDDE12 Fast		_/_		_	—
CAL_WE[1]/BE[1]	Calibration write/byte enable	Р	01	342	0	VDDE12 Fast		_/_	_	_	—
CAL_OE	Calibration output enable	Р	01	342	0	VDDE12 Fast		_/_	_	_	—
CAL_TS CAL_ALE	Calibration transfer start Address Latch Enable	P A	01 10	343	0 0	VDDE12 Fast		_/_	_	_	—
CAL_MDO[4]	Calibration Nexus Message Data Out	Р	01	_	0	VDDE12 Fast	_	CAL_MDO[4]/	_	_	_
CAL_MDO[5]	Calibration Nexus Message Data Out	Р	01	_	0	VDDE12 Fast	_	CAL_MDO[5]/—	_	_	_
CAL_MDO[6]	Calibration Nexus Message Data Out	Р	01	_	0	VDDE12 Fast	—	CAL_MDO[6]/—	_	_	—
CAL_MDO[7]	Calibration Nexus Message Data Out	Р	01	_	ο	VDDE12 Fast	_	CAL_MDO[7]/-	_	_	_

		Р	PCR		I/O		Sta	tus ⁽⁷⁾	Package pin #		
Name	Function ⁽¹⁾	A G ⁽²⁾	PA Field (3)	PCR (4)	Туре	Voltage ⁽⁵⁾ / Pad Type ⁽⁶⁾	During Reset	After Reset	176	208	324
CAL_MDO[8]	Calibration Nexus Message Data Out	Ρ	01	_	0	VDDE12 Fast		CAL_MDO[8]/	_	_	_
CAL_MDO[9]	Calibration Nexus Message Data Out	Р	01	_	0	VDDE12 Fast		CAL_MDO[9] / —	_	_	_
CAL_MDO[10]	Calibration Nexus Message Data Out	Р	01		0	VDDE12 Fast		CAL_MDO[10] /	_	_	_
CAL_MDO[11]	Calibration Nexus Message Data Out	Р	01		ο	VDDE12 Fast	_	CAL_MDO[11] /	_	_	_
		•			NE	xus				•	
EVTI	Nexus event in	Ρ	01	231	I	VDDEH7 MultiV ^{(12),(14)}	— / Up	EVTI / Up	116	E15	F21
EVTO	Nexus event out	Р	01	227	0	VDDEH7 MultiV ^{(12),(14),} (15)	_	EVTO / —	120	D15	F22
МСКО	Nexus message clock out	Р	_	219 ⁽¹¹)	0	VRC33 Fast	_	МСКО / —	14	F15	G20
MDO0 ⁽¹⁶⁾	Nexus message data out	Р	01	220	0	VRC33 Fast	_	MDO[0] / —	17	A14	B20
MDO1 ⁽¹⁶⁾	Nexus message data out	Р	01	221	0	VRC33 Fast	_	MDO[1] / —	18	B14	C19
MDO2 ⁽¹⁶⁾	Nexus message data out	Р	01	222	0	VRC33 Fast	_	MDO[2] / —	19	A13	C18
MDO3 ⁽¹⁶⁾	Nexus message data out	Р	01	223	0	VRC33 Fast	_	MDO[3] / —	20	B13	D18
MDO4 ⁽¹⁶⁾ ETPUA2_O ⁽⁸⁾ GPIO[75]	Nexus message data out eTPU A channel (output only) GPIO	P A1 G	01 10 00	75	0 0 I/0	VDDEH7 MultiV ^{(12),(14)}	_	_/_	126	P10	B19

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		Р	PCR		1/0	(5)	Sta	tus ⁽⁷⁾		Packag	e pin #
Name	Function ⁽¹⁾	A G ⁽²⁾	PA Field (3)	PCR (4)	l/O Type	Voltage ⁽⁵⁾ / Pad Type ⁽⁶⁾	During Reset	After Reset	176	208	324
MDO5 ⁽¹⁶⁾ ETPUA4_O ⁽⁸⁾ GPIO[76]	Nexus message data out eTPU A channel (output only) GPIO	P A1 G	01 10 00	76	0 0 I/O	VDDEH7 MultiV ^{(12),(14)}	_	_/_	129	T10	C17
MDO6 ⁽¹⁶⁾ ETPUA13_O ⁽⁸⁾ GPIO[77]	Nexus message data out eTPU A channel (output only) GPIO	P A1 G	01 10 00	77	0 0 I/O	VDDEH7 MultiV ^{(12),(14)}	_	_/_	135	T11	D17
MDO7 ⁽¹⁶⁾ ETPUA19_O ⁽⁸⁾ GPIO[78]	Nexus message data out eTPU A channel (output only) GPIO	P A1 G	01 10 00	78	0 0 I/O	VDDEH7 MultiV ^{(12),(14)}	_	_/_	136	N11	B18
MDO8 ⁽¹⁶⁾ ETPUA21_O ⁽⁸⁾ GPIO[79]	Nexus message data out eTPU A channel (output only) GPIO	P A1 G	01 10 00	79	0 0 I/O	VDDEH7 MultiV ^{(12),(14)}	_	_/_	137	P11	A19
MDO9 ⁽¹⁶⁾ ETPUA25_O ⁽⁸⁾ GPIO[80]	Nexus message data out eTPU A channel (output only) GPIO	P A1 G	01 10 00	80	0 0 I/O	VDDEH7 MultiV ^{(12),(14)}	_	_/_	139	Т7	B17
MDO10 ⁽¹⁶⁾ ETPUA27_O ⁽⁸⁾ GPIO[81]	Nexus message data out eTPU A channel (output only) GPIO	P A1 G	01 10 00	81	0 0 I/O	VDDEH7 MultiV ^{(12),(14)}	_	_/_	134	R10	A18
MDO11 ⁽¹⁶⁾ ETPUA29_O ⁽⁸⁾ GPIO[82]	Nexus message data out eTPU A channel (output only) GPIO[82]	P A1 G	01 10 00	82	000	VDDEH7 MultiV ^{(12),(14)}	_	_/_	124	P9	A17
MSEO[0] ⁽¹⁶⁾	Nexus message start/end out	Ρ	01	224	0	VDDEH7 MultiV ^{(12),(14)}	—	MSEO[0] /	118	C15	G21
MSEO[1] ⁽¹⁶⁾	Nexus message start/end out	Ρ	01	225	0	VDDEH7 MultiV ^{(12),(14)}	_	MSEO[1] /	117	E16	G22
RDY	Nexus ready output	Ρ	01	226	0	VDDEH7 MultiV ^{(12),(14)}	_	_	_	_	G19

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Pinout and signal description

		Р	PCR		I/O		Sta	tus ⁽⁷⁾	Package pin #		
Name	Function ⁽¹⁾	A G ⁽²⁾	PA Field (3)	PCR (4)	Туре	Voltage ⁽⁵⁾ / Pad Type ⁽⁶⁾	During Reset	After Reset	176	208	324
тск	JTAG test clock input	Ρ	01	_	I	VDDEH7 MultiV ⁽¹²⁾	TCK / Down	TCK / Down	128	C16	D21
TDI	JTAG test data input	Р	01	232	I	VDDEH7 MultiV ⁽¹²⁾	TDI / Up	TDI / Up	130	E14	D22
TDO	JTAG test data output	Р	01	228	0	VDDEH7 MultiV ⁽¹²⁾	TDO / Up	TDO / Up	123	F14	E21
TMS	JTAG test mode select input	Р	01	_	I	VDDEH7 MultiV ⁽¹²⁾	TMS / Up	TMS / Up	131	D14	E20
JCOMP	JTAG TAP controller enable	Р	01	_	I	VDDEH7 MultiV ⁽¹²⁾	JCOMP / Down	JCOMP / Down	121	F16	F20
	·				Flex	CAN			•		
CAN_A_TX SCI_A_TX GPIO[83]	FlexCAN A TX eSCI A TX GPIO	P A1 G	01 10 00	83	0 0 I/O	VDDEH6 Slow	— / Up	— / Up	81	P12	Y17
CAN_A_RX SCI_A_RX GPIO[84]	FlexCAN A RX eSCI A RX GPIO	P A1 G	01 10 00	84	 /O	VDDEH6 Slow	— / Up	— / Up	82	R12	AA18
CAN_B_TX DSPI_C_PCS[3] SCI_C_TX GPIO[85]	FlexCAN B TX DSPI C peripheral chip select eSCI C TX GPIO	P A1 A2 G	001 010 100 000	85	0 0 0 I/0	VDDEH6 Slow	— / Up	— / Up	88	T12	AB18
CAN_B_RX DSPI_C_PCS[4] SCI_C_RX GPIO[86]	FlexCAN B RX DSPI C peripheral chip select eSCI C RX GPIO	P A1 A2 G	001 010 100 000	86	 0 /0	VDDEH6 Slow	— / Up	— / Up	89	R13	AB19
CAN_C_TX DSPI_D_PCS[3] GPIO[87]	FlexCAN C TX DSPI D peripheral chip select GPIO	P A1 G	01 10 00	87	0 0 I/0	VDDEH6 Medium	— / Up	— / Up	101	К13	P19

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Table 4.	SPC564A80 signal properties (conti	nued)			
		Р		PCB	I/O	Ve

		Р	PCR	PCR	I/O	Voltage ⁽⁵⁾ /	Sta	tus ⁽⁷⁾	Packa		ge pin #	
Name	Function ⁽¹⁾	A G ⁽²⁾	PA Field (3)	PCR (4)	Туре	Pad Type ⁽⁶⁾	During Reset	After Reset	176	208	324	
CAN_C_RX DSPI_D_PCS[4] GPIO[88]	FlexCAN C RX DSPI D peripheral chip select GPIO	P A1 G	01 10 00	88	 0 /0	VDDEH6 Slow	— / Up	— / Up	98	L14	R20	
	-				eS	SCI						
SCI_A_TX EMIOS13 ⁽⁸⁾ GPIO[89]	eSCI A TX eMIOS channel GPIO	P A1 G	01 10 00	89	0 0 I/O	VDDEH6 Medium	— / Up	— / Up	100	J14	N20	
SCI_A_RX EMIOS15 ⁽⁸⁾ GPIO[90]	eSCI A RX eMIOS channel GPIO	P A1 G	01 10 00	90	 0 /0	VDDEH6 Medium	— / Up	— / Up	99	K14	P20	
SCI_B_TX DSPI_D_PCS[1] GPIO[91]	eSCI B TX DSPI D peripheral chip select GPIO	P A1 G	01 10 00	91	0 0 I/O	VDDEH6 Medium	— / Up	— / Up	87	L13	R21	
SCI_B_RX DSPI_D_PCS[5] GPIO[92]	eSCI B RX DSPI D peripheral chip select GPIO	P A1 G	01 10 00	92	 0 /0	VDDEH6 Medium	— / Up	— / Up	84	M13	T19	
SCI_C_TX GPIO[244]	eSCI C TX GPIO	P G	01 00	244	0 I/O	VDDEH6 Medium	— / Up	— / Up	_	_	W18	
SCI_C_RX GPIO[245]	eSCI C RX GPIO	P G	01 00	245	l I/O	VDDEH6 Medium	— / Up	— / Up	_	_	Y19	
					DS	SPI						
DSPI_A_SCK ⁽¹⁷⁾ DSPI_C_PCS[1] GPIO[93]	— DSPI C peripheral chip select GPIO	— A1 G	— 10 00	93	— 0 I/O	VDDEH7 Medium	— / Up	— / Up	_	_	L22	
DSPI_A_SIN ⁽¹⁷⁾ DSPI_C_PCS[2] GPIO[94]	— DSPI C peripheral chip select GPIO	— A1 G	— 10 00	94	— 0 I/O	VDDEH7 Medium	— / Up	— / Up	_	_	L21	

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Table 4.	SPC564A80 signal properties (continued)
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		Р	PCR		I/O		Sta	tus ⁽⁷⁾	Package pin #		
Name	Function ⁽¹⁾	A G ⁽²⁾	PA Field (3)	PCR (4)	Туре	Voltage ⁽⁵⁾ / Pad Type ⁽⁶⁾	During Reset	After Reset	176	208	324
DSPI_A_SOUT ⁽¹⁷⁾ DSPI_C_PCS[5] GPIO[95]	— DSPI C peripheral chip select GPIO	— A1 G	— 10 00	95	— 0 I/O	VDDEH7 Medium	— / Up	— / Up	_	_	L20
DSPI_A_PCS[0] ⁽¹⁷⁾ DSPI_D_PCS[2] GPIO[96]	— DSPI D peripheral chip select GPIO	— A1 G	— 10 00	96	— 0 I/0	VDDEH7 Medium	— / Up	— / Up	_	_	M20
DSPI_A_PCS[1] ⁽¹⁷⁾ DSPI_B_PCS[2] GPIO[97]	— DSPI B peripheral chip select GPIO	— A1 G	— 10 00	97	— 0 I/O	VDDEH7 Medium	— / Up	— / Up	_	_	M19
CS[2] DSPI_D_SCK GPIO[98]	— SPI clock pin for DSPI module GPIO	— A1 G	— 10 00	98	— I/O I/O	VDDEH7 Medium	— / Up	— / Up	141	J15	M21
CS[3] DSPI_D_SIN GPIO[99]	— DSPI D data input GPIO	— A1 G	— 10 00	99	– I I/O	VDDEH7 Medium	— / Up	— / Up	142	H13	K19
DSPI_A_PCS[4] ⁽¹⁷⁾ DSPI_D_SOUT GPIO[100]	— DSPI D data output GPIO	— A1 G	— 10 00	100	0 I/O	VDDEH7 Medium	— / Up	— / Up	_	_	N19
DSPI_A_PCS[5] ⁽¹⁷⁾ DSPI_B_PCS[3] GPIO[101]	— DSPI B peripheral chip select GPIO	— A1 G	— 10 00	101	0 I/O	VDDEH7 Medium	— / Up	— / Up	_	_	N21
DSPI_B_SCK DSPI_C_PCS[1] GPIO[102]	SPI clock pin for DSPI module DSPI C peripheral chip select GPIO	P A1 G	01 10 00	102	I/O O I/O	VDDEH6 Medium	— / Up	— / Up	106	J16	K21
DSPI_B_SIN DSPI_C_PCS[2] GPIO[103]	DSPI B data input DSPI C peripheral chip select GPIO	P A1 G	01 10 00	103	 0 /0	VDDEH6 Medium	— / Up	— / Up	112	G15	H22

Table 4.	SPC564A80 signal properties (continued)
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		Р	PCR		1/0	(5)	Sta	tus ⁽⁷⁾		Package pin #		
Name	Function ⁽¹⁾	A G ⁽²⁾	PA Field (3)	PCR (4)	l/O Type	Voltage ⁽⁵⁾ / Pad Type ⁽⁶⁾	During Reset	After Reset	176	208	324	
DSPI_B_SOUT DSPI_C_PCS[5] GPIO[104]	DSPI B data output DSPI C peripheral chip select GPIO	P A1 G	01 10 00	104	0 0 I/O	VDDEH6 Medium	— / Up	— / Up	113	G13	J19	
DSPI_B_PCS[0] DSPI_D_PCS[2] GPIO[105]	DSPI B peripheral chip select DSPI D peripheral chip select GPIO	P A1 G	01 10 00	105	I/O O I/O	VDDEH6 Medium	— / Up	— / Up	111	G16	J21	
DSPI_B_PCS[1] DSPI_D_PCS[0] GPIO[106]	DSPI B peripheral chip select DSPI D peripheral chip select GPIO	P A1 G	01 10 00	106	0 I/O I/O	VDDEH6 Medium	— / Up	— / Up	109	H16	J22	
DSPI_B_PCS[2] DSPI_C_SOUT GPIO[107]	DSPI B peripheral chip select DSPI C data output GPIO	P A1 G	01 10 00	107	0 0 I/O	VDDEH6 Medium	— / Up	— / Up	107	H15	K22	
DSPI_B_PCS[3] DSPI_C_SIN GPIO[108]	DSPI B peripheral chip select DSPI C data input GPIO	P A1 G	01 10 00	108	0 I I/O	VDDEH6 Medium	— / Up	— / Up	114	G14	J20	
DSPI_B_PCS[4] DSPI_C_SCK GPIO[109]	DSPI B peripheral chip select SPI clock pin for DSPI module GPIO	P A1 G	01 10 00	109	0 I/O I/O	VDDEH6 Medium	— / Up	— / Up	105	H14	K20	
DSPI_B_PCS[5] DSPI_C_PCS[0] GPIO[110]	DSPI B peripheral chip select DSPI C peripheral chip select GPIO	P A1 G	01 10 00	110	0 I/O I/O	VDDEH6 Medium	— / Up	— / Up	104	J13	L19	
					eQ	ADC						
ANO ⁽¹⁸⁾ DAN0+	Single Ended Analog Input Positive Terminal Diff. Input	Р	_	_	I I	VDDA Analog	I / —	AN[0] / —	172	B5	B8	
AN1 ⁽¹⁸⁾ DAN0-	Single Ended Analog Input Negative Terminal Diff. Input	Р	_	_	l I	VDDA Analog	I / —	AN[1]/—	171	A6	A8	
AN2 ⁽¹⁸⁾ DAN1+	Single Ended Analog Input Positive Terminal Diff. Input	Р	_	_	l I	VDDA Analog	I/—	AN[2] / —	170	D6	D10	

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		Р	PCR		I/O	(5)	Sta	tus ⁽⁷⁾		Package pin #		
Name	Function ⁽¹⁾	A G ⁽²⁾	PA Field (3)	PCR (4)	і/О Туре	Voltage ⁽⁵⁾ / Pad Type ⁽⁶⁾	During Reset	After Reset	176	208	324	
AN3 ⁽¹⁸⁾ DAN1-	Single Ended Analog Input Negative Terminal Diff. Input	Р	_	_	l I	VDDA Analog	I/—	AN[3] / —	169	C7	C9	
AN4 ⁽¹⁸⁾ DAN2+	Single Ended Analog Input Positive Terminal Diff. Input	Р	_	_	l I	VDDA Analog	I/—	AN[4] / —	168	B6	B9	
AN5 ⁽¹⁸⁾ DAN2-	Single Ended Analog Input Negative Terminal Diff. Input	Р	_	_	l I	VDDA Analog	I / —	AN[5] / —	167	A7	A9	
AN6 ⁽¹⁸⁾ DAN3+	Single Ended Analog Input Positive Terminal Diff. Input	Р		_	l	VDDA Analog	I/—	AN[6] / —	166	D7	D11	
AN7 ⁽¹⁸⁾ DAN3-	Single Ended Analog Input Negative Terminal Diff. Input	Р	_	_	l I	VDDA Analog	I/—	AN[7] / —	165	C8	C10	
AN8 ANW	Single-ended Analog Input Multiplexed Analog Input	Р	01	_	I	VDDA Analog	I / —	AN[8] / —	9	B3	D6	
AN9 ANX	Single-ended Analog Input External Multiplexed Analog Input	Р	01	_	l	VDDA Analog	I/—	AN[9] / —	5	A2	D7	
AN10 ANY	Single-ended Analog Input Multiplexed Analog Input	Р	01	_	I	VDDA Analog	I/—	AN[10] / —	_	_	D8	
AN11 ANZ	Single-ended Analog Input Multiplexed Analog Input	Р	01	_	I	VDDA Analog	I/—	AN[11] / —	4	A3	A5	
AN12 - SDS MA0 ETPUA19_O ⁽⁸⁾ SDS	Single-ended Analog Input MUX Address 0 eTPU A channel (output only) eQADC Serial Data Select	P A1 A2 G	001 010 100 000	215	 0 /0	VDDEH7 ⁽¹⁹⁾ Medium	1/—	AN[12] / —	148	A12	A16	
AN13 - SDO MA1 ETPUA21_O ⁽⁸⁾ SDO	Single-ended Analog Input MUX Address 1 eTPU A channel (output only) eQADC Serial Data Out	P A1 A2 G	001 010 100 000	216	 0 0	VDDEH7 ⁽¹⁹⁾ Medium	1/—	AN[13] / —	147	B12	B16	

		Р	PCR		I/O		Sta	tus ⁽⁷⁾	Package pin #		
Name	Function ⁽¹⁾	A G ⁽²⁾	PA Field (3)	PCR (4)	Туре	Voltage ⁽⁵⁾ / Pad Type ⁽⁶⁾	During Reset	After Reset	176	208	324
AN14 - SDI MA2 ETPUA27_O ⁽⁸⁾ SDI	Single-ended Analog Input MUX Address 2 eTPU A channel (output only) eQADC Serial Data In	P A1 A2 G	001 010 100 000	217	 0 	VDDEH7 ⁽¹⁹⁾ Medium	1/—	AN[14] / —	146	C12	C16
AN15 - FCK FCK ETPUA29_O ⁽⁸⁾	Single-ended Analog Input eQADC Free Running Clock eTPU A channel (output only)	P A1 A2	001 010 100	218	 0 0	VDDEH7 ⁽¹⁹⁾ Medium	1/—	AN[15] / —	145	C13	D16
AN16	Single-ended Analog Input	Ρ	_	_	I	VDDA Analog	I / —	AN[16] / —	3	C6	B7
AN17	Single-ended Analog Input	Ρ	_	_	I	VDDA Analog	I / —	AN[17] / —	2	C4	C6
AN18	Single-ended Analog Input	Ρ	_	_	I	VDDA Analog	I / —	AN[18] / —	1	D5	D9
AN19	Single-ended Analog Input	Ρ	_	_	I	VDDA Analog	I / —	AN[19] / —	_	_	B6
AN20	Single-ended Analog Input	Ρ	_	_	I	VDDA Analog	I / —	AN[20] / —	_	_	C7
AN21	Single-ended Analog Input	Ρ	_	_	I	VDDA Analog	I / —	AN[21] / —	173	B4	C8
AN22	Single-ended Analog Input	Ρ	_	_	I	VDDA Analog	I / —	AN[22] / —	161	B8	C11
AN23	Single-ended Analog Input	Ρ		_	I	VDDA Analog	I / —	AN[23] / —	160	C9	B11
AN24	Single-ended Analog Input	Ρ	_	_	I	VDDA Analog	I/—	AN[24] / —	159	D8	D12
AN25	Single-ended Analog Input	Ρ	_	_	I	VDDA Analog	I/—	AN[25] / —	158	B9	C12

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		Р	PCR		I/O	Voltage ⁽⁵⁾ /	Sta	tus ⁽⁷⁾		Packag	ge pin #
Name	Function ⁽¹⁾	A G ⁽²⁾	PA Field (3)	PCR (4)	і/О Туре	Pad Type ⁽⁶⁾	During Reset	After Reset	176	208	324
AN26	Single-ended Analog Input	Р	_	_	I	VDDA Analog	I / —	AN[26] / —	_	_	B12
AN27	Single-ended Analog Input	Р	_	_	I	VDDA Analog	I / —	AN[27] / —	157	A10	A12
AN28	Single-ended Analog Input	Р	_	_	I	VDDA Analog	I / —	AN[28] / —	156	B10	A13
AN29	Single-ended Analog Input	Р	_	_	I	VDDA Analog	I / —	AN[29] / —	_	_	D13
AN30	Single-ended Analog Input	Р	_	_	I	VDDA Analog	I / —	AN[30] / —	155	D9	C13
AN31	Single-ended Analog Input	Р	_	_	I	VDDA Analog	I / —	AN[31] / —	154	D10	B13
AN32	Single-ended Analog Input	Р	_	_	I	VDDA Analog	I / —	AN[32]/—	153	C10	B14
AN33	Single-ended Analog Input	Р	_	_	I	VDDA Analog	I / —	AN[33] / —	152	C11	C14
AN34	Single-ended Analog Input	Р	_	_	I	VDDA Analog	I / —	AN[34] / —	151	C5	D14
AN35	Single-ended Analog Input	Р	_	_	I	VDDA Analog	I / —	AN[35] / —	150	D11	A14
AN36	Single-ended Analog Input	Р	_	_	I	VDDA Analog	I / —	AN[36] / —	174	F4	B4
AN37	Single-ended Analog Input	Р	_	_	I	VDDA Analog	I / —	AN[37] / —	175	E3	A4
AN38	Single-ended Analog Input	Р	_	_	I	VDDA Analog	I / —	AN[38] / —	_	_	C5
AN39	Single-ended Analog Input	Р	_	_	I	VDDA Analog	I / —	AN[39] / —	8	D2	B5

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Table 4.	SPC564A80 signal properties (continued)
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		Р	PCR		I/O		Sta	tus ⁽⁷⁾		Packag	je pin #
Name	Function ⁽¹⁾	A G ⁽²⁾	PA Field (3)	PCR (4)	і/О Туре	Voltage ⁽⁵⁾ / Pad Type ⁽⁶⁾	During Reset	After Reset	176	208	324
VRH	Voltage Reference High	Р	_	_	I	VDDA —	I / —	VRH	163	A8	A10
VRL	Voltage Reference Low	Р	_		I	VDDA —	I/—	VRL	162	A9	A11
REFBYBC	Reference Bypass Capacitor Input	Р	_	_	I	VDDA Analog	I / —	REFBYPC	164	B7	B10
					eT	PU2					
TCRCLKA IRQ[7] GPIO[113]	eTPU A TCR clock External interrupt request GPIO	P A1 G	01 10 00	113	 /O	VDDEH4 Slow	— / Up	— / Up	_	L4	M2
ETPUA0 ETPUA12_O ⁽⁸⁾ ETPUA19_O ⁽⁸⁾ GPIO[114]	eTPU A channel eTPU A channel (output only) eTPU A channel (output only) GPIO	P A1 A2 G	001 010 100 000	114	I/O O O I/O	VDDEH4 Slow	— / WKPCFG	— / WKPCFG	61	N3	L3
ETPUA1 ETPUA13_O ⁽⁸⁾ GPIO[115]	eTPU A channel eTPU A channel (output only) GPIO	P A1 G	01 10 00	115	I/O O I/O	VDDEH4 Slow	— / WKPCFG	— / WKPCFG	60	МЗ	L4
ETPUA2 ETPUA14_O ⁽⁸⁾ GPIO[116]	eTPU A channel eTPU A channel (output only) GPIO	P A1 G	01 10 00	116	I/O O I/O	VDDEH4 Slow	— / WKPCFG	— / WKPCFG	59	P2	кз
ETPUA3 ETPUA15_O ⁽⁸⁾ GPIO[117]	eTPU A channel eTPU A channel (output only) GPIO	P A1 G	01 10 00	117	I/O O I/O	VDDEH4 Slow	— / WKPCFG	GPIO / WKPCFG	58	P1	L2
ETPUA4 ETPUA16_O ⁽⁸⁾ FR_B_TX GPIO[118]	eTPU A channel eTPU A channel (output only) Flexray TX data channel B GPIO	P A1 A3 G	0001 0010 1000 0000	118	I/O O O I/O	VDDEH4 Slow	— / WKPCFG	— / WKPCFG	56	N2	L1

Table 4.	SPC564A80 signal properties (continued)
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		Р	PCR		I/O		Sta	tus ⁽⁷⁾	Package pin #		
Name	Function ⁽¹⁾	A G ⁽²⁾	PA Field (3)	PCR (4)	Туре	Voltage ⁽⁵⁾ / Pad Type ⁽⁶⁾	During Reset	After Reset	176	208	324
ETPUA5 ETPUA17_O ⁽⁸⁾ DSPI_B_SCK_LVD S- FR_B_TX_EN GPIO[119]	eTPU A channel eTPU A channel (output only) LVDS negative DSPI clock Flexray TX data enable for ch. B GPIO	P A1 A2 A3 G	0001 0010 0100 1000 0000	119	I/O O O I/O	VDDEH4 Slow + LVDS	— / WKPCFG	— / WKPCFG	54	M4	К4
ETPUA6 ETPUA18_O ⁽⁸⁾ DSPI_B_SCK_LVD S+ FR_B_RX GPIO[120]	eTPU A channel eTPU A channel (output only) LVDS positive DSPI clock Flexray RX data channel B GPIO	P A1 A2 A3 G	0001 0010 0100 1000 0000	120	I/O O I I/O	VDDEH4 Medium + LVDS	— / WKPCFG	— / WKPCFG	53	L3	J3
ETPUA7 ETPUA19_0 ⁽⁸⁾ DSPI_B_SOUT_LV DS- ETPUA6_0 ⁽⁸⁾ GPIO[121]	eTPU A channel eTPU A channel (output only) LVDS negative DSPI data out eTPU A channel (output only) GPIO	P A1 A2 A3 G	0001 0010 0100 1000 0000	121	I/O O O I/O	VDDEH4 Slow + LVDS	— / WKPCFG	— / WKPCFG	52	кз	к2
ETPUA8 ETPUA20_O ⁽⁸⁾ DSPI_B_SOUT_LV DS+ GPIO[122]	eTPU A channel eTPU A channel (output only) LVDS positive DSPI data out GPIO	P A1 A2 G	001 010 100 000	122	I/O O O I/O	VDDEH4 Slow + LVDS	— / WKPCFG	— / WKPCFG	51	N1	К1
ETPUA9 ETPUA21_O ⁽⁸⁾ RCH1_B GPIO[123]	eTPU A channel eTPU A channel (output only) Reaction channel 1B GPIO	P A1 A2 G	001 010 100 000	123	I/O O O I/O	VDDEH4 Slow	— / WKPCFG	— / WKPCFG	50	M2	J4
ETPUA10 ETPUA22_O ⁽⁸⁾ RCH1_C GPIO[124]	eTPU A channel eTPU A channel (output only) Reaction channel 1C GPIO	P A1 A2 G	001 010 100 000	124	I/O O O I/O	VDDEH1 Slow	— / WKPCFG	— / WKPCFG	49	M1	НЗ



		Р	PCR		I/O	(E)	Sta	tus ⁽⁷⁾	Package pin #			
Name	Function ⁽¹⁾	A G ⁽²⁾	PA Field (3)	PCR (4)	і/О Туре	Voltage ⁽⁵⁾ / Pad Type ⁽⁶⁾	During Reset	After Reset	176	208	324	
ETPUA11 ETPUA23_O ⁽⁸⁾ RCH4_B GPIO[125]	eTPU A channel eTPU A channel (output only) Reaction channel 4B GPIO	P A1 A2 G	001 010 100 000	125	I/O O O I/O	VDDEH1 Slow	— / WKPCFG	— / WKPCFG	48	L2	J2	
ETPUA12 DSPI_B_PCS[1] RCH4_C GPIO[126]	eTPU A channel DSPI B peripheral chip select Reaction channel 4C GPIO	P A1 A2 G	001 010 100 000	126	I/O O O I/O	VDDEH1 Medium	— / WKPCFG	— / WKPCFG	47	L1	J1	
etpua13 DSPI_B_PCS[3] GPIO[127]	eTPU A channel DSPI B peripheral chip select GPIO	P A1 G	01 10 00	127	I/O O I/O	VDDEH1 Medium	— / WKPCFG	— / WKPCFG	46	J4	G4	
ETPUA14 DSPI_B_PCS[4] ETPUA9_O ⁽⁸⁾ RCH0_A GPIO[128]	eTPU A channel DSPI B peripheral chip select eTPU A channel (output only) Reaction channel 0A GPIO	P A1 A2 A3 G	0001 0010 0100 1000 0000	128	I/O O O I/O	VDDEH1 Medium	— / WKPCFG	— / WKPCFG	42	J3	G3	
ETPUA15 DSPI_B_PCS[5] RCH1_A GPIO[129]	eTPU A channel DSPI B peripheral chip select Reaction channel 1A GPIO	P A1 A2 G	001 010 100 000	129	I/O O O I/O	VDDEH1 Medium	— / WKPCFG	— / WKPCFG	40	К2	H2	
ETPUA16 DSPI_D_PCS[1] RCH2_A GPIO[130]	eTPU A channel DSPI D peripheral chip select Reaction channel 2A GPIO	P A1 A2 G	001 010 100 000	130	I/O O O I/O	VDDEH1 Slow	— / WKPCFG	— / WKPCFG	39	К1	H1	
ETPUA17 DSPI_D_PCS[2] RCH3_A GPIO[131]	eTPU A channel DSPI D peripheral chip select Reaction channel 3A GPIO	P A1 A2 G	001 010 100 000	131	I/O O O I/O	VDDEH1 Slow	— / WKPCFG	— / WKPCFG	38	НЗ	F3	

SPC564A80 signal properties (continued) Table 4.

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		Р	PCR		I/O		Sta	tus ⁽⁷⁾	Package pin #		
Name	Function ⁽¹⁾	A G ⁽²⁾	PA Field (3)	PCR (4)	Туре	Voltage ⁽⁵⁾ / Pad Type ⁽⁶⁾	During Reset	After Reset	176	208	324
ETPUA18	eTPU A channel	Р	001		I/O						
DSPI_D_PCS[3]	DSPI D peripheral chip select	A1	010	132	0	VDDEH1	— /	—/	37	H4	F4
RCH4_A	Reaction channel 4A	A2	100	-	0	Slow	WKPCFG	WKPCFG	-		
GPIO[132]	GPIO	G	000		I/O						
ETPUA19	eTPU A channel	Р	001		I/O						
DSPI_D_PCS[4]	DSPI D peripheral chip select	A1	010	133	0	VDDEH1	— /	— /	36	J2	G2
RCH5_A	Reaction channel 5A	A2	100	100	0	Slow	WKPCFG	WKPCFG	50	52	02
GPIO[133]	GPIO	G	000		I/O						
ETPUA20	eTPU A channel	Р	0001		I/O						
IRQ[8]	External interrupt request	A1	0010		I	VDDEH1	,	1			
RCH0_B	Reaction channel 0B	A2	0100	134	0	Slow	— / WKPCFG	— / WKPCFG	35	J1	G1
FR_A_TX	Flexray TX data channel A	A3	1000		0	510W	WKPCFG	WKPCFG			
GPIO[134]	GPIO	G	0000		I/O						
ETPUA21	eTPU A channel	Р	0001		I/O						
IRQ[9]	External interrupt request	A1	0010		I	VDDEH1	,	1			
RCH0_C	Reaction channel 0C	A2	0100	135	0	Slow	WKPCFG	— / WKPCFG	34	G4	E4
FR_A_RX	Flexray RX channel A	A3	1000		I	510W	WKPCFG	WKPCFG			
GPIO[135]	GPIO	G	0000		I/O						
ETPUA22	eTPU A channel	Р	001		I/O						
IRQ[10]	External interrupt request	A1	010	136	I.	VDDEH1	— /	— /	32	H2	F2
ETPUA17_O ⁽⁸⁾	eTPU A channel (output only)	A2	100	100	0	Slow	WKPCFG	WKPCFG	52		' <i>-</i>
GPIO[136]	GPIO	G	000		I/O						
ETPUA23	eTPU A channel	Р	0001		I/O						
IRQ[11]	External interrupt request	A1	0010		I	VDDEH1	— /	—/			
ETPUA21_O ⁽⁸⁾	eTPU A channel (output only)	A2	0100	137	0	Slow	WKPCFG	WKPCFG	30	H1	F1
FR_A_TX_EN	Flexray ch. A TX enable	A3	1000		0	SIOW	WINFUEG	WINFUEG			
GPIO[137]	GPIO	G	0000		I/O						

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Table 4.	SPC564A80 signal properties	(contii
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	Function ⁽¹⁾	Р	PCR		I/O		Sta	tus ⁽⁷⁾	Package pin #		
Name		A G ⁽²⁾	PA Field (3)	PCR (4)	Туре	Voltage ⁽⁵⁾ / Pad Type ⁽⁶⁾	During Reset	After Reset	176	208	324
ETPUA24 IRQ[12] DSPI_C_SCK_LVD S- GPIO[138]	eTPU A channel External interrupt request LVDS negative DSPI clock GPIO	P A1 A2 G	001 010 100 000	138	I/O I O I/O	VDDEH1 Slow + LVDS	— / WKPCFG	— / WKPCFG	28	G1	E1
ETPUA25 IRQ[13] DSPI_C_SCK_LVD S+ GPIO[139]	eTPU A channel External interrupt request LVDS positive DSPI clock GPIO	P A1 A2 G	001 010 100 000	139	I/O I O I/O	VDDEH1 Medium + LVDS	— / WKPCFG	— / WKPCFG	27	G3	E3
ETPUA26 IRQ[14] DSPI_C_SOUT_LV DS- GPIO[140]	eTPU A channel External interrupt request LVDS negative DSPI data out GPIO	P A1 A2 G	001 010 100 000	140	I/O I O I/O	VDDEH1 Slow + LVDS	— / WKPCFG	— / WKPCFG	26	F3	D3
ETPUA27 IRQ[15] DSPI_C_SOUT_LV DS+ DSPI_B_SOUT GPIO[141]	eTPU A channel External interrupt request LVDS positive DSPI data out DSPI data out GPIO	P A1 A2 A3 G	0001 0010 0100 1000 0000	141	I/O I O I/O	VDDEH1 Slow + LVDS	— / WKPCFG	— / WKPCFG	25	G2	E2
ETPUA28 DSPI_C_PCS[1] RCH5_B GPIO[142]	eTPU A channel DSPI C peripheral chip select Reaction channel 5B GPIO	P A1 A2 G	001 010 100 000	142	I/O O O I/O	VDDEH1 Medium	— / WKPCFG	— / WKPCFG	24	F1	D1
ETPUA29 DSPI_C_PCS[2] RCH5_C GPI0[143]	eTPU A channel DSPI C peripheral chip select Reaction channel 5C GPIO	P A1 A2 G	001 010 100 000	143	I/O O O I/O	VDDEH1 Medium	— / WKPCFG	— / WKPCFG	23	F2	D2

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Table 4.	SPC564A80 signal properties (continued)
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		Р	PCR	PCR (4)	I/O		Sta	tus ⁽⁷⁾		Packag	je pin #
Name	Function ⁽¹⁾	A G ⁽²⁾	PA Field (3)		і/О Туре	Voltage ⁽⁵⁾ / Pad Type ⁽⁶⁾	During Reset	After Reset	176	208	324
ETPUA30	eTPU A channel	Р	001		I/O						
DSPI_C_PCS[3]	DSPI C peripheral chip select	A1	010	144	0	VDDEH1	_/	<u> </u>	22	E1	C1
ETPUA11_O ⁽⁸⁾	eTPU A channel (output only)	A2	100	144	0	Medium	WKPCFG	WKPCFG	22		01
GPIO[144]	GPIO	G	000		I/O						
ETPUA31	eTPU A channel	Р	001		I/O						
DSPI_C_PCS[4]	DSPI C peripheral chip select	A1	010		0	VDDEH1	<u> </u>	— /		50	
ETPUA13_O ⁽⁸⁾	eTPU A channel (output only)	A2	100		0	Medium	WKPCFG	WKPCFG	21	E2	C2
GPIO[145]	GPIO	G	000		I/O						
					eM	IOS					1
EMIOS0	eMIOS channel	Р	001		I/O						
ETPUA0_O ⁽⁸⁾	eTPU A channel (output only)	A1	010		0	VDDEH4					
ETPUA25_O ⁽⁸⁾	eTPU A channel (output only)	A2	100	100 179	0	Slow	— / Up	— / Up	63	T4	AB10
GPIO[179]	GPIO	G	000		I/O						
EMIOS1	eMIOS channel	Р	01		I/O						
ETPUA1_O ⁽⁸⁾	eTPU A channel (output only)	A1	10	180	0	VDDEH4 Slow	— / Up	— / Up	64	Т5	AB11
GPIO[180]	GPIO	G	00		I/O						
EMIOS2	eMIOS channel	Р	001		I/O						
ETPUA2_O ⁽⁸⁾	eTPU A channel (output only)	A1	010		0	VDDEH4	<i>.</i>	<i>.</i>			
RCH2_B	Reaction channel 2B	A2	100	181	0	Slow	— / Up	— / Up	65	N7	W12
GPIO[181]	GPIO	G	000		I/O						
EMIOS3	eMIOS channel	Р	01		I/O		,				
ETPUA3_O ⁽⁸⁾	eTPU A channel (output only)	A1	10	182	0	VDDEH4	—/	—/	66	R6	AA11
GPIO[182]	GPIO	G	00	102	I/O	Slow	WKPCFG	WKPCFG			
EMIOS4	eMIOS channel	Р	001		I/O						
ETPUA4_O ⁽⁸⁾	eTPU A channel (output only)	A1	010		0	VDDEH4	_/	—/			
RCH2_C	Reaction channel 2C	A2	100	183	0	Slow	WKPCFG	WKPCFG	67	R5	AB12
GPIO[183]	GPIO	G	000		I/O						

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Pinout and signal description

		Р	PCR			(5)	Sta	tus ⁽⁷⁾	Package pin #		
Name	Function ⁽¹⁾	A G ⁽²⁾	PA Field (3)	PCR (4)	l/O Type	Voltage ⁽⁵⁾ / Pad Type ⁽⁶⁾	During Reset	After Reset	176	208	32
EMIOS5 ETPUA5_O ⁽⁸⁾ GPIO[184]	eMIOS channel eTPU A channel (output only) GPIO	P A1 G	01 10 00	184	I/O O I/O	VDDEH4 Slow	— / WKPCFG	— / WKPCFG	_	_	AA12
EMIOS6 ETPUA6_O ⁽⁸⁾ GPIO[185]	eMIOS channel eTPU A channel (output only) GPIO	P A1 G	01 10 00	185	I/O O I/O	VDDEH4 Slow	— / Down	— / Down	68	P7	Y12
EMIOS7 ETPUA7_O ⁽⁸⁾ GPIO[186]	eMIOS channel eTPU A channel (output only) GPIO	P A1 G	01 10 00	186	I/O O I/O	VDDEH4 Slow	— / Down	— / Down	69	_	AB13
EMIOS8 ETPUA8_O ⁽⁸⁾ SCI_B_TX GPIO[187]	eMIOS channel eTPU A channel (output only) eSCI B TX GPIO	P A1 A2 G	001 010 100 000	187	I/O O O I/O	VDDEH4 Slow	— / Up	— / Up	70	P8	W13
EMIOS9 ETPUA9_O ⁽⁸⁾ SCI_B_RX GPIO[188]	eMIOS channel eTPU A channel (output only) eSCI B RX GPIO	P A1 A2 G	001 010 100 000	188	I/O O I I/O	VDDEH4 Slow	— / Up	— / Up	71	R7	AA13
EMIOS10 DSPI_D_PCS[3] RCH3_B GPIO[189]	eMIOS channel DSPI D peripheral chip select Reaction channel 3B GPIO	P A1 A2 G	001 010 100 000	189	I/O O O I/O	VDDEH4 Medium	— / WKPCFG	— / WKPCFG	73	N8	Y13
EMIOS11 DSPI_D_PCS[4] RCH3_C GPIO[190]	eMIOS channel DSPI D peripheral chip select Reaction channel 3C GPIO	P A1 A2 G	001 010 100 000	190	I/O O O I/O	VDDEH4 Medium	— / WKPCFG	— / WKPCFG	75	R8	AB14
EMIOS12 DSPI_C_SOUT ETPUA27_O ⁽⁸⁾	eMIOS channel DSPI C data output eTPU A channel (output only)	P A1 A2	001 010 100	191	I/O O O	VDDEH4 Medium	— / WKPCFG	— / WKPCFG	76	N10	W15

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I/O

Table 4. SPC564A80 signal properties (continued)

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GPIO[191]

GPIO

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		Р	PCR PA Field (3)		I/O	(5)	Sta	tus ⁽⁷⁾	Package pin #		
Name	Function ⁽¹⁾	A G ⁽²⁾		PCR (4)	і/О Туре	Voltage ⁽⁵⁾ / Pad Type ⁽⁶⁾	During Reset	After Reset	176	208	324
EMIOS13 DSPI_D_SOUT GPIO[192]	eMIOS channel DSPI D data output GPIO	P A1 G	01 10 00	192	I/O O I/O	VDDEH4 Medium	— / WKPCFG	— / WKPCFG	77	Т8	AA14
EMIOS14 IRQ[0] ETPUA29_O ⁽⁸⁾ GPIO[193]	eMIOS channel External interrupt request eTPU A channel (output only) GPIO	P A1 A2 G	001 010 100 000	193	I/O I O I/O	VDDEH4 Slow	— / Down	— / Down	78	R9	AB15
EMIOS15 IRQ[1] GPIO[194]	eMIOS channel External interrupt request GPIO	P A1 G	01 10 00	194	I/O I I/O	VDDEH4 Slow	— / Down	— / Down	79	Т9	Y14
EMIOS16 GPIO[195]	eMIOS channel GPIO	P G	01 00	195	I/O I/O	VDDEH4 Slow	— / Up	— / Up	_	_	AA15
EMIOS17 GPIO[196]	eMIOS channel GPIO	P G	01 00	196	I/O I/O	VDDEH4 Slow	— / Up	— / Up	_	_	Y15
EMIOS18 GPIO[197]	eMIOS channel GPIO	P G	01 00	197	I/O I/O	VDDEH4 Slow	— / Up	— / Up	_	_	AB16
EMIOS19 GPIO[198]	eMIOS channel GPIO	P G	01 00	198	I/O I/O	VDDEH4 Slow	— / WKPCFG	— / WKPCFG	_	_	AA16
EMIOS20 GPIO[199]	eMIOS channel GPIO	P G	01 00	199	I/O I/O	VDDEH4 Slow	— / WKPCFG	—/ WKPCFG	_	_	AB17
EMIOS21 GPIO[200]	eMIOS channel GPIO	P G	01 00	200	I/O I/O	VDDEH4 Slow	— / WKPCFG	—/ WKPCFG	_	_	W16
EMIOS22 GPIO[201]	eMIOS channel GPIO	P G	01 00	201	I/O I/O	VDDEH4 Slow	— / Down	— / Down	_		Y16
EMIOS23 GPIO[202]	eMIOS channel GPIO	P G	01 00	202	I/O I/O	VDDEH4 Slow	— / Down	— / Down	80	R11	AA17

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SPC564A74L7, SPC564A80B4, SPC564A80L7

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		Р	PCR		I/O		Sta	tus ⁽⁷⁾	Package pin #			
Name	Function ⁽¹⁾	A G ⁽²⁾	PA Field (3)	PCR (4)	-	Voltage ⁽⁵⁾ / Pad Type ⁽⁶⁾	During Reset	After Reset	176	208	324	
XTAL	Crystal oscillator output	Ρ	01	_	0	VDDEH6 Analog	_	_	93	P16	V22	
EXTAL EXTCLK	Crystal oscillator input External clock input	P A	01 10	_	I	VDDEH6 Analog			92	N16	U22	
CLKOUT	System clock output	Ρ	01	229	ο	VDDE5 Fast		CLKOUT	_	_	AA20	
ENGCLK	Engineering clock output	Ρ	01	214	0	VDDE5 Fast	_	ENGCLK	_	T14	AB21	
					Power /	Ground			_			
VDDREG	Voltage Regulator Supply	_		_	I	5 V	I/—	VDDREG	10	K16	M22	
VRCCTL	Voltage Regulator Control Output	_		_	0	_	0/—	VRCCTL	11	N14	V20	
VRC33 ⁽²⁰⁾	Internal regulator output Input for external 3.3 V supply	_		_	0	3.3 V 3.3 V	I/O / —	VRC33	13		A21, B1, P4, W7, Y22	
VDDA	eQADC high reference voltage	_		_	I	5 V	I/—	VDDA	6	_	_	
VSSA	eQADC ground/low reference voltage	_		_	I		I / —	VSSA	7	_		
VDDA0 ⁽²¹⁾	eQADC high reference voltage	—		_	I	5 V	I/—	VDDA0	—	B11	A6	
VSSA0 ⁽²²⁾	eQADC ground/low reference voltage	_		_	I	—	I/—	VSSA0	_	A11	A7	
VDDA1 ⁽²¹⁾	eQADC high reference voltage	_		_	I	5 V	I/—	VDDA1	—	A4	C15	
VSSA1 ⁽²²⁾	eQADC ground/low reference voltage	_		_	I	_	I / —	VSSA1	_	A5	A15, B15	
VDDPLL	FMPLL Supply Voltage	_		_	I	1.2	I/—	VDDPLL	91	R16	W22	
VSTBY	Power Supply for Standby RAM	_		—	I	0.9 V - 6 V	I/—	VSTBY	12	C1	A3	

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		P A G ⁽²⁾	PCR PA Field (3)	PCR (4)	1/0		Sta	tus ⁽⁷⁾	Package pin #			
Name	Function ⁽¹⁾				l/O Type	Voltage ⁽⁵⁾ / Pad Type ⁽⁶⁾	During Reset	After Reset	176	208	324	
VDD	Core supply for input or decoupling	_		_	I	1.2 V	1/—	VDD	33, 45, 62, 103, 132, 149, 176	B1, B16, C2, D3, E4, N5, P4, P13, R3, R14, T2, T15	C4, C22, D5, V19, W5, W20, Y4, Y2 ⁻	
VDDE12	External supply input for calibration bus interfaces	_			I	1.8 V - 3.3 V	I/—	VDDE12	-	_	_	
VDDE2 ⁽²³⁾	External supply input for EBI interfaces	_		_	I	1.8 V - 3.3 V	1/—	VDDE2 ⁽²⁴⁾	_	_	M9, M10, N1 P11, W6, W8 Y5, AA4, AA6 AA10, AB3	
VDDE5	External supply input for ENGCLK, CLKOUT and EBI signals DATA[0:15]	_		_	I	1.8 V - 3.3 V	1/—	VDDE5	_	T13	W17, Y18, AA19, AB20	
VDDE-EH	External supply for EBI interfaces	_		_	I	3.0 V - 5 V	I/—	VDDE-EH	—	—	R3, W2	
VDDEH1A ⁽²⁵⁾	I/O Supply Input	_			I	3.3 V - 5.0 V	I/—	VDDEH1A ⁽²⁵⁾	31	_	_	
VDDEH1B ⁽²⁵⁾	I/O Supply Input	_		_	I	3.3 V - 5.0 V	I/—	VDDEH1B ⁽²⁵⁾	41	_	_	
VDDEH1AB ⁽²⁵⁾	I/O Supply Input	_		_	I	3.3 V - 5.0 V	I/—	VDDEH1AB ⁽²⁵⁾	_	K4	H4	
VDDEH4 ⁽²⁶⁾	I/O Supply Input	_		_	I	3.3 V - 5.0 V	I/—	VDDEH4 ⁽²⁶⁾	_	_	_	
VDDEH4A ⁽²⁶⁾	I/O Supply Input	_		_	I	3.3 V - 5.0 V	I / —	VDDEH4A ⁽²⁶⁾	55	_	_	
VDDEH4B ⁽²⁶⁾	I/O Supply Input	_		_	I	3.3 V - 5.0 V	I/—	VDDEH4B ⁽²⁶⁾	74	_	_	

		Р	PCR		I/O) (. lt (5) (Sta	tus ⁽⁷⁾	Package pin #		
Name	Function ⁽¹⁾	A G ⁽²⁾	PA Field (3)	PCR (4)	Туре	Voltage ⁽⁵⁾ / Pad Type ⁽⁶⁾	During Reset	After Reset	176	208	324
VDDEH4AB ⁽²⁶⁾	I/O Supply Input	_		_	I	3.3 V - 5.0 V	I / —	VDDEH4AB ⁽²⁶⁾	_	N9	W14
VDDEH6 ⁽²⁷⁾	I/O Supply Input	_		_	I	3.3 V - 5.0 V	I / —	VDDEH6 ⁽²⁷⁾	_	_	_
VDDEH6A ⁽²⁷⁾	I/O Supply Input	_			I	3.3 V - 5.0 V	I / —	VDDEH6A ⁽²⁷⁾	95	_	_
VDDEH6B ⁽²⁷⁾	I/O Supply Input	_		_	I	3.3 V - 5.0 V	I/—	VDDEH6B ⁽²⁷⁾	110	_	_
VDDEH6AB ⁽²⁷⁾	I/O Supply Input	_			I	3.3 V - 5.0 V	I/—	VDDEH6AB ⁽²⁷⁾	_	F13	H19, U19
VDDEH7	I/O Supply Input	_		_	I	3.3 V - 5.0 V	I/—	VDDEH7	_	D12	D15
VDDEH7A	I/O Supply Input	_		_	I	3.3 V - 5.0 V	I / —	VDDEH7A	125	_	_

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Package pin #

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SPC564A80L7	

P PCR P PCR

Voltage⁽⁵⁾ / I/O PCR PA Function⁽¹⁾ Α Name (4) Pad Type⁽⁶⁾ After Field G⁽²⁾ Type 176 **During Reset** 208 324 (3) Reset I/O Supply Input VDDEH7B 3.3 V - 5.0 V 1/-VDDEH7B 138 ____ 1 ____ A1, A16, A1, A22, B2, B2, B15, B21, C3, C20, C3, C14, D4, D19, J9, D4, D13, J10, J11, J12, 15. J13, K9, K10, G7, G8, 29. K11. K12. G9. 43, K13, K14, L9, G10, 57. L10. L11. L12. 72, H7, H8, L13, L14, H9, H10 90. M11, M12, VSS Ground 1/-VSS 94. Т J7, J8, M13. M14. N9. 96. J9, J10, N10. N12. 108. K7, N13, N14, P9, 115. K8. K9. P10. P12. 127, K10, P13, P14. 133, M16. T21, T22, 140 N4. N13. W4.W19. Y3. P3, P14, Y20, AA2, AA21, AB1, R2, R15, AB22 T1, T16

Status⁽⁷⁾

1. For each pin in the table, each line in the Function column is a separate function of the pin. For all I/O pins the selection of primary pin function or secondary function or GPIO is done in the SIU except where explicitly noted. See the Signal details table for a description of each signal.

The P/A/G column indicates the position a signal occupies in the muxing order for a pin—Primary, Alternate 1, Alternate 2, Alternate 3, or GPIO. Signals are selected by setting the PA field value in the appropriate PCR register in the SIU module. The PA field values are as follows: P - 0b0001, A1 - 0b0010, A2 - 0b0100, A3 - 0b1000, or G - 0b00000. Depending on the register, the PA field size can vary in length. For PA fields having fewer than four bits, remove the appropriate number of leading zeroes from these values.

3. The Pad Configuration Register (PCR) PA field is used by software to select pin function.

4. Values in the PCR No. column refer to registers in the System Integration Unit (SIU). The actual register name is "SIU_PCR" suffixed by the PCR number. For example, PCR[190] refers to the SIU register named SIU_PCR190.

 The VDDE and VDDEH supply inputs are broken into segments. Each segment of slow I/O pins (VDDEH) may have a separate supply in the 3.3 V to 5.0 V range (-10%/+5%). Each segment of fast I/O (VDDE) may have a separate supply in the 1.8 V to 3.3 V range (+/- 10%).

6. See *Table 5* for details on pad types.

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Pinout and signal description

- 7. The Status During Reset pin is sampled after the internal POR is negated. Prior to exiting POR, the signal has a high impedance. Terminology is O output, I input, Up weak pull up enabled, Down weak pull down enabled, Low output driven low, High output driven high. A dash for the function in this column denotes that both the input and output buffer are turned off. The signal name to the left or right of the slash indicates the pin is enabled.
- 8. Output only.
- 9. When used as ETRIG, this pin must be configured as an input. For GPIO it can be configured either as an input or output.
- 10. Maximum frequency is 50 kHz.
- 11. The SIU_PCR219 register is unusual in that it controls pads for two separate device pins: GPIO[219] and MCKO. See the SPC564A80 Microcontroller Reference Manual (SIU chapter) for details.
- 12. Multivoltage pads are automatically configured in low swing mode when a JTAG or Nexus function is selected, otherwise they are high swing.
- 13. On LQFP176 and LBGA208 packages, this pin is tied low internally.
- 14. Nexus multivoltage pads default to 5 V operation until the Nexus module is enabled.
- 15. EVTO should be clamped to 3.3 V to prevent possible damage to external tools that only support 3.3 V.
- 16. Do not connect pin directly to a power supply or ground.
- 17. This signal name is used to support legacy naming.
- 18. During and just after POR negates, internal pull resistors can be enabled, resulting in as much as 4 mA of current draw. The pull resistors are disabled when the system clock propagates through the device.
- 19. For pins AN12-AN15, if the analog features are used the VDDEH7 input pins should be tied to VDDA because that segment must meet the VDDA specification to support analog input function.
- 20. Do not use VRC33 to drive external circuits.
- 21. VDDA0 and VDDA1 are shorted together internally in BGA packages. In the QFP package the two pads are double bonded on one pin called VDDA.
- 22. VSSA0 and VSSA1 are shorted together internally in BGA packages. In the QFP package the two pads are double bonded on one pin called VSSA.
- 23. VDDE2 and VDDE3 are shorted together in all production packages.
- 24. VDDE2 and VDDE3 are shorted together in all production packages.
- 25. VDDEH1A, VDDEH1B, and VDDEH1AB are shorted together in all production packages. The separation of the signal names is present to support legacy naming, however they should be considered as the same signal in this document.
- 26. VDDEH4, VDDEH4A, VDDEH4B, and VDDEH4AB are shorted together in all production packages. The separation of the signal names is present to support legacy naming, however they should be considered as the same signal in this document.
- 27. VDDEH6, VDDEH6A, VDDEH6B, and VDDEH6AB are shorted together in all production packages. The separation of the signal names is present to support legacy naming, however they should be considered as the same signal in this document.
| Pad Type | Name | I/O Voltage Range |
|---------------------------|--------------|---|
| Slow | pad_ssr_hv | 3.0V - 5.5 V |
| Medium | pad_msr_hv | 3.0 V - 5.5 V |
| Fast | pad_fc | 3.0 V - 3.6 V |
| MultiV ^{(1),(2)} | pad_multv_hv | 3.0 V - 5.5 V (high swing mode)
3.0 V - 3.6 V (low swing mode) |
| Analog | pad_ae_hv | 0.0 - 5.5 V |
| LVDS | pad_lo_lv | _ |

Table 5. Pad types

1. Multivoltage pads are automatically configured in low swing mode when a JTAG or Nexus function is selected, otherwise they are high swing.

2. VDDEH7 supply cannot be below 4.5 V when in low-swing mode.

2.5 Signal details

Table 6.Signal details

Signal	Module or Function	Description
CLKOUT	Clock Generation	SPC564A80 clock output for the external/calibration bus interface
ENGCLK	Clock Generation	Clock for external ASIC devices
EXTAL	Clock Generation	Input pin for an external crystal oscillator or an external clock source based on the value driven on the PLLREF pin at reset.
PLLREF	Clock Generation Reset/Configuration	 PLLREF is used to select whether the oscillator operates in xtal mode or external reference mode from reset. PLLREF=0 selects external reference mode. On the 324BGA package, PLLREF is bonded to the ball used for PLLCFG[0] for compatibility with previous devices . For the 176-pin QFP and 208-ball BGA packages: 0: External reference clock is selected. 1: XTAL oscillator mode is selected. For the 324 ball BGA package: If RSTCFG is 0: 0: External reference clock is selected. 1: XTAL oscillator mode is selected. If RSTCFG is 1, XTAL oscillator mode is selected.
XTAL	Clock Generation	Crystal oscillator input
DSPI_B_SCK_LVDS- DSPI_B_SCK_LVDS+	DSPI	LVDS pair used for DSPI_B TSB mode transmission
DSPI_B_SOUT_LVDS- DSPI_B_SOUT_LVDS+	DSPI	LVDS pair used for DSPI_B TSB mode transmission



able 6. Signal details (continued)		
Signal	Module or Function	Description
DSPI_C_SCK_LVDS- DSPI_C_SCK_LVDS+	DSPI	LVDS pair used for DSPI_C TSB mode transmission
DSPI_C_SOUT_LVDS- DSPI_C_SOUT_LVDS+	DSPI	LVDS pair used for DSPI_C TSB mode transmission
PCS_B[0] PCS_C[0] PCS_D[0]	DSPI_B - DSPI_D	Peripheral chip select when device is in master mode—slave select when used in slave mode
PCS_B[1:5] PCS_C[1:5] PCS_D[1:5]	DSPI_B - DSPI_D	Peripheral chip select when device is in master mode—not used in slave mode
SCK_B SCK_C SCK_D	DSPI_B - DSPI_D	DSPI clock—output when device is in master mode; input when in slave mode
SIN_B SIN_C SIN_D	DSPI_B - DSPI_D	DSPI data in
SOUT_B SOUT_C SOUT_D	DSPI_B - DSPI_D	DSPI data out
ADDR[10:31]	EBI	The ADDR[10:31] signals specify the physical address of the bus transaction. The 26 address lines correspond to bits 3-31 of the EBI's 32-bit internal address bus. ADDR[15:31] can be used as Address and Data signals when configured appropriately for a multiplexed external bus. This allows 32-bit data operations, or 16-bit data operations without using DATA[0:15] signals.
ALE	EBI	The Address Latch Enable (ALE) signal is used to demultiplex the address from the data bus. It is asserted while the least significant 16 bits of the address are present in the multiplexed address/data bus.
BDIP	EBI	BDIP is asserted to indicate that the master is requesting another data beat following the current one.
<u>CS</u> [0:3]	EBI	$\overline{\text{CS}}$ x is asserted by the master to indicate that this transaction is targeted for a particular memory bank on the Primary external bus.
DATA[0:31]	EBI	The DATA[0:31] signals contain the data to be transferred for the current transaction.
ŌĒ	EBI	\overline{OE} is used to indicate when an external memory is permitted to drive back read data. External memories must have their data output buffers off when \overline{OE} is negated. \overline{OE} is only asserted for chip-select accesses.

Table 6. Signal details (continued)



Signal	Module or Function	Description
RD_WR	EBI	RD_WR indicates whether the current transaction is a read access or a write access.
TA	EBI	$\overline{\text{TA}}$ is asserted to indicate that the slave has received the data (and completed the access) for a write cycle, or returned data for a read cycle. If the transaction is a burst read, $\overline{\text{TA}}$ is asserted for each one of the transaction beats. For write transactions, $\overline{\text{TA}}$ is only asserted once at access completion, even if more than one write data beat is transferred.
TS	EBI	The Transfer Start signal (\overline{TS}) is asserted by the SPC564A80 to indicate the start of a transfer.
WE[2:3]	EBI	Write enables are used to enable program operations to a particular memory. WE[2:3] are only asserted for write accesses
WE[0:3]/BE[0:3]	EBI	Write enables are used to enable program operations to a particular memory. These signals can also be used as byte enables for read and write operation by setting the WEBS bit in the appropriate EBI Base Register (EBI_BR <i>n</i>). WE[0:3] are only asserted for write accesses. BE[0:3] are asserted for both read and write accesses
eMIOS[0:23]	eMIOS	eMIOS I/O channels
AN[0:39]	eQADC	Single-ended analog inputs for analog-to-digital converter
FCK	eQADC	eQADC free running clock for eQADC SSI.
MA[0:2]	eQADC	These three control bits are output to enable the selection for an external Analog Mux for expansion channels.
REFBYPC	eQADC	Bypass capacitor input
SDI	eQADC	Serial data in
SDO	eQADC	Serial data out
SDS	eQADC	Serial data select
VRH	eQADC	Voltage reference high input
VRL	eQADC	Voltage reference low input
SCI_A_RX SCI_B_RX SCI_C_RX	eSCI_A - eSCI_C	eSCI receive
SCI_A_TX SCI_B_TX SCI_C_TX	eSCI_A - eSCI_C	eSCI transmit
ETPU_A[0:31]	eTPU	eTPU I/O channel

Table 6.Signal details (continued)



Fable 6. Signal details (continued)		
Signal	Module or Function	Description
RCH0_[A:C] RCH1_[A:C] RCH2_[A:C] RCH3_[A:C] RCH4_[A:C] RCH5_[A:C]	eTPU2 Reaction Module	eTPU2 reaction channels. Used to control external actuators, e.g., solenoid control for direct injection systems and valve control in automatic transmissions
TCRCLKA	eTPU2	Input clock for TCR time base
CAN_A_TX CAN_B_TX CAN_C_TX	FlexCan_A - FlexCAN_C	FlexCAN transmit
CAN_A_RX CAN_B_RX CAN_C_RX	FlexCAN_A - FlexCAN_C	FlexCAN receive
FR_A_RX FR_B_RX	FlexRay	FlexRay receive (Channels A, B)
FR_A_TX_EN FR_B_TX_EN	FlexRay	FlexRay transmit enable (Channels A, B)
FR_A_TX FR_B_TX	FlexRay	Flexray transmit (Channels A, B)
JCOMP	JTAG	Enables the JTAG TAP controller.
ТСК	JTAG	Clock input for the on-chip test logic.
TDI	JTAG	Serial test instruction and data input for the on-chip test logic.
TDO	JTAG	Serial test data output for the on-chip test logic.
TMS	JTAG	Controls test mode operations for the on-chip test logic.
EVTI	Nexus	$\overline{\text{EVTI}}$ is an input that is read on the negation of $\overline{\text{RESET}}$ to enable or disable the Nexus Debug port. After reset, the $\overline{\text{EVTI}}$ pin is used to initiate program synchronization messages or generate a breakpoint.
EVTO	Nexus	Output that provides timing to a development tool for a single watchpoint or breakpoint occurrence.
мско	Nexus	MCKO is a free running clock output to the development tools which is used for timing of the MDO and MSEO signals.
MDO[0:11] ⁽¹⁾	Nexus	Trace message output to development tools. This pin also indicates the status of the crystal oscillator clock following a power-on reset, when MDO[0] is driven high until the crystal oscillator clock achieves stability and is then negated.
MSEO[0:1] ⁽¹⁾	Nexus	Output pin—Indicates the start or end of the variable length message on the MDO pins
RDY	Nexus	Nexus Ready Output (\overline{RDY}) is an output that indicates to the development tools the data is ready to be read from or written to the Nexus read/write access registers.

Table 6. Signal details (continued)



Table 6. S	ignal details	(continued)
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Signal	Module or Function	Description
BOOTCFG[0:1]	SIU - Configuration	Two BOOTCFG signals are implemented in SPC564A80 MCUs. The BAM program uses the BOOTCFG0 bit to determine where to read the reset configuration word, and whether to initiate a FlexCAN or eSCI boot. The BOOTCFG1 pin is sampled during the assertion of the RSTOUT signal, and the value is used to update the RSR and the BAM boot mode See the <i>SPC564A80 Microcontroller Reference Manual</i> for more information. The following values are for BOOTCFG[0:1]: 00:Boot from internal flash memory 01:FlexCAN/eSCI boot 10:Boot from external memory using EBI 11:Reserved Note: For the 176-pin QFP and 208-ball BGA packages BOOTCFG[0] is always 0 since the EBI interface is not available.
WKPCFG	SIU - Configuration	The WKPCFG pin is applied at the assertion of the internal reset signal (assertion of RSTOUT), and is sampled 4 clock cycles before the negation of the RSTOUT pin. The value is used to configure whether the eTPU and eMIOS pins are connected to internal weak pull up or weak pull down devices after reset. The value latched on the WKPCFG pin at reset is stored in the Reset Status Register (RSR), and is updated for all reset sources except the Debug Port Reset and Software External Reset.
ETRIG[2:3]	SIU - eQADC Triggers	External signal eTRIGx triggers eQADC CFIFOx
GPIO[206] ETRIG0 (Input)	SIU - eQADC Triggers	External signal eTRIGx triggers eQADC CFIFOx
GPIO[207] ETRIG1 (Input)	SIU - eQADC Triggers	External signal eTRIGx triggers eQADC CFIFOx



Table 6.	Signal	details	(continued))

Signal	Module or Function	Description
ĪRQ[0:5] ĪRQ[7:15]	SIU - External Interrupts	The IRQ[0:15] pins connect to the SIU IRQ inputs. IMUX Select Register 1 is used to select the IRQ[0:15] pins as inputs to the IRQs. See the <i>SPC564A80 Microcontroller Reference Manual</i> for more information.
NMI	SIU - External Interrupts	Non-Maskable Interrupt
GPIO[0:3] GPIO[8:43] GPIO[62:65] GPIO[68:70] GPIO[75:145] GPIO[179:204] GPIO[208:213] GPIO[219]	SIU - GPIO	Configurable general purpose I/O pins. Each GPIO input and output is separately controlled by an 8-bit input (GPDI) or output (GPDO) register. Additionally, each GPIO pins is configured using a dedicated SIU_PCR register. The GPIO pins are generally multiplexed with other I/O pin functions. See The <i>SPC564A80 Microcontroller Reference Manual</i> for more information.
GPIO[244:245]		
RESET	SIU - Reset	The RESET pin is an active low input. The RESET pin is asserted by an external device during a power-on or external reset. The internal reset signal asserts only if the RESET pin asserts for 10 clock cycles. Assertion of the RESET pin while the device is in reset causes the reset cycle to start over. The RESET pin has a glitch detector which detects spikes greater than two clock cycles in duration that fall below the switch point of the input buffer logic of the VDDEH input pins. The switch point lies between the maximum VIL and minimum VIH specifications for the VDDEH input pins.
RSTCFG	SIU - Reset	Used to enable or disable the PLLREF and the BOOTCFG[0:1] configuration signals. 0:Get configuration information from BOOTCFG[0:1] and PLLREF 1:Use default configuration of booting from internal flash with crystal clock source For the 176-pin QFP and 208-ball BGA packages RSTCFG is always 0, so PLLREF and BOOTCFG signals are used.
RSTOUT	SIU - Reset	The RSTOUT pin is an active low output that uses a push/pull configuration. The RSTOUT pin is driven to the low state by the MCU for all internal and external reset sources. There is a delay between initiation of the reset and the assertion of the RSTOUT pin.

1. Do not connect pin directly to a power supply or ground.



Power Segment	Voltage	I/O Pins Powered by Segment
VDDE2	1.8 V - 3.3 V	CS0, CS1, CS2, CS3, RD_WR, BDIP, WE0, WE1, OE, TS, TA
VDDE3	1.8 V - 3.3 V	ADDR12, ADDR13, ADDR14, ADDR15
VDDE5	1.8 V - 3.3 V	DATA0, DATA1, DATA2, DATA3, DATA4, DATA5, DATA6, DATA7, DATA8, DATA9, DATA10, DATA11, DATA12, DATA13, DATA14, DATA15, CLKOUT, ENGCLK
VDDE12	1.8 V - 3.3 V	CAL_CS0, CAL_CS2, CAL_CS3 CAL_ADDR12, CAL_ADDR13, CAL_ADDR14, CAL_ADDR15, CAL_ADDR16, CAL_ADDR17, CAL_ADDR18, CAL_ADDR19, CAL_ADDR20, CAL_ADDR21, CAL_ADDR22, CAL_ADDR23, CAL_ADDR24, CAL_ADDR25, CAL_ADDR26, CAL_ADDR27, CAL_ADDR28, CAL_ADDR29, CAL_ADDR30, CAL_DATA0, CAL_DATA1, CAL_DATA2, CAL_DATA3, CAL_DATA4, CAL_DATA5, CAL_DATA6, CAL_DATA7, CAL_DATA8, CAL_DATA9, CAL_DATA10, CAL_DATA6, CAL_DATA7, CAL_DATA12, CAL_DATA13, CAL_DATA14, CAL_DATA15, CAL_RD_WR, CAL_WE0, CAL_WE1, CAL_OE, CAL_TS
VDDE-EH	3.0 V - 5 V	ADDR16, ADDR17, ADDR18, ADDR19, ADDR20, ADDR21, ADDR22, ADDR23, ADDR24, ADDR25, ADDR26, ADDR27, ADDR28, ADDR29, ADDR30, ADDR31
VDDEH1	3.3 V - 5.0 V	ETPUA10, ETPUA11, ETPUA12, ETPUA13, ETPUA14, ETPUA15, ETPUA16, ETPUA17, ETPUA18, ETPUA19, ETPUA20, ETPUA21, ETPUA22, ETPUA23, ETPUA24, ETPUA25, ETPUA26, ETPUA27, ETPUA28, ETPUA29, ETPUA30, ETPUA31
VDDEH4	3.3 V - 5.0 V	EMIOS0, EMIOS1, EMIOS2, EMIOS3, EMIOS4, EMIOS5, EMIOS6, EMIOS7, EMIOS8, EMIOS9, EMIOS10, EMIOS11, EMIOS12, EMIOS13, EMIOS14, EMIOS15, EMIOS16, EMIOS17, EMIOS18, EMIOS19, EMIOS20, EMIOS21, EMIOS22, EMIOS23, TCRCLKA, ETPUA0, ETPUA1, ETPUA2, ETPUA3, ETPUA4, ETPUA5, ETPUA6, ETPUA7, ETPUA8, ETPUA9, ETPUA0
VDDEH6	3.3 V - 5.0 V	RESET, RSTOUT, PLLREF, PLLCFG1, RSTCFG, BOOTCFG0, BOOTCFG1, WKPCFG, CAN_A_TX, CAN_A_RX, CAN_B_TX, CAN_B_RX, CAN_C_TX, CAN_C_RX, SCI_A_TX, SCI_A_RX, SCI_B_TX, SCI_C_RX, DSPI_B_SCK, DSPI_B_SIN, DSPI_B_SOUT, DSPI_B_PCS[0], DSPI_B_PCS[1], DSPI_B_PCS[2], DSPI_B_PCS[3], DSPI_B_PCS[4], DSPI_B_PCS[5], SCI_B_RX, SCI_C_TX, EXTAL, XTAL
VDDEH7	3.3 V - 5.0 V	EMIOS14, EMIOS 15, GPIO98, GPIO99, GPIO203, GPIO204, GPIO206, GPIO207, GPIO219, EVTI, EVTO, MDO4, MDO5, MDO6, MDO7, MDO8, MDO9, MDO10, MDO11, MSEO0, MSEO1, RDY, TCK, TDI, TDO, TMS, JCOMP, DSPI_A_SCK, DSPI_A_SIN, DSPI_A_SOUT, DSPI_A_PCS[0], DSPI_A_PCS[1], DSPI_A_PCS[4], DSPI_A_PCS[5], AN12-SDS, AN13-SDO, AN14- SDI, AN15-FCK
VDDA	5 V	ANO, AN1, AN2, AN3, AN4, AN5, AN6, AN7, AN8, AN9, AN10, AN11, AN16, AN17, AN18, AN19, AN20, AN21, AN22, AN23, AN24, AN25, AN26, AN27, AN28, AN29, AN30, AN31, AN32, AN33, AN34, AN35, AN36, AN37, AN38, AN39, VRH, VRL, REFBYBC
VRC33 ⁽¹⁾	3.3 V	MCKO, MDO0, MDO1, MDO2, MDO3

Table 7.Power/ground segmentation



Table 7. Power/ground segmentation (continued)

Power Segment	Voltage	I/O Pins Powered by Segment	
	Other Power Segments		
VDDREG	5 V	_	
VRCCTL	—	_	
VDDPLL	1.2 V	_	
VSTBY	0.95–1.2 V (unregulated mode)	_	
VSIBY	2.0–5.5 V (regulated mode)	_	
VSS	—	—	

1. Do not use VRC33 to drive external circuits.



3 Electrical characteristics

This section contains detailed information on power considerations, DC/AC electrical characteristics, and AC timing specifications for the SPC564A80 series of MCUs.

The electrical specifications are preliminary and are from previous designs, design simulations, or initial evaluation. These specifications may not be fully tested or guaranteed at this early stage of the product life cycle, however for production silicon these specifications will be met. Finalized specifications will be published after complete characterization and device qualifications have been completed.

In the tables where the device logic provides signals with their respective timing characteristics, the symbol "CC" for Controller Characteristics is included in the Symbol column.

In the tables where the external system must provide signals with their respective timing characteristics to the device, the symbol "SR" for System Requirement is included in the Symbol column.

3.1 Parameter classification

The electrical parameters shown in this supplement are guaranteed by various methods. To give the customer a better understanding, the classifications listed in *Table 8* are used and the parameters are tagged accordingly in the tables where appropriate.

Classification tag	Tag description
Р	Those parameters are guaranteed during production testing on each individual device.
с	Those parameters are achieved by the design characterization by measuring a statistically relevant sample size across process variations.
т	Those parameters are achieved by design characterization on a small sample size from typical devices under typical conditions unless otherwise noted. All values shown in the typical column are within this category.
D	Those parameters are derived mainly from simulations.

 Table 8.
 Parameter classifications

Note: The classification is shown in the column labeled "C" in the parameter tables where appropriate.



3.2 Maximum ratings

Table 9.	Absolute	maximum	ratings ⁽¹⁾
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Symbol		Devemeter	Conditions	Va	Unit	
Symbol		Parameter	Conditions	min	max	Unit
V _{DD}	SR	1.2 V core supply voltage ⁽²⁾		-0.3	1.32	V
V _{FLASH}	SR	Flash core voltage ^{(3),(4)}		-0.3	3.6	V
V _{STBY}	SR	SRAM standby voltage ⁽⁵⁾		-0.3	6	V
V _{DDPLL}	SR	Clock synthesizer voltage		-0.3	1.32	V
V _{RC33}	SR	Voltage regulator control input voltage ⁽⁴⁾		-0.3	3.6	V
V _{DDA}	SR	Analog supply voltage ⁽⁵⁾	Reference to V _{SSA}	-0.3	5.5	V
V _{DDE}	SR	I/O supply voltage ^{(4),(6)}		-0.3	3.6	V
V _{DDEH}	SR	I/O supply voltage ⁽⁵⁾		-0.3	5.5	V
			V _{DDEH} powered I/O pads	-1.0 ⁽⁸⁾	V _{DDEH} + 0.3 V ⁽⁹⁾	
V _{IN}	SR	DC input voltage ⁽⁷⁾	V _{DDE} powered I/O pads	-1.0 ⁽¹⁰⁾	V _{DDE} + 0.3 V ⁽¹⁰⁾	V
			V _{DDA} powered I/O pads	-1.0	5.5	
V _{DDREG}	SR	Voltage regulator supply voltage		-0.3	5.5	V
V _{RH}	SR	Analog reference high voltage	Reference to VRL	-0.3	5.5	V
$V_{SS} - V_{SSA}$	SR	V _{SS} differential voltage		-0.1	0.1	V
V _{RH} – V _{RL}	SR	V _{REF} differential voltage		-0.3	5.5	V
V _{RL} – V _{SSA}	SR	VRL to V _{SSA} differential voltage		-0.3	0.3	V
V _{SSPLL} – V _{SS}	SR	V _{SSPLL} to V _{SS} differential voltage		-0.1	0.1	V
I _{MAXD}	SR	Maximum DC digital input current ⁽¹¹⁾	Per pin, applies to all digital pins	-3	3	mA
I _{MAXA}	SR	Maximum DC analog input current ⁽¹²⁾	Per pin, applies to all analog pins	_	5	mA



Symbol		Parameter	Conditions	Va	Unit	
Symbol		Parameter	Conditions	min	max	Unit
Тј	SR	Maximum operating temperature range - die junction temperature		-40.0	150.0	°C
T _{STG}	SR	Storage temperature range		-55.0	150.0	°C
T _{SDR}	SR	Maximum solder temperature ⁽¹³⁾		_	260.0	°C
MSL	SR	Moisture sensitivity level ⁽¹⁴⁾			3	

Table 9. Absolute maximum ratings⁽¹⁾ (continued)

1. Functional operating conditions are given in the DC electrical specifications. Absolute maximum ratings are stress ratings only, and functional operation at the maxima is not guaranteed. Stress beyond the listed maxima may affect device reliability or cause permanent damage to the device.

2. Allowed 2 V for 10 hours cumulative time, remaining time at 1.2 V +10%.

- The V_{FLASH} supply is connected to V_{RC33} in the package substrate. This specification applies to calibration package devices only.
- 4. Allowed 5.3 V for 10 hours cumulative time, remaining time at 3.3 V +10%.
- 5. Allowed 5.9 V for 10 hours cumulative time, remaining time at 5 V +10%.
- 6. All functional non-supply I/O pins are clamped to V_{SS} and $V_{\text{DDE}},$ or $V_{\text{DDEH}}.$
- 7. AC signal overshoot and undershoot of up to 2.0 V of the input voltages is permitted for an accumulative duration of 60 hours over the complete lifetime of the device (injection current not limited for this duration).
- 8. Internal structures hold the voltage greater than -1.0 V if the injection current limit of 2 mA is met.
- Internal structures hold the input voltage less than the maximum voltage on all pads powered by V_{DDEH} supplies, if the maximum injection current specification is met (2 mA for all pins) and V_{DDEH} is within the operating voltage specifications.
- 10. Internal structures hold the input voltage less than the maximum voltage on all pads powered by V_{DDE} supplies, if the maximum injection current specification is met (2 mA for all pins) and V_{DDE} is within the operating voltage specifications.
- 11. Total injection current for all pins (including both digital and analog) must not exceed 25 mA.
- 12. Total injection current for all analog input pins must not exceed 15 mA.
- 13. Solder profile per IPC/JEDEC J-STD-020D.
- 14. Moisture sensitivity per JEDEC test method A112.

3.3 Thermal characteristics

Table 10. Thermal characteristics for 176-pin QFP⁽¹⁾

Symbo	Symbol		Parameter	Conditions	Value	Unit
R_{\thetaJA}	CC	D	Junction-to-Ambient, Natural Convection ⁽²⁾	Single layer board - 1s	38	°C/W
R_{\thetaJA}	СС	D	Junction-to-Ambient, Natural Convection ⁽²⁾ Four layer board - 2s2p		31	°C/W
$R_{ ext{ heta}JMA}$	СС	D	Junction-to-Moving-Air, Ambient ⁽²⁾ 200 ft./min., single layer board - 1s		30	°C/W
$R_{ ext{ heta}JMA}$	СС	D	Junction-to-Moving-Air, Ambient ⁽²⁾	at 200 ft./min., four layer board - 2s2p	25	°C/W
$R_{\theta JB}$	СС	D	Junction-to-Board ⁽³⁾		20	°C/W



Sym	Symbol		Symbol		Parameter	Conditions	Value	Unit
R _{0JCtop}	CC	D	Junction-to-Case ⁽⁴⁾		5	°C/W		
Ψ_{JT}	сс	D	Junction-to-Package Top, Natural Convection ⁽⁵⁾		2	°C/W		

Table 10. Thermal characteristics for 176-pin QFP⁽¹⁾ (continued)

1. Thermal characteristics are targets based on simulation that are subject to change per device characterization.

2. Junction-to-Ambient Thermal Resistance determined per JEDEC JESD51-3 and JESD51-6. Thermal test board meets JEDEC specification for this package.

3. Junction-to-Board thermal resistance determined per JEDEC JESD51-8. Thermal test board meets JEDEC specification for the specified package.

4. Junction-to-Case at the top of the package determined using MIL-STD 883 Method 1012.1. The cold plate temperature is used for the case temperature. Reported value includes the thermal resistance of the interface layer.

 Thermal characterization parameter indicating the temperature difference between the package top and the junction temperature per JEDEC JESD51-2. When Greek letters are not available, the thermal characterization parameter is written as Psi-JT.

Symb	Symbol C		Parameter	Conditions	Value	Unit
$R_{ hetaJA}$	сс	D	D Junction-to-Ambient, Natural Convection ^{(2),(3)} One layer board - 1s		39	°C/W
$R_{ hetaJA}$	сс	D	Junction-to-Ambient, Natural Convection ^{(2),(4)} Four layer board - 2s2p		24	°C/W
R _{0JMA}	сс	D	Junction-to-Moving-Air, Ambient ^{(2),(4)} at 200 ft./min., one layer board		31	°C/W
$R_{ hetaJMA}$	сс	D	Junction-to-Moving-Air, Ambient ^{(2),(4)}	at 200 ft./min., four layer board 2s2p	20	°C/W
$R_{\theta JB}$	СС	D	Junction-to-board ⁽⁵⁾	Four layer board - 2s2p	13	°C/W
$R_{ ext{ heta}JC}$	СС	D	Junction-to-case ⁽⁶⁾		6	°C/W
Ψ_{JT}	сс	D	Junction-to-package top natural convection ⁽⁷⁾		2	°C/W

Table 11. Thermal characteristics for 208-pin LBGA⁽¹⁾

1. Thermal characteristics are targets based on simulation that are subject to change per device characterization.

 Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance.

3. Per SEMI G38-87 and JEDEC JESD51-2 with the single-layer board horizontal.

4. Per JEDEC JESD51-6 with the board horizontal.

5. Thermal resistance between the die and the printed circuit board per JEDEC JESD51-8. Board temperature is measured on the top surface of the board near the package.

6. Indicates the average thermal resistance between the die and the case top surface as measured by the cold plate method (MIL SPEC-883 Method 1012.1) with the cold plate temperature used for the case temperature.

 Thermal characterization parameter indicating the temperature difference between package top and the junction temperature per JEDEC JESD51-2. When Greek letters are not available, the thermal characterization parameter is written as Psi-JT.



	-	-				
Symbo	ol	С	Parameter	Conditions	Value	Unit
$R_{ hetaJA}$	CC	D	Junction-to-Ambient, Natural Convection ⁽²⁾	Single layer board - 1s	31	°C/W
$R_{ hetaJA}$	СС	D	Junction-to-Ambient, Natural Convection ⁽²⁾	Four layer board - 2s2p	23	°C/W
R_{\thetaJMA}	СС	D	Junction-to-Moving-Air, Ambient ⁽²⁾	at 200 ft./min., single layer board	23	°C/W
R_{\thetaJMA}	СС	D	Junction-to-Moving-Air, Ambient ⁽²⁾	at 200 ft./min., four layer board 2s2p	17	°C/W
$R_{\theta JB}$	СС	D	Junction-to-Board ⁽³⁾		11	°C/W
$R_{\theta JCtop}$	СС	D	Junction-to-Case ⁽⁴⁾		7	°C/W
Ψ_{JT}	СС	D	Junction-to-Package Top, Natural Convection ⁽⁵⁾		2	°C/W

 Table 12.
 Thermal characteristics for 324-pin PBGA⁽¹⁾

1. Thermal characteristics are targets based on simulation that are subject to change per device characterization.

2. Junction-to-Ambient Thermal Resistance determined per JEDEC JESD51-3 and JESD51-6. Thermal test board meets JEDEC specification for this package.

3. Junction-to-Board thermal resistance determined per JEDEC JESD51-8. Thermal test board meets JEDEC specification for the specified package.

4. Junction-to-Case at the top of the package determined using MIL-STD 883 Method 1012.1. The cold plate temperature is used for the case temperature. Reported value includes the thermal resistance of the interface layer.

 Thermal characterization parameter indicating the temperature difference between the package top and the junction temperature per JEDEC JESD51-2. When Greek letters are not available, the thermal characterization parameter is written as Psi-JT.

3.3.1 General notes for specifications at maximum junction temperature

An estimation of the chip junction temperature, T_J, can be obtained from the equation:

Equation 1 $T_J = T_A + (R_{\theta JA} * P_D)$

where:

 T_A = ambient temperature for the package (^oC)

 $R_{\theta,JA}$ = junction-to-ambient thermal resistance (^oC/W)

 P_D = power dissipation in the package (W)

The thermal resistance values used are based on the JEDEC JESD51 series of standards to provide consistent values for estimations and comparisons. The difference between the values determined for the single-layer (1s) board compared to a four-layer board that has two signal layers, a power and a ground plane (2s2p), demonstrate that the effective thermal resistance is not a constant. The thermal resistance depends on the:

- Construction of the application board (number of planes)
- Effective size of the board which cools the component
- Quality of the thermal and electrical connections to the planes
- Power dissipated by adjacent components

Connect all the ground and power balls to the respective planes with one via per ball. Using fewer vias to connect the package to the planes reduces the thermal performance. Thinner planes also reduce the thermal performance. When the clearance between the vias leave the planes virtually disconnected, the thermal performance is also greatly reduced.



As a general rule, the value obtained on a single-layer board is within the normal range for the tightly packed printed circuit board. The value obtained on a board with the internal planes is usually within the normal range if the application board has:

- One oz. (35 micron nominal thickness) internal planes
- Components are well separated
- Overall power dissipation on the board is less than 0.02 W/cm²

The thermal performance of any component depends on the power dissipation of the surrounding components. In addition, the ambient temperature varies widely within the application. For many natural convection and especially closed box applications, the board temperature at the perimeter (edge) of the package is approximately the same as the local air temperature near the device. Specifying the local ambient conditions explicitly as the board temperature provides a more precise description of the local ambient conditions that determine the temperature of the device.

At a known board temperature, the junction temperature is estimated using the following equation:

Equation 2 T_J = T_B + ($R_{\theta JB} * P_D$)

where:

 T_B = board temperature for the package perimeter (^oC)

 $R_{\theta JB}$ = junction-to-board thermal resistance (°C/W) per JESD51-8S

 P_D = power dissipation in the package (W)

When the heat loss from the package case to the air does not factor into the calculation, an acceptable value for the junction temperature is predictable. Ensure the application board is similar to the thermal test condition, with the component soldered to a board with internal planes.

The thermal resistance is expressed as the sum of a junction-to-case thermal resistance plus a case-to-ambient thermal resistance:

Equation 3 $R_{\theta JA} = R_{\theta JC} + R_{\theta CA}$

where:

 $R_{\theta,JA}$ = junction-to-ambient thermal resistance (^oC/W)

 $R_{\theta JC}$ = junction-to-case thermal resistance (^oC/W)

 $R_{\theta CA}$ = case to ambient thermal resistance (^oC/W)

 $R_{\theta JC}$ is device related and is not affected by other factors. The thermal environment can be controlled to change the case-to-ambient thermal resistance, $R_{\theta CA}$. For example, change the air flow around the device, add a heat sink, change the mounting arrangement on the printed circuit board, or change the thermal dissipation on the printed circuit board surrounding the device. This description is most useful for packages with heat sinks where 90% of the heat flow is through the case to heat sink to ambient. For most packages, a better model is required.

A more accurate two-resistor thermal model can be constructed from the junction-to-board thermal resistance and the junction-to-case thermal resistance. The junction-to-case thermal resistance describes when using a heat sink or where a substantial amount of heat is dissipated from the top of the package. The junction-to-board thermal resistance describes the thermal performance when most of the heat is conducted to the printed circuit



board. This model can be used to generate simple estimations and for computational fluid dynamics (CFD) thermal models.

To determine the junction temperature of the device in the application on a prototype board, use the thermal characterization parameter (Ψ_{JT}) to determine the junction temperature by measuring the temperature at the top center of the package case using the following equation:

Equation 4 $T_J = T_T + (\Psi_{JT} \times P_D)$

where:

 T_T = thermocouple temperature on top of the package (^oC)

 Ψ_{JT} = thermal characterization parameter (^oC/W)

 P_D = power dissipation in the package (W)

The thermal characterization parameter is measured in compliance with the JESD51-2 specification using a 40-gauge type T thermocouple epoxied to the top center of the package case. Position the thermocouple so that the thermocouple junction rests on the package. Place a small amount of epoxy on the thermocouple junction and approximately 1 mm of wire extending from the junction. Place the thermocouple wire flat against the package case to avoid measurement errors caused by the cooling effects of the thermocouple wire.

References:

Semiconductor Equipment and Materials International

3081 Zanker Road San Jose, CA 95134 USA (408) 943-6900

MIL-SPEC and EIA/JESD (JEDEC) specifications are available from Global Engineering Documents at 800-854-7179 or 303-397-7956.

JEDEC specifications are available on the WEB at http://www.jedec.org.

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- G. Kromann, S. Shidore, and S. Addison, "Thermal Modeling of a PBGA for Air-Cooled Applications", Electronic Packaging and Production, pp. 53-58, March 1998.
- B. Joiner and V. Adams, "Measurement and Simulation of Junction to Board Thermal Resistance and Its Application in Thermal Modeling," Proceedings of SemiTherm, San Diego, 1999, pp. 212-220.



3.4 EMI (electromagnetic interference) characteristics

Symbol	Parameter	Conditions	Clocks	Frequency Range	Level (Max)	Unit	
				150 kHz – 50 MHz	20		
			16 MHz crystal	50 – 150 MHz	20	dBµV	
		V _{DDREG} = 5.25 V;	40 MHz bus	150 – 500 MHz	26		
	W	$T_A = 25 °C$ 150 kHz – 30 MHz RBW 9 kHz, Step	25 °C modulation	500 – 1000 MHz	26		
				IEC Level	К	—	
Radiated emissions,				SAE Level	3	_	
electric field	V _{RE_TEM}	Size 5 kHz) MHz – 1 GHz - 16 MHz crystal	150 kHz– 50 MHz	13		
		30 MHz – 1 GHz - RBW 120 kHz,		50 – 150 MHz	13	dBµV	
		Step Size 80 kHz	40 MHz bus ± 2% PLL	150 – 500 MHz	11		
			frequency	500 – 1000 MHz	13		
			modulation	IEC Level	L	_	
				SAE Level	2	_	

Table 13. EMI Testing Specifications⁽¹⁾

1. EMI testing and I/O port waveforms per SAE J1752/3 issued 1995-03 and IEC 61967-2.

3.5 Electrostatic discharge (ESD) characteristics

Table 14.ESD ratings(1),(2)

Symbol		Parameter	Conditions	Value	Unit
	SR	ESD for Human Body Model (HBM)	—	2000	V
R1	SR	HBM circuit description	—	1500	Ω
С	SR		_	100	рF
	6 D	SR ESD for field induced charge Model (FDCM)	All pins	500	V
	Sh		Corner pins	750	v
	SR		Positive pulses (HBM)	1	—
	эп	Number of pulses per pin	Negative pulses (HBM)	1	—
_	SR	Number of pulses	—	1	

1. All ESD testing is in conformity with CDF-AEC-Q100 Stress Test Qualification for Automotive Grade Integrated Circuits.



Device failure is defined as: "If after exposure to ESD pulses, the device does not meet the device specification requirements, which includes the complete DC parametric and functional testing at room temperature and hot temperature."

3.6 Power management control (PMC) and power on reset (POR) electrical specifications

ID	Nam	Name		Parameter	Min	Тур	Max	Unit
1	Jtemp	SR	—	Junction temperature	-40	27	150	°C
2	Vddreg	SR	—	PMC 5 V supply voltage V _{DDREG}	4.75	5	5.25	V
3	Vdd	SR		Core supply voltage 1.2 V V _{DD} when external regulator is used without disabling the internal regulator (PMC unit turned on, LVI monitor active) ⁽¹⁾	1.26 ⁽²⁾	1.3	1.32	v
3a	_	SR		Core supply voltage 1.2 V V _{DD} when external regulator is used with a disabled internal regulator (PMC unit turned-off, LVI monitor disabled)	1.14	1.2	1.32	v
4	lvdd	SR	_	Voltage regulator core supply maximum required DC output current	445	_	_	mA
5	Vdd33	SR		Regulated 3.3 V supply voltage when external regulator is used without disabling the internal regulator (PMC unit turned-on, internal 3.3V regulator enabled, LVI monitor active) ⁽³⁾	3.3	3.45	3.6	v
5a	_	SR		Regulated 3.3 V supply voltage when external regulator is used with a disabled internal regulator (PMC unit turned-off, LVI monitor disabled)	3	3.3	3.6	v
6	_	SR		Voltage regulator 3.3 V supply maximum required DC output current	80	_	_	mA

Table 15. PMC Operating Conditions and External Regulators Supply Voltage

1. An internal regulator controller can be used to regulate core supply.

2. The minimum supply required for the part to exit reset and enter in normal run mode is 1.28 V.

3. An internal regulator can be used to regulate 3.3 V supply.

Table 16. PMC Electrical Characteristics

ID	Name	Name		Parameter	Min	Тур	Max	Unit	Notes
1	VBG	сс	с	Nominal bandgap voltage reference	_	1.219	_	V	
1a	—	сс	Р	Untrimmed bandgap reference voltage	VBG - 7%	VBG	Vbg + 6%	V	
1b	_	сс	Р	Trimmed bandgap reference voltage (5 V, 27 °C)	VBG -10mV	VBG	VBG + 10mV	V	
1c	_	сс	с	Bandgap reference temperature variation		100	_	ppm/°C	
1d	_	сс	с	Bandgap reference supply voltage variation	_	3000	_	ppm/V	



ID	Nam	е		Parameter	Min	Тур	Max	Unit	Notes
2	Vdd	сс	с	Nominal V _{DD} core supply internal regulator target DC output voltage ⁽¹⁾	_	1.28	_	v	
2a		сс	Р	Nominal V _{DD} core supply internal regulator target DC output voltage variation at power-on reset	Vdd - 6%	Vdd	Vdd + 10%	V	
2b	_	сс	Р	Nominal V _{DD} core supply internal regulator target DC output voltage variation after power-on reset	Vdd - 10% ⁽²⁾	Vdd	Vdd + 3%	v	
2c	_	СС	С	Trimming step Vdd	—	20	—	mV	
2d	lvrcctl	сс	с	Voltage regulator controller for core supply maximum DC output current	20	_	_	mA	
3	Lvi1p2	сс	с	Nominal LVI for rising core supply ⁽³⁾	—	1.160	_	V	
За	_	сс	с	Variation of LVI for rising core supply at power-on reset	1.120	1.200	1.280	v	See note ⁽⁴⁾
3b	_	сс	с	Variation of LVI for rising core supply after power-on reset	Lvi1p2 - 3%	Lvi1p2	Lvi1p2 + 3%	v	See note ⁽⁴⁾
3c	_	сс	с	Trimming step LVI core supply	—	20	—	mV	
3d	Lvi1p2_h	СС	С	LVI core supply hysteresis	—	40	—	mV	
4	Por1.2V_r	СС	С	POR 1.2 V rising	_	0.709	—	V	
4a		сс	С	POR 1.2 V rising variation	Por1.2V_r - 35%	Por1.2V_r	Por1.2V_r+ 35%	v	
4b	Por1.2V_f	СС	С	POR 1.2 V falling	—	0.638	—	V	
4c	—	сс	с	POR 1.2 V falling variation	Por1.2V_f - 35%	Por1.2V_f	Por1.2V_f + 35%	v	
5	Vdd33	сс	с	Nominal 3.3 V supply internal regulator DC output voltage	_	3.39	_	v	
5a	_	сс	Р	Nominal 3.3 V supply internal regulator DC output voltage variation at power- on reset	Vdd33 - 8.5%	Vdd33	Vdd3 + 7%	v	See note ⁽⁵⁾
5b	_	сс	Р	Nominal 3.3 V supply internal regulator DC output voltage variation power-on reset	Vdd33 - 7.5%	Vdd33	Vdd33 + 7%	v	With internal load up to Idd3p3

Table 16.	PMC Electrical	Characteristics	(continued)
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ID	Namo	Ð		Parameter	Min	Тур	Max	Unit	Notes
5c	_	сс	D	Voltage regulator 3.3 V output impedance at maximum DC load	_	_	2	Ω	
5d	ldd3p3	сс	Ρ	Voltage regulator 3.3 V maximum DC output current (internal regulator enabled) ⁽⁶⁾	80 ⁽⁷⁾	_	_	mA	
5e	Vdd33 ILim	сс	с	Voltage regulator 3.3 V DC current limit	_	130	—	mA	
6	Lvi3p3	сс	С	Nominal LVI for rising 3.3 V supply	_	3.090	_	V	The Lvi3p3 specs are also valid for the Vddeh LVI
6a	_	сс	с	Variation of LVI for rising 3.3 V supply at power-on reset	Lvi3p3 - 6%	Lvi3p3	Lvi3p3 + 6%	V	See note ⁽⁸⁾
6b		сс	с	Variation of LVI for rising 3.3 V supply after power-on reset	Lvi3p3 - 3%	Lvi3p3	Lvi3p3 + 3%	V	See note ⁽⁸⁾
6c	_	СС	С	Trimming step LVI 3.3 V		20	—	mV	
6d	Lvi3p3_h	СС	С	LVI 3.3 V hysteresis		60	—	mV	
7	Por3.3V_r	сс	с	Nominal POR for rising 3.3 V supply	_	2.07	_	V	The 3.3V POR specs are also valid for the V _{DDEH} POR
7a	_	сс	с	Variation of POR for rising 3.3 V supply	Por3.3V_r- 35%	Por3.3V_r	Por3.3V_r + 35%	V	
7b	Por3.3V_f	сс	с	Nominal POR for falling 3.3 V supply	_	1.95	_	V	
7c		сс	с	Variation of POR for falling 3.3 V supply	Por3.3V_f - 35%	Por3.3V_f	Por3.3V_f + 35%	V	
8	Lvi5p0	сс	с	Nominal LVI for rising 5 V V _{DDREG} supply	_	4.290	—	V	
8a	_	сс	с	Variation of LVI for rising 5 V V _{DDREG} supply at power-on reset	Lvi5p0 - 6%	Lvi5p0	Lvi5p0 + 6%	V	
8b	_	сс	с	Variation of LVI for rising 5 V V _{DDRE} G supply power-on reset	Lvi5p0 - 3%	Lvi5p0	Lvi5p0 + 3%	V	
8c		СС	С	Trimming step LVI 5 V		20	—	mV	
8d	Lvi5p0_h	СС	С	LVI 5 V hysteresis	_	60	_	mV	

 Table 16.
 PMC Electrical Characteristics (continued)



ID	Name	е		Parameter	Min	Тур	Max	Unit	Notes
9	Por5V_r	сс		Nominal POR for rising 5 V V _{DDREG} supply	_	2.67	_	V	
9a	_	сс	С	Variation of POR for rising 5 V V _{DDREG} supply	Por5V_r - 35%	Por5V_r	Por5V_r + 50%	V	
9b	Por5V_f	сс		Nominal POR for falling 5 V V _{DDREG} supply	_	2.47	_	V	
9c		сс	С	Variation of POR for falling 5 V V _{DDREG} supply	Por5V_f - 35%	Por5V_f	Por5V_f + 50%	V	

 Table 16.
 PMC Electrical Characteristics (continued)

1. Using external ballast transistor.

- 2. Min range is extended to 10% since Lvi1p2 is reprogrammed from 1.2 V to 1.16 V after power-on reset.
- 3. LVI for falling supply is calculated as LVI rising LVI hysteresis.
- Lvi1p2 tracks DC target variation of internal Vdd regulator. Minimum and maximum Lvi1p2 correspond to minimum and maximum Vdd DC target respectively.
- 5. Minimum loading (<10 mA) for reading trim values from flash, powering internal RC oscillator, and IO consumption during POR.
- 6. No external load is allowed, except for use as a reference for an external tool.
- 7. This value is valid only when the internal regulator is bypassed. When the internal regulator is enabled, the maximum external load allowed on the Nexus pads is 30 pF at 40 MHz.
- 8. Lvi3p3 tracks DC target variation of internal Vdd33 regulator. Minimum and maximum Lvi3p3 correspond to minimum and maximum Vdd33 DC target respectively.

3.6.1 Regulator Example

In designs where the SPC564A80 microcontroller's internal regulators are used, a ballast is required for generation of the 1.2 V internal supply. No ballast is required when an external 1.2 V supply is used.





VRCCTL capacitor and resistor is required

Figure 8. Core voltage regulator controller external components preferred configuration

Table 17.	SPC564A80 External network specification
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External Network Parameter	Min	Тур	Max	Comment
T1				NJD2873 or BCP68 only
Cb	1.1 μF	2.2μF	2.97µF	X7R,-50%/+35%
Се	3*2.35μF+5μF	3*4.7μF+10μF	3*6.35µF+13.5µF	X7R, -50%/+35%
Equivalent ESR of Ce capacitors	5mΩ		50mΩ	
Cd	4*50nF	4*100nF	4*135nF	X7R, -50%/+35%
Rb	9Ω	10Ω	11Ω	+/-10%
Re	0.252Ω	0.280Ω	0.308Ω	+/-10%
Creg		10µF		It depends on external Vreg.
Сс	5μF	10µF	13.5μF	X7R, -50%/+35%
Rc	1.1Ω		5.6Ω	May or may not be required. It depends on the allowable power dissipation of T1.



3.6.2 Recommended power transistors

The following NPN transistors are recommended for use with the on-chip voltage regulator controller: ON SemiconductorTM BCP68T1 or NJD2873 as well as Philips SemiconductorTM BCP68. The collector of the external transistor is preferably connected to the same voltage supply source as the output stage of the regulator.

Symbol	Parameter	Value	Unit
h _{FE} (β)	DC current gain (Beta)	60 - 550	_
P _D	Absolute minimum power dissipation	>1.0 (1.5 preferred)	W
I _{CMaxDC}	Minimum peak collector current	1.0	А
VCE _{SAT}	Collector-to-emitter saturation voltage	200 – 600 ⁽¹⁾	mV
V _{BE}	Base-to-emitter voltage	0.4 – 1.0	V

 Table 18.
 Recommended operating characteristics

1. Adjust resistor at bipolar transistor collector for 3.3 V/5.0 V to avoid VCE < VCE_{SAT}.

3.7 Power up/down sequencing

There is no power sequencing required among power sources during power up and power down, in order to operate within specification.

Although there are no power up/down sequencing requirements to prevent issues such as latch-up or excessive current spikes the state of the I/O pins during power up/down varies according to *Table 19* for all pins with fast pads, and *Table 20* for all pins with medium, slow, and multi-voltage pads.

 Table 19.
 Power sequence pin states (fast pads)

V _{DDE}	V _{RC33}	V _{DD}	Pad State
LOW	х	х	LOW
V _{DDE}	LOW	Х	HIGH
V _{DDE}	V _{RC33}	LOW	HIGH IMPEDANCE
V _{DDE}	V _{RC33}	V _{DD}	FUNCTIONAL

Table 20.	Power sequence pin states (medium, slow, and multi-voltage pads)
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V _{DDEH}	V _{DD}	Pad State
LOW	Х	LOW
V _{DDEH}	LOW	HIGH IMPEDANCE
V _{DDEH}	V _{DD}	FUNCTIONAL



3.8 DC electrical specifications

Table 21. DC electrical specification

Quarter			Baurantan	O a malibilita ma		Value		
Symbol		С	Parameter	Conditions	min	typ	max	Unit
V _{DD}	SR	—	Core supply voltage	_	1.14		1.32	V
V _{DDE}	SR	—	I/O supply voltage	_	1.62		3.6	V
V _{DDEH}	SR	—	I/O supply voltage	_	3.0		5.25	V
V _{DDE-EH}	SR	—	I/O supply voltage	—	3.0		5.25	V
V _{RC33}	SR	_	3.3 V regulated voltage ⁽¹⁾	_	3.0	_	3.6	V
V _{DDA}	SR	—	Analog supply voltage		4.75 ⁽²⁾	_	5.25	V
V _{INDC}	SR	—	Analog input voltage	_	V _{SSA} -0.3		V _{DDA} +0.3	V
$V_{SS} - V_{SSA}$	SR	—	V _{SS} differential voltage	_	-100	_	100	mV
V _{RL}	SR		Analog reference low voltage	_	V _{SSA}		V _{SSA} +0.1	V
V _{RL} – V _{SSA}	SR	—	VRL differential voltage		-100	_	100	mV
V _{RH}	SR	_	Analog reference high voltage	_	V _{DDA} -0.1	_	V _{DDA}	V
V _{RH} – V _{RL}	SR	_	V _{REF} differential voltage	_	4.75	_	5.25	V
V _{DDF}	SR	_	Flash operating voltage ⁽³⁾	_	1.14	_	1.32	V
V _{FLASH} ⁽⁴⁾	SR	—	Flash read voltage	_	3.0		3.6	V
N			SRAM standby voltage	Unregulated mode	0.95		1.2	V
V _{STBY}	SR	-	Keep-out Range: 1.2V– 2V	Regulated mode	2.0		V _{DDA} +0.3 100 V _{SSA} +0.1 100 V _{DDA} 5.25 1.32 3.6 1.2 5.5 5.25 1.32 1.32 1.32 1.32 1.32	V
V _{DDREG}	SR	_	Voltage regulator supply voltage	_	4.75	_	5.25	V
V _{DDPLL}	SR	_	Clock synthesizer operating voltage	_	1.14	_	1.32	V
V _{SSPLL} – V _{SS}	SR	_	V _{SSPLL} to V _{SS} differential voltage	_	-100	_	100	mV
V	<u> </u>	с	Slow/medium I/O pad	Hysteresis enabled	V _{SS} -0.3		0.35*V _{DDEH}	V
V _{IL_S}	СС	Р	input low voltage	Hysteresis disabled	V _{SS} -0.3	_	5.25 1.32 3.6 1.2 5.5 5.25 1.32 1.32 1.00	V



0	Symbol		Demonster	O an disting a		Value		11	
Symbo)	С	Parameter	Conditions	min	typ	max	Unit	
N	сс	с	Fast pad I/O input low	Hysteresis enabled	V _{SS} -0.3	_	0.35*V _{DDE}	V	
V _{IL_F}		Ρ	voltage	Hysteresis disabled	V _{SS} -0.3	_	0.40*V _{DDE}	V	
M	сс	с	Multi-voltage I/O pad input low voltage in	Hysteresis enabled	V _{SS} -0.3	_	0.8		
V _{IL_LS}		Р	Low-swing- mode ^{(5),(6),(7),(8)}	Hysteresis disabled	V _{SS} -0.3	_	1.1	V	
N	сс	с	Multi-voltage pad I/O input low voltage in	Hysteresis enabled	V _{SS} -0.3	_	0.35 V _{DDEH}		
V _{IL_HS}		Р	high-swing-mode	Hysteresis disabled	V _{SS} -0.3	_	0.4 V _{DDEH}	V	
V	сс	с	Slow/medium pad I/O	Hysteresis enabled	0.65 V _{DDEH}	_	V _{DDEH} +0.3	V	
V _{IH_S}		Р	input high voltage ⁽⁹⁾	Hysteresis disabled	0.55 V _{DDEH}	_	V _{DDEH} +0.3		
N		с	Fast I/O input high	Hysteresis enabled	0.65 V _{DDE}	_	V _{DDE} +0.3	v	
V _{IH_F}	СС	Р	voltage	Hysteresis disabled	0.58 V _{DDE}	_	V _{DDE} +0.3	v	
N	сс	с	Multi-voltage pad I/O input high voltage in	Hysteresis enabled	2.5	_	V _{DDEH} +0.3	V	
V _{IH_LS}		Р	low-swing- mode ^{(5),(6),(7),(8)}	Hysteresis disabled	2.2	_	V _{DDEH} +0.3	v	
N	сс	с	Multi-voltage I/O input	Hysteresis enabled	0.65 V _{DDEH}	_	V _{DDEH} +0.3	V	
V _{IH_HS}		Ρ	swing-mode	high voltage in high- swing-mode Hysteresis disabled 0.55 V _{DDEH}		_	V _{DDEH} +0.3	v	
V _{OL_S}	сс	Ρ	Slow/medium pad I/O output low voltage ⁽⁹⁾		_	_	0.2*V _{DDEH}	V	
V _{OL_F}	сс	Ρ	Fast I/O output low voltage ⁽⁹⁾		_	_	0.2*V _{DDE}	v	
V _{OL_LS}	сс	Р	Multi-voltage pad I/O output low voltage in low-swing mode ^{(5),(6),(7),(8),(9)}		_		0.6	V	

Table 21.	DC electrical specifications (continued)
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Cumha	Symbol		hal		mh e l		0h.e.l		Downstow	Canditiana		Value		11
Symbol		С	Parameter Conditions		min	typ	max	Unit						
V _{OL_HS}	сс	Ρ	Multi-voltage pad I/O output low voltage in high-swing mode ⁽⁹⁾		_	_	0.2*V _{DDEH}	v						
V _{OH_S}	сс	Р	Slow/medium pad I/O output high voltage ⁽⁹⁾		0.8 V _{DDEH}	_	_	v						
V _{OH_F}	сс	Р	Fast pad I/O output high voltage ⁽⁹⁾		0.8 V _{DDE}	_	_	v						
V _{OH_LS}	сс	Ρ	Multi-voltage pad I/O output high voltage in low-swing mode ^{(5),(6),(7),(8)}	I _{OH_LS} = 0.5 mA	2.1	3.1	3.7	V						
V _{OH_HS}	сс	Ρ	Multi-voltage pad I/O output high voltage in high-swing mode ⁽⁹⁾		0.8 V _{DDEH}	_	_	v						
V _{HYS_S}	сс	с	Slow/medium/multi- voltage I/O input hysteresis	_	0.1 * V _{DDEH}	_	_	v						
V _{HYS_F}	СС	С	Fast I/O input hysteresis	—	0.1 * V _{DDE}	—	—	V						
V _{HYS_LS}	сс	с	Low-Swing-Mode Multi- Voltage I/O Input Hysteresis	hysteresis enabled	0.25	_	_	v						
		Р		V _{DD} at 1.32 V at 80 MHz	—		380	mA						
I _{DD} +I _{DDPLL}	сс	Р	Operating current 1.2 V supplies	V _{DD} at 1.32V at 120 MHz	—		400	mA						
		Р		V _{DD} at 1.32V at 150 MHz	—		445	mA						
		т	Operating current 0.95- 1.2 V	V _{STBY} at 55 ⁰C	—	35	100	μA						
'DDSTBY	I _{DDSTBY} CC		Operating current 2– 5.5 V	V _{STBY} at 55 °C	—	45	110	μA						
		Ρ	Operating current 0.95- 1.2 V	V _{STBY} 27 °C		25	90	μA						
I _{DDSTBY27}	CC	Р	Operating current 2- 5.5 V	V _{STBY} 27 °C		35	100	μA						

Table 21.	DC electrical specifications	(continued)
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Cumbal	Symbol		Dowowodow	Conditions		Value		11
Symbol		С	Parameter Conditions		min	typ	max	Unit
	СС	Ρ	Operating current 0.95- 1.2 V	V _{STBY} 150 °C		790	2000	μA
I _{DDSTBY150}		Р	Operating current 2– 5.5 V	V _{STBY} at 150 °C		760	2000	μA
IDDSLOW		Р	V _{DD} low-power mode	Slow mode ⁽¹⁰⁾	_		191	
IDDSTOP	СС	Р	operating current at 1.32 V	Stop mode ⁽¹¹⁾	_		190	mA
I _{DD33}	сс	с	Operating current 3.3 V supplies	V _{RC33} ⁽¹⁾ , ⁽¹²⁾			60	mA
		Р		V _{DDA}	_	_	30.0	
I _{DDA} I _{REF} I _{DDREG}	сс	Ρ	Operating current 5.0 V supplies	Analog reference supply current (transient)	_	_	1.0	mA
		С		V _{DDREG}	_		70 ⁽¹³⁾	
		D		V _{DDEH1}	_	—		
I _{DDH1}		D		V _{DDEH4}	_	—	See note ⁽¹⁴⁾	
I _{DDH4} I _{DDH6}		D	Operating current V _{DDE} (¹⁴⁾ supplies	V _{DDEH6}	_	—		
I _{DDH7}	СС	D		V _{DDEH7}		_		mA
I _{DD7} I _{DDH9}		D		V _{DDE7}		_		
I _{DD12}		D		V _{DDEH9}		_		
		D		V _{DDE12}		_		
l	сс	С	Slow/medium I/O weak	3.0 V – 3.6 V	15	_	95	•
I _{ACT_S}	00	Ρ	pull up/down current ⁽¹⁵⁾	4.75 V – 5.5 V	35	—	200	μA
		D		1.62 V – 1.98 V	36	—	120	
I _{ACT_F}	сс	D	Fast I/O weak pull up/down current ⁽¹⁵⁾	2.25 V – 2.75 V	34	—	139	μA
		D		3.0 V – 3.6 V	42	—	158	
I _{ACT_MV_PU}	СС	с	Multi-voltage pad weak pullup current	V _{DDE} = 3.0–3.6 V ⁽⁵⁾ , MultiV pad, high swing mode only	10	_	75	μA
		Р		4.75 V – 5.25 V	25	_	200	

Table 21.	DC electrical specifications (continued)
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Symbol		с	Parameter	Conditions		Value			
Symbol			Parameter	Conditions	min	typ	max	Unit	
I _{ACT_MV_PD}	СС	с	Multivoltage pad weak pulldown current	V _{DDE} = 3.0–3.6 V ⁽⁵⁾ , MultiV pad, high swing mode only	10	_	60	μΑ	
		Ρ		4.75 V – 5.25 V	25	_	200		
I _{INACT_D}	СС	Р	I/O input leakage current ⁽¹⁶⁾	_	-2.5	_	2.5	μΑ	
l _{IC}	SR	т	DC injection current (per pin)	_	-1.0	_	1.0	mA	
		Р	Analog input current, channel off, AN[0:7] ⁽¹⁷⁾	_	-250	_	250		
I _{INACT_A}	SR	Р	Analog input current, channel off, all other analog pins ⁽¹⁷⁾	_	-150		150	nA	
		D		DSC(PCR[8:9]) = 0b00			10		
	СС	D D	Load capacitance (fast I/O) ⁽¹⁸⁾	DSC(PCR[8:9]) = 0b01			20		
CL	CC			DSC(PCR[8:9]) = 0b10	_		30	pF	
		D		DSC(PCR[8:9]) = 0b11	_		50		
C _{IN}	СС	D	Input capacitance (digital pins)	_	_		7	pF	
C _{IN_A}	СС	D	Input capacitance (analog pins)	_	_		10	pF	
C _{IN_M}	СС	D	Input capacitance (digital and analog pins ⁽¹⁹⁾)	_	_		12	pF	
R _{PUPD200K}	SR	Ρ	Weak Pull-Up/Down Resistance ⁽²⁰⁾ , 200 kΩ Option	_	130	_	280	kΩ	
R _{PUPD100K}	SR	Ρ	Weak Pull-Up/Down Resistance ⁽²⁰⁾ , 100 kΩ Option	_	65	_	140	kΩ	

Table 21.	DC electrical specifications (contin	ued)
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Symbol		с	Parameter Conditions			Value	Unit		
Symbol	Symbol C		Farameter	Conditions	min	typ	max		
R _{PUPD5K}	SR	с	Weak Pull-Up/Down Resistance ⁽²⁰⁾ , 5 kΩ Option	5 V ± 5% supply	1.4	_	7.5	kΩ	
R _{PUPDMTCH}	СС	С	Pull-up/Down Resistance matching ratios (100K/200K)	Pull-up and pull-down resistances both enabled and settings are equal.	-2.5	_	2.5	%	
T _A (T _L to T _H)	SR		Operating temperature range - ambient (packaged)	_	-40.0		125.0	°C	
_	SR	_	Slew rate on power 25					V/ms	

Table 21.	DC electrical specifications (continued)
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1. These specifications apply when V_{RC33} is supplied externally, after disabling the internal regulator (V_{DDREG} = 0).

2. ADC is functional with 4 V \leq V_{DDA} \leq 4.75 V but with derated accuracy. This means the ADC will continue to function at full speed with no undesirable behavior, but the accuracy will be degraded.

 The V_{DDF} supply is connected to V_{DD} in the package substrate. This specification applies to calibration package devices only.

4. V_{FLASH} is only available in the calibration package.

5. Power supply for multi-voltage pads cannot be below 4.5 V when in low-swing mode.

6. The slew rate (SRC) setting must be 0b11 when in low-swing mode.

7. While in low-swing mode there are no restrictions in transitioning to high-swing mode.

8. Pin in low-swing mode can accept a 5 V input.

9. All V_{OL}/V_{OH} values 100% tested with ± 2 mA load except where noted.

10. Bypass mode, system clock at 1 MHz (using system clock divider), PLL shut down, CPU running simple executive code, 4 x ADC conversion every 10 ms, 2 x PWM channels 1 kHz, all other modules stopped.

11. Bypass mode, system clock at 1 MHz (using system clock divider), CPU stopped, PIT running, all other modules stopped.

12. This current will be consumed for external regulation and internal regulation, when 3.3V regulator is switched off by shadow flash

13. If 1.2V and 3.3V internal regulators are on,then iddreg=70mA

If supply is external that is 3.3V internal regulator is off, then iddreg=15mA

- 14. Power requirements for each I/O segment are dependent on the frequency of operation and load of the I/O pins on a particular I/O segment, and the voltage of the I/O segment. See *Table 22* for values to calculate power dissipation for specific operation. The total power consumption of an I/O segment is the sum of the individual power consumptions for each pin on the segment.
- 15. Absolute value of current, measured at V_{IL} and $V_{\text{IH}}.$
- 16. Weak pull up/down inactive. Measured at V_{DDE} = 3.6 V and V_{DDEH} = 5.25 V. Applies to fast, slow, and medium pads.
- 17. Maximum leakage occurs at maximum operating temperature. Leakage current decreases by approximately one-half for each 8 to 12 °C, in the ambient temperature range of 50 to 125 °C. Applies to analog pads.
- 18. Applies to CLKOUT, external bus pins, and Nexus pins.
- 19. Applies to the FCK, SDI, SDO, and $\overline{\text{SDS}}$ pins.
- This programmable option applies only to eQADC differential input channels and is used for biasing and sensor diagnostics.



3.9 I/O pad current specifications

The power consumption of an I/O segment depends on the usage of the pins on a particular segment. The power consumption is the sum of all output pin currents for a particular segment. The output pin current can be calculated from *Table 22* based on the voltage, frequency, and load on the pin. Use linear scaling to calculate pin currents for voltage, frequency, and load parameters that fall outside the values given in *Table 22*.

Pad Type	Symbol		с	Period (ns)	Load ⁽²⁾ (pF)	V _{DDE} (V)	Drive/Slew Rate Select	I _{DDE} Avg (mA) ⁽³⁾	I _{DDE} RMS (mA)
		СС	D	37	50	5.5	11	9	—
Slow	I	СС	D	130	50	5.5	01	2.5	—
31000	I _{DRV_SSR_HV}	СС	D	650	50	5.5	00	0.5	—
		СС	D	840	200	5.5	00	1.5	—
		СС	D	24	50	5.5	11	14	—
Medium		СС	D	62	50	5.5	01	5.3	—
Wediam	I _{DRV_MSR_HV}	СС	D	317	50	5.5	00	1.1	_
		СС	D	425	200	5.5	00	3	—
		СС	D	10	50	3.6	11	22.7	68.3
		СС	D	10	30	3.6	10	12.1	41.1
		СС	D	10	20	3.6	01	8.3	27.7
Fast	I _{DRV_FC}	СС	D	10	10	3.6	00	4.44	14.3
Tast		СС	D	10	50	1.98	11	12.5	31
		СС	D	10	30	1.98	10	7.3	18.6
		СС	D	10	20	1.98	01	5.42	12.6
		СС	D	10	10	1.98	00	2.84	6.4
N 4 - 14:1 /		СС	D	20	50	5.5	11	9	_
MultiV (High		СС	D	30	50	5.5	01	6.1	—
Swing Mode)	IDRV_MULTV_HV	СС	D	117	50	5.5	00	2.3	—
		CC	D	212	200	5.5	00	5.8	_
MultiV (Low Swing Mode)	I _{DRV_MULTV_HV}	сс	D	30	30	5.5	11	3.4	_

Table 22.	I/O pad average I _{DDE} specifications ⁽¹⁾
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1. Numbers from simulations at best case process, 150 $^\circ\text{C}.$

2. All loads are lumped.

3. Average current is for pad configured as output only.



3.9.1 I/O pad V_{RC33} current specifications

The power consumption of the V_{RC33} supply is dependent on the usage of the pins on all I/O segments. The power consumption is the sum of all input and output pin V_{RC33} currents for all I/O segments. The output pin V_{RC33} current can be calculated from *Table 23* based on the voltage, frequency, and load on all fast pad pins. The input pin V_{RC33} current can be calculated from *Table 23* based on the voltage, frequency, and load on the voltage, frequency, and load on all medium-speed pads. Use linear scaling to calculate pin currents for voltage, frequency, and load parameters that fall outside the values given in *Table 23*.

Pad Type	Symbol		с	Period (ns)	Load ⁽²⁾ (pF)	Drive Select	I _{DD33} Avg (μΑ)	I _{DD33} RMS (µA)
		СС	D	100	50	11	0.8	235.7
Slow		СС	D	200	50	01	0.04	87.4
31000	IDRV_SSR_HV	СС	D	800	50	00	0.06	47.4
		СС	D	800	200	00	0.009	47
	I _{DRV_MSR_HV}	СС	D	40	50	11	2.75	258
Medium		СС	D	100	50	01	0.11	76.5
Wedium		СС	D	500	50	00	0.02	56.2
		СС	D	500	200	00	0.01	56.2
		СС	D	20	50	11	33.4	35.4
MultiV ⁽³⁾ (High	1	СС	D	30	50	01	33.4	34.8
Swing Mode)	IDRV_MULTV_HV	СС	D	117	50	00	33.4	33.8
		СС	D	212	200	00	33.4	33.7
MultiV ⁽⁴⁾ (Low Swing Mode)	I _{DRV_MULTV_HV}	сс	D	30	30	11	33.4	34.9

Table 23.	I/O pad V _{RC33} average I _{DDE} specifications ⁽¹⁾

1. These are typical values that are estimated from simulation and not tested. Currents apply to output pins only.

2. All loads are lumped.

3. Average current is for pad configured as output only.

4. In low swing mode, multi-voltage pads must operate in highest slew rate setting.



Pad Type	Symbol		с	Period (ns)	Load ⁽²⁾ (pF)	V _{RC33} (V)	V _{DDE} (V)	Drive Select	I _{DD33} Avg (μΑ)	I _{DD33} RMS (μA)
		СС	D	10	50	3.6	3.6	11	2.35	6.12
		СС	D	10	30	3.6	3.6	10	1.75	4.3
		СС	D	10	20	3.6	3.6	01	1.41	3.43
Fast		СС	D	10	10	3.6	3.6	00	1.06	2.9
rasi	IDRV_FC	СС	D	10	50	3.6	1.98	11	1.75	4.56
		СС	D	10	30	3.6	1.98	10	1.32	3.44
		СС	D	10	20	3.6	1.98	01	1.14	2.95
		СС	D	10	10	3.6	1.98	00	0.95	2.62

Table 24. V_{RC33} pad average DC current⁽¹⁾

1. These are typical values that are estimated from simulation and not tested. Currents apply to output pins only.

2. All loads are lumped.

3.9.2 LVDS pad specifications

LVDS pads are implemented to support the MSC (Microsecond Channel) protocol which is an enhanced feature of the DSPI module. The LVDS pads are compliant with LVDS specifications and support data rates up to 50 MHz.

Table 25.	DSPI LVDS pad specification
-----------	-----------------------------

#	Characteristic	Symbol		с	Condition	Min. Value	Typ. Value	Max. Value	Unit		
			Dat	a Ra	te						
4	Data Frequency	f _{LVDSCLK}	СС	D	—		50		MHz		
Driver Specs											
			сс	Ρ	SRC=0b00 or 0b11	150		400			
5	Differential output voltage	V _{OD}	СС	Ρ	SRC=0b01	90		320	mV		
			СС	Ρ	SRC=0b10	160		480			
6	Common mode voltage (LVDS), VOS	V _{OD}	сс	Ρ		1.06	1.2	1.39	V		
7	Rise/Fall time	T _R /T _F	СС	D	_		2		ns		
8	Propagation delay (Low to High)	T _{PLH}	сс	D			4		ns		
9	Propagation delay (High to Low)	T _{PHL}	сс	D	_		4		ns		



#	Characteristic	Symbol		с	Condition	Min. Value	Typ. Value	Max. Value	Unit		
10	Delay (H/L), sync Mode	t _{PDSYNC}	СС	D			4		ns		
11	Delay, Z to Normal (High/Low)	T _{DZ}	сс	D	_		500		ns		
12	Diff Skew Itphla-tplhbl or Itplhb-tphlal	T _{SKEW}	сс	D	_			0.5	ns		
	Termination										
13	Trans. Line (differential Zo)		СС	D	—	95	100	105	Ω		
14	Temperature		СС	D		-40		150	°C		

Table 25. DSPI LVDS pad specification (continued)

3.10 Oscillator and PLLMRFM electrical characteristics

Table 26. PLLMRFM electrical specifications

(V_{DDPLL} = 1.08 V to 3.6 V, V_{SS} = V_{SSPLL} = 0 V, T_A = T_L to T_H)

Symbo	. .	с	Parameter	Conditions	Va	lue	Unit	
Symbo		C	Falameter	Conditions	min	max		
f _{ref_crystal}	сс	D	PLL reference frequency range ⁽¹⁾	Crystal reference	4	40	MH-7	
f _{ref_ext}		С		External reference	4	80	MHz	
f _{pll_in}	сс	Ρ	Phase detector input frequency range (after pre-divider)	_	4	16	MHz	
f _{vco}	СС	Ρ	VCO frequency range	—	256	512	MHz	
f _{sys}	СС	С	On-chip PLL frequency ⁽²⁾	—	16	150	MHz	
f	сс	т	System frequency in bypass mode ⁽²⁾	Crystal reference	4	40	MHz	
f _{sys}		Ρ	System frequency in bypass mode ⁽²⁾	External reference	0	80	IVIEIZ	
t _{CYC}	СС	D	System clock period	—	—	1 / f _{sys}	ns	
f _{LORL}	сс	D	Loss of reference frequency	Lower limit	1.6	3.7	MHz	
f _{LORH}		D	window ⁽³⁾	Upper limit	24	56		
f _{SCM}	СС	Ρ	Self-clocked mode frequency ^{(4),(5)}		1.2	72.25	MHz	



Table 26.	PLLMRFM electrical specifications
	(V_{DDPLL} = 1.08 V to 3.6 V, V_{SS} = V_{SSPLL} = 0 V, T_A = T_L to T_H) (continued)

	Symbol					Va	lue	Unit	
Symbo	DI	С	Pa	rameter	Conditions	min	max	Unit	
		т	CLKOUT	Peak-to-peak (clock edge to clock edge)		-5	5	% f _{CLKOUT}	
C _{JITTER}	СС	т	period jitter ^{(6),(7),(8),(9)}	Long-term jitter (avg. over 2 ms interval)	f _{SYS} maximum	-6	6	ns	
t _{cst}	СС	Т	Crystal start-up	time ^{(10), (11)}	—	—	10	ms	
		т			Crystal Mode ⁽¹²⁾	Vxtal + 0.4	_	v	
V _{IHEXT}	СС	т	EXTAL input hig	h voltage	External Reference ^{(12),} (13)	V _{RC33} /2 + 0.4	V _{RC33}		
		т			Crystal Mode ⁽¹²⁾	_	Vxtal - 0.4		
V _{ILEXT}	СС	т	EXTAL input low	FAL input low voltage		0	V _{RC33} /2 - 0.4	V	
					4 MHz	5	30		
						5	26	- pF	
	сс	т	XTAL load capacitance ⁽¹⁰⁾		12 MHz	5	23		
					16 MHz	5	19		
					20 MHz	5	16	-	
					40 MHz	5	8		
t _{lpll}	СС	Ρ	PLL lock time (10)), (14)	—	—	200	μs	
t _{dc}	СС	Т	Duty cycle of ref	erence	_	40	60	%	
f _{LCK}	СС	Т	Frequency LOC	K range		-6	6	% f _{sys}	
f _{UL}	СС	Т	Frequency un-L0	DCK range		-18	18	% f _{sys}	
f _{CS}	сс	D	Modulation Dept		Center spread	±0.25	±4.0	% f	
f _{DS}		D			Down Spread	-0.5	-8.0	- % f _{sys}	
f _{MOD}	СС	D	Modulation frequ	uency ⁽¹⁵⁾	_	—	100	kHz	

1. Considering operation with PLL not bypassed.

2. All internal registers retain data at 0 Hz.

3. "Loss of Reference Frequency" window is the reference frequency range outside of which the PLL is in self clocked mode.

4. Self clocked mode frequency is the frequency that the PLL operates at when the reference frequency falls outside the f_{LOR} window.



- f_{VCO} self clock range is 20–150 MHz. f_{SCM} represents f_{SYS} after PLL output divider (ERFD) of 2 through 16 in enhanced mode.
- 6. This value is determined by the crystal manufacturer and board design.
- 7. Jitter is the average deviation from the programmed frequency measured over the specified interval at maximum f_{SYS}. Measurements are made with the device powered by filtered supplies and clocked by a stable external clock signal. Noise injected into the PLL circuitry via V_{DDPLL} and V_{SSPLL} and variation in crystal oscillator frequency increase the C_{JITTER} percentage for a given interval.
- 8. Proper PC board layout procedures must be followed to achieve specifications.
- Values are with frequency modulation disabled. If frequency modulation is enabled, jitter is the sum of C_{JITTER} and either f_{CS} or f_{DS} (depending on whether center spread or down spread modulation is enabled).
- 10. This value is determined by the crystal manufacturer and board design. For 4 MHz to 40 MHz crystals specified for this PLL, load capacitors should not exceed these limits.
- 11. Proper PC board layout procedures must be followed to achieve specifications.
- 12. This parameter is guaranteed by design rather than 100% tested.
- 13. V_{IHEXT} cannot exceed V_{RC33} in external reference mode.
- 14. This specification applies to the period required for the PLL to relock after changing the MFD frequency control bits in the synthesizer control register (SYNCR).
- 15. Modulation depth will be attenuated from depth setting when operating at modulation frequencies above 50 kHz.

3.11 Temperature sensor electrical characteristics

Table 27. Temperature sensor electrical characteristics

Symbo	Symbol C		Parameter	Conditions		Unit		
Symbo	Л	C	Farameter	Conditions	min typical max			
_	сс	С	Temperature monitoring range		-40	—	150	°C
—	CC	С	Sensitivity		_	6.3	_	mV/°C
_	СС	Ρ	Accuracy	T _J = –40 to 150 °C	-10	_	10	°C

3.12 eQADC electrical characteristics

Table 28. eQADC conversion specifications (operating)

Symbol		С	Parameter	Va	lue	Unit
		U	Falanciel	min	max	
f _{ADCLK}	SR	_	ADC clock (ADCLK) frequency	2	16	MHz
CC	CC	D	Conversion cycles	2+13	128+14	ADCLK cycles
T _{SR}	CC	С	Stop mode recovery time ⁽¹⁾	—	10	μS
f _{ADCLK}	SR		ADC clock (ADCLK) frequency	2	16	mV

1. Stop mode recovery time is the time from the setting of either of the enable bits in the ADC Control Register to the time that the ADC is ready to perform conversions.Delay from power up to full accuracy = 8 ms.



Symbol		с	Parameter	v	alue	Unit
Symbol		C	Falametei	min	max	Onit
OFFNC	CC	С	Offset error without calibration	0	160	Counts
OFFWC	CC	С	Offset error with calibration	-4	4	Counts
GAINNC	CC	С	Full scale gain error without calibration	-160	0	Counts
GAINWC	CC	С	Full scale gain error with calibration	-4	4	Counts
I _{INJ}	CC	Т	Disruptive input injection current ^{(1), (2), (3), (4)}	-3	3	mA
E _{INJ}	CC	Т	Incremental error due to injection current ^{(5),(6)}	-4	4	Counts
TUE8	CC	С	Total unadjusted error (TUE) at 8 MHz	-4	4 ⁽⁶⁾	Counts
TUE16	CC	С	Total unadjusted error at 16 MHz	-8	8	Counts

	Table 29.	eQADC single ended conversion specifications	(operating)
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1. Below disruptive current conditions, the channel being stressed has conversion values of 0x3FF for analog inputs greater then V_{RH} and 0x0 for values less then V_{RL} . Other channels are not affected by non-disruptive conditions.

2. Exceeding limit may cause conversion error on stressed channels and on unstressed channels. Transitions within the limit do not affect device reliability or cause permanent damage.

3. Input must be current limited to the value specified. To determine the value of the required current-limiting resistor, calculate resistance values using $V_{POSCLAMP} = V_{DDA} + 0.5$ V and $V_{NEGCLAMP} = -0.3$ V, then use the larger of the calculated values.

4. Condition applies to two adjacent pins at injection limits.

5. Performance expected with production silicon.

6. All channels have same 10 k Ω < Rs < 100 k Ω ; Channel under test has Rs=10 k Ω ; $I_{INJ}=I_{INJMAX}$, I_{INJMIN}

Symbol		с	Parameter		Value		Unit
		C			min	max	Unit
	CC	-	Variable gain ampl	ifier accurad	y (gain=1) ⁽²⁾		
GAINVGA1 (1)	СС	С	- INL	8 MHz ADC	-4	4	Counts ⁽³⁾
	СС	С		16 MHz ADC	-8	8	Counts
	СС	С	DNL	8 MHz ADC	-3 ⁽⁴⁾	3 ⁽⁴⁾	Counts
	СС	С		16 MHz ADC	-3 ⁽⁴⁾	3 ⁽⁴⁾	Counts

Table 30. eQADC differential ended conversion specifications (operating)



Symbol C		•	Parameter		Value		11-14
		C			min	max	Unit
	CC	_	Variable gain ampli	ifier accurad	y (gain=2) ⁽²⁾		
GAINVGA2 (1)	СС	D	INL	8 MHz ADC	-5	5	Counts
	СС	D		16 MHz ADC	-8	8	Counts
	СС	D	- DNL	8 MHz ADC	-3	3	Counts
	СС	D		16 MHz ADC	-3	3	Counts
GAINVGA4 (1)	CC	_	Variable gain amplifier accuracy (gain=4) ⁽²⁾				
	СС	D	- INL	8 MHz ADC	-7	7	Counts
	СС	D		16 MHz ADC	-8	8	Counts
	СС	D	- DNL	8 MHz ADC	-4	4	Counts
	СС	D		16 MHz ADC	-4	4	Counts
DIFF _{max}	СС	С	Maximum differential voltage (DANx+ - DANx-) or (DANx DANx+) ⁽⁵⁾	PREGAIN set to 1X setting	_	(VRH - VRL)/2	v
DIFF _{max2}	СС	С		PREGAIN set to 2X setting	_	(VRH - VRL)/4	V
DIFF _{max4}	СС	С		PREGAIN set to 4X setting	_	(VRH - VRL)/8	V
DIFF _{cmv}	СС	С	Differential input Common mode voltage (DANx- + DANx+)/2 ⁽⁵⁾	_	(V _{RH} + V _{RL})/2 - 5%	(V _{RH} + V _{RL})/2 + 5%	v

Table 30.	eQADC differential ended convers	ion specifications	(operating) (continued)
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1. Applies only to differential channels.

Variable gain is controlled by setting the PRE_GAIN bits in the ADC_ACR1-8 registers to select a gain factor of ×1, ×2, or ×4. Settings are for differential input only. Tested at ×1 gain. Values for other settings are guaranteed by as indicated.

3. At $V_{RH}-V_{RL}$ = 5.12 V, one LSB = 1.25 mV.

4. Guaranteed 10-bit mono tonicity.

5. Voltages between VRL and VRH will not cause damage to the pins. However, they may not be converted accurately if the differential voltage is above the maximum differential voltage. In addition, conversion errors may occur if the common mode voltage of the differential signal violates the Differential Input common mode voltage specification.


3.13 Configuring SRAM wait states

Use the SWSC field in the ECSM_MUDCR register to specify an additional wait state for the device SRAM. By default, no wait state is added.

Table 31.	Cutoff frequency for additional SRAM wait state
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(1)	SWSC Value				
98	0				
153	1				

1. Max frequencies including 2% PLL FM.

Please see the device reference manual for details.

3.14 Platform flash controller electrical characteristics

Max. Flash Operating Frequency (MHz) ⁽³⁾	APC ⁽⁴⁾	RWSC ⁽⁴⁾	wwsc
20 MHz	0b000	0b000	0b11
61 MHz	0b001	0b001	0b11
90 MHz	0b010	0b010	0b11
123 MHz	0b011	0b011	0b11
153 MHz	0b100	0b100	0b11

Table 32. APC, RWSC, WWSC settings vs. frequency of operation^{(1),(2)}

 APC, RWSC and WWSC are fields in the flash memory BIUCR register used to specify wait states for address pipelining and read/write accesses. Illegal combinations exist—all entries must be taken from the same row.

- 2. TBD: To Be Defined.
- 3. Max frequencies including 2% PLL FM.
- 4. APC must be equal to RWSC.

3.15 Flash memory electrical characteristics

Table 33. Flash program and erase specifications⁽¹⁾

#	Symbol C		С	Parameter	Min. Value	Typical Value	Initial Max ⁽²⁾	Max ⁽³⁾	Unit
1	T _{dwprogram}	C C	Ρ	Double Word (64 bits) Program Time	_	45		500	μs
2	T _{pprogram}	C C	Ρ	Page Program Time	_	55	160 ⁽⁴⁾	500	μs
3	T _{16kpperase}	C C	Ρ	16 KB Block Pre-program and Erase Time		300	1000	5000	ms



#	Symbol		С	Parameter	Min. Value	Typical Value	Initial Max ⁽²⁾	Max ⁽³⁾	Unit
5	T _{64kpperase}	C C	Ρ	64 KB Block Pre-program and Erase Time	_	800	1800	5000	ms
6	T _{128kpperase}	C C	Ρ	128 KB Block Pre-program and Erase Time	_	1500	3000	7500	ms
7	T _{256kpperase}	C C	Ρ	256 KB Block Pre-program and Erase Time	_	3000	5300	15000	ms
8	T _{psrt}	SR	—	Program suspend request rate ⁽⁵⁾	100	—	—	—	μs
9	T _{esrt}	SR		Erase suspend request rate ⁽⁶⁾	10				ms

 Table 33.
 Flash program and erase specifications⁽¹⁾ (continued)

1. Typical program and erase times assume nominal supply values and operation at 25 °C. All times are subject to change pending device characterization.

2. Initial factory condition: ≤ 100 program/erase cycles, 25 °C, typical supply voltage, 80 MHz minimum system frequency.

- 3. The maximum erase time occurs after the specified number of program/erase cycles. This maximum value is characterized but not guaranteed.
- 4. Page size is 128 bits (4 words).
- 5. Time between program suspend resume and the next program suspend request.
- 6. Time between erase suspend resume and the next erase suspend request.

Table 34. Flash module life

Symbol		с	Parameter	Conditions	Val	ue	Unit
Symbo	Symbol C		Fatameter	Conditions	min	typ	Unit
P/E	СС	С	Number of program/erase cycles per block for 16 KB, 48 KB, and 64 Kbyte blocks over the operating temperature range (T _J)	_	100,000	_	P/E cycles
P/E	СС	С	Number of program/erase cycles per block for 128 Kbyte and 256 Kbyte blocks over the operating temperature range (T _J)	_	1,000	100,000	P/E cycles
				Blocks with 0 – 1,000 P/E cycles	20	_	years
Data Retention	сс	сс с	C C S °C average ambient temperature ⁽¹⁾	Blocks with 1,001 – 10,000 P/E cycles	10	_	years
				Blocks with 10,001 – 100,000 P/E cycles	5	_	years

1. Ambient temperature averaged over duration of application, not to exceed product operating temperature range.



3.16 AC specifications

3.16.1 Pad AC specifications

Table 35. Pad AC specifications (5.0 V)⁽¹⁾

Name		с	Output Delay (ns) ^{(2),(3)} Low-to-High / High- to-Low		Rise/Fall Edge (ns) ^{(3),(4)}		Drive Load (pF)	SRC/DSC
			Min	Max	Min	Max		MSB,LSB
	CC	D	4.6/3.7	12/12	2.2/2.2	7/7	50	11 ⁽⁸⁾
Medium ^{(5),(6),(7)}		•			N/A			10 ⁽⁹⁾
Medium	CC	D	12/13	28/34	5.6/6	15/15	50	01
	CC	D	69/71	152/165	34/35	74/74	50	00
	CC	D	7.3/5.7	19/18	4.4/4.3	14/14	50	11 ⁽⁸⁾
Slow ^{(7),(10)}	N/A							10 ⁽⁹⁾
Slow	CC	D	26/27	61/69	13/13	34/34	50	01
	CC	D	137/142	320/330	72/74	164/164	50	00
	CC	D	4.1/3.6	10.3/8.9	3.28/2.98	8/8	50	11 ⁽⁸⁾
MultiV ⁽¹¹⁾					N/A			10 ⁽⁹⁾
(High Swing Mode)	CC	D	8.38/6.11	16/12.9	5.48/4.81	11/11	50	01
	CC	D	61.7/10.4	92.2/24.3	42.0/12.2	63/63	50	00
MultiV (Low Swing Mode)	сс	D	2.31/2.34	7.62/6.33	1.26/1.67	6.5/4.4	30	11 ⁽⁸⁾
Fast ⁽¹²⁾					N/A			
pad_i_hv ⁽¹³⁾	СС	D	0.5/0.5	1.9/1.9	0.3/0.3	±1.5/1.5	0.5	N/A
pull_hv	CC	D	NA	6000		5000/5000	50	N/A

1. These are worst case values that are estimated from simulation and not tested. The values in the table are simulated at V_{DD} = 1.14 V to 1.32 V, V_{DDEH} = 4.5 V to 5.5 V, T_A = T_L to T_H

- 2. This parameter is supplied for reference and is not guaranteed by design and not tested.
- 3. Delay and rise/fall are measured to 20% or 80% of the respective signal.
- 4. This parameter is guaranteed by characterization before qualification rather than 100% tested.
- 5. In high swing mode, high/low swing pad Vol and Voh values are the same as those of the slew controlled output pads
- 6. Medium Slew-Rate Controlled Output buffer. Contains an input buffer and weak pullup/pulldown.
- 7. Output delay is shown in *Figure 9: Pad output delay*. Add a maximum of one system clock to the output delay for delay with respect to system clock.
- 8. Can be used on the tester.
- 9. This drive select value is not supported. If selected, it will be approximately equal to 11.
- 10. Slow Slew-Rate Controlled Output buffer. Contains an input buffer and weak pullup/pulldown.
- 11. Selectable high/low swing IO pad with selectable slew in high swing mode only.
- 12. Fast pads are 3.3 V pads.
- 13. Stand alone input buffer. Also has weak pull-up/pull-down.



Pad Type	Pad Type		(ns) Low-to-Hi	t Delay ^{(2),(3)} gh / High- _ow	Rise/Fall Ec	lge (ns) ^{(3),(4)}	Drive Load (pF)	SRC/DSC
			Min	Max	Min	Max		MSB,LSB
	CC	D	5.8/4.4	18/17	2.7/2.1	10/10	50	11 ⁽⁸⁾
	CC	D	16/13	46/49	11.2/8.6	34/34	200	11, 7
					N/A			10 ⁽⁹⁾
Medium ^{(5),(6),(7)}	CC	D	14/16	37/45	6.5/6.7	19/19	50	01
	CC	D	27/27	69/82	15/13	43/43	200	01
	CC	D	83/86	200/210	38/38	86/86	50	00
	CC	D	113/109	270/285	53/46	120/120	200	00
	CC	D	9.2/6.9	27/28	5.5/4.1	20/20	50	11
	CC	D	30/23	81/87	21/16	63/63	200	11
					N/A			10 ⁽⁹⁾
Slow ^{(7),(10)}	CC	D	31/31	80/90	15.4/15.4	42/42	50	01
	CC	D	58/52	144/155	32/26	82/85	200	01
	CC	D	162/168	415/415	80/82	190/190	50	00
	CC	D	216/205	533/540	106/95	250/250	200	00
	CC	D		3.7/3.1		10/10	30	11 ⁽⁸⁾
	CC	D		46/49		37/37	200	1157
MultiV ^{(7),(11)}		N/A						10 ⁽⁹⁾
(High Swing Mode)	CC	D		32		15/15	50	01
(ingli etting meae)	CC	D		72		46/46	200	01
	CC	D		210		100/100	50	00
	CC	D		295		134/134	200	00
MultiV (Low Swing Mode)				Not	a valid operat	ional mode		
	CC	D		2.5/2.5		1.2/1.2	10	00
East	CC	D		2.5/2.5		1.2/1.2	20	01
Fast	CC	D		2.5/2.5		1.2/1.2	30	10
	CC	D		2.5/2.5		1.2/1.2	50	11 ⁽⁸⁾
pad_i_hv ⁽¹²⁾	CC	D	0.5/0.5	3/3	0.4/0.4	±1.5/1.5	0.5	N/A
pull_hv	CC	D	NA	6000		5000/5000	50	N/A

Table 36.Pad AC specifications $(V_{DDE} = 3.3 V)^{(1)}$

1. These are worst case values that are estimated from simulation and not tested. The values in the table are simulated at $V_{DD} = 1.14$ V to 1.32 V, $V_{DDE} = 3$ V to 3.6 V, $V_{DDEH} = 3$ V to 3.6 V, $T_A = T_L$ to T_H .

2. This parameter is supplied for reference and is not guaranteed by design and not tested.

3. Delay and rise/fall are measured to 20% or 80% of the respective signal.



- 4. This parameter is guaranteed by characterization before qualification rather than 100% tested.
- 5. In high swing mode, high/low swing pad Vol and Voh values are the same as those of the slew controlled output pads
- 6. Medium Slew-Rate Controlled Output buffer. Contains an input buffer and weak pullup/pulldown.
- 7. Output delay is shown in *Figure 9*. Add a maximum of one system clock to the output delay for delay with respect to system clock.
- 8. Can be used on the tester.
- 9. This drive select value is not supported. If selected, it will be approximately equal to 11.
- 10. Slow Slew-Rate Controlled Output buffer. Contains an input buffer and weak pullup/pulldown.
- 11. Selectable high/low swing IO pad with selectable slew in high swing mode only.
- 12. Stand alone input buffer. Also has weak pull-up/pull-down.



Figure 9. Pad output delay



3.17 AC timing

3.17.1 Reset and configuration pin timing

Table 37. Reset and Configuration Pin Timing⁽¹⁾

#	Characteristic	Symbol	Min	Max	Unit
1	RESET Pulse Width ⁽²⁾	t _{RPW}	10	_	t _{cyc}
2	RESET Glitch Detect Pulse Width	t _{GPW}	2		t _{cyc}
3	PLLREF, BOOTCFG, WKPCFG Setup Time to RSTOUT Valid	t _{RCSU}	10		t _{cyc}
4	PLLREF, BOOTCFG, WKPCFG Hold Time to RSTOUT Valid	t _{RCH}	0		t _{cyc}

1. Reset timing specified at: V_{DDEH} = 3.0 V to 5.25 V, V_{DD} = 1.14 V to 1.32 V, T_A = T_L to T_H .

2. RESET pulse width is measured from 50% of the falling edge to 50% of the rising edge.



Figure 10. Reset and Configuration Pin Timing



3.17.2 IEEE 1149.1 interface timing

#	Symbol		с	Characteristic	Min. Value	Max. Value	Unit
1	tJCYC	СС	D	TCK Cycle Time	100	—	ns
2	t _{JDC}	СС	D	TCK Clock Pulse Width	40	60	ns
3	t _{TCKRISE}	сс	D	TCK Rise and Fall Times (40% - 70%)	_	3	ns
4	t _{TMSS} , t _{TDIS}	СС	D	TMS, TDI Data Setup Time	5	—	ns
5	t _{TMSH} , t _{TDIH}	СС	D	TMS, TDI Data Hold Time	25	—	ns
6	t _{TDOV}	СС	D	TCK Low to TDO Data Valid	—	22 ⁽²⁾	ns
7	t _{TDOI}	СС	D	TCK Low to TDO Data Invalid	0	—	ns
8	t _{TDOHZ}	СС	D	TCK Low to TDO High Impedance	—	22	ns
9	t _{JCMPPW}	СС	D	JCOMP Assertion Time	100	—	ns
10	t _{JCMPS}	СС	D	JCOMP Setup Time to TCK Low	40	—	ns
11	t _{BSDV}	СС	D	TCK Falling Edge to Output Valid	—	50	ns
12	t _{BSDVZ}	сс	D	TCK Falling Edge to Output Valid out of High Impedance	_	50	ns
13	^t BSDHZ	сс	D	TCK Falling Edge to Output High Impedance	_	50	ns
14	t _{BSDST}	сс	D	Boundary Scan Input Valid to TCK Rising Edge	25 ⁽³⁾	_	ns
15	t _{BSDHT}	СС	D	TCK Rising Edge to Boundary Scan Input Invalid	25 ⁽³⁾	_	ns

 Table 38.
 JTAG pin AC electrical characteristics⁽¹⁾

1. JTAG timing specified at V_{DD} = 1.14 V to 1.32 V, V_{DDEH} = 4.5 V to 5.5 V with multi-voltage pads programmed to Low-Swing mode, $T_A = T_L$ to T_H , and C_L = 30 pF with DSC = 0b10, SRC = 0b11. These specifications apply to JTAG boundary scan only. See *Table 39* for functional specifications.

2. Pad delay is 8–10 ns. Remainder includes TCK pad delay, clock tree delay logic delay and TDO output pad delay.

3. For 20 MHz TCK.

Note: The Nexus/JTAG Read/Write Access Control/Status Register (RWCS) write (to begin a read access) or the write to the Read/Write Access Data Register (RWD) (to begin a write access) does not actually begin its action until 1 JTAG clock (TCK) after leaving the JTAG Update-DR state. This prevents the access from being performed and therefore will not signal its completion via the READY (RDY) output unless the JTAG controller receives an additional TCK. In addition, EVTI is not latched into the device unless there are clock transitions on TCK.

The tool/debugger must provide at least one TCK clock for the EVTI signal to be recognized by the MCU. When using the RDY signal to indicate the end of a Nexus read/write access, ensure that TCK continues to run for at least 1 TCK after leaving the Update-DR state. This can be just a TCK with TMS low while in the Run-Test/Idle state or by continuing with the



next Nexus/JTAG command. Expect the affect of EVTI and RDY to be delayed by edges of TCK. Note: RDY is not available in all packages of all devices.



Figure 11. JTAG test clock input timing



Figure 12. JTAG test access port timing





Figure 13. JTAG JCOMP timing





Figure 14.	JTAG boundary scan timing
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3.17.3 Nexus timing

Table 39.	Nexus	debug	port	timing ⁽¹⁾
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#	Symbol		С	Characteristic	Min. Value	Max. Value	Unit
1	t _{MCYC}	СС	D	MCKO Cycle Time	2 ^{(2),(3)}	8	t _{CYC}
1a	t _{MCYC}	СС	D	Absolute Minimum MCKO Cycle Time	25 ⁽⁴⁾	—	ns
2	t _{MDC}	СС	D	MCKO Duty Cycle	40	60	%
3	t _{MDOV}	СС	D	MCKO Low to MDO Data Valid ⁽⁵⁾	- 0.1	0.35	t _{MCYC}
4	t _{MSEOV}	СС	D	MCKO Low to MSEO Data Valid ⁽⁵⁾	- 0.1	0.35	t _{MCYC}
6	t _{EVTOV}	СС	D	MCKO Low to EVTO Data Valid ⁽⁵⁾	- 0.1	0.35	t _{MCYC}
7	t _{EVTIPW}	СС	D	EVTI Pulse Width	4.0	—	t _{TCYC}
8	t _{EVTOPW}	СС	D	EVTO Pulse Width	1	—	t _{MCYC}



#	Symbol		С	Characteristic	Min. Value	Max. Value	Unit
9	t _{TCYC}	CC	D	TCK Cycle Time	4 ^{(6),(7)}	—	tCYC
9a	t _{TCYC}	СС	D	Absolute Minimum TCK Cycle Time	100 ⁽⁸⁾	—	ns
10	t _{TDC}	СС	D	TCK Duty Cycle	40	60	%
11	t _{NTDIS}	СС	D	TDI Data Setup Time	5	—	ns
12	t _{NTDIH}	СС	D	TDI Data Hold Time	25	—	ns
13	t _{NTMSS}	СС	D	TMS Data Setup Time	5	—	ns
14	t _{NTMSH}	СС	D	TMS Data Hold Time	25	—	ns
15	_	сс	D	TDO propagation delay from falling edge of TCK	_	19.5	ns
16	_	сс	D	TDO hold time with respect to TCK falling edge (minimum TDO propagation delay)	5.25	_	ns

Table 39.	Nexus debug port timing ⁽¹⁾ (continued
Table 39.	Nexus debug port timing ^v (continued

1. All Nexus timing relative to MCKO is measured from 50% of MCKO and 50% of the respective signal. Nexus timing specified at $V_{DD} = 1.14$ V to 1.32 V, $V_{DDEH} = 4.5$ V to 5.5 V with multi-voltage pads programmed to Low-Swing mode, $T_A = T_L$ to T_H , and $C_L = 30$ pF with DSC = 0b10.

- 2. Achieving the absolute minimum MCKO cycle time may require setting the MCKO divider to more than its minimum setting (NPC_PCR[MCKO_DIV] depending on the actual system frequency being used.
- 3. This is a functionally allowable feature. However, this may be limited by the maximum frequency specified by the Absolute minimum MCKO period specification.
- 4. This may require setting the MCO divider to more than its minimum setting (NPC_PCR[MCKO_DIV]) depending on the actual system frequency being used.
- 5. MDO, MSEO, and EVTO data is held valid until next MCKO low cycle.
- Achieving the absolute minimum TCK cycle time may require a maximum clock speed (system frequency / 8) that is less than the maximum functional capability of the design (system frequency / 4) depending on the actual system frequency being used.
- 7. This is a functionally allowable feature. However, this may be limited by the maximum frequency specified by the Absolute minimum TCK period specification.
- 8. This may require a maximum clock speed (system frequency / 8) that is less than the maximum functional capability of the design (system frequency / 4) depending on the actual system frequency being used.



Figure 15. Nexus output timing

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Figure 16. Nexus event trigger and test clock timings



Figure 17. Nexus TDI, TMS, TDO timing

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Package	Nexus Width	Nexus Routing)	Max. Operating		
Fackage		Nexus Houting	MDO[0:3]	MDO[4:11]	CAL_MDO[4:11]	Frequency	
LQFP176	Reduced port mode ⁽¹⁾	Route to MDO ⁽²⁾	Nexus Data Out [0:3]	GPIO	GPIO	40 MHz ⁽³⁾	
BGA208 BGA324	Full port mode ⁽⁴⁾	Route to MDO ⁽²⁾	Nexus Data Out [0:3]	Nexus Data Out [4:11]	GPIO	40 MHz ^{(5),(6)}	
	Reduced port mode ⁽¹⁾	Route to MDO ⁽²⁾	Nexus Data Out [0:3]	GPIO	GPIO	40 MHz ⁽³⁾	
CSP496	Full port	Route to MDO ⁽²⁾	Nexus Data Out [0:3]	Nexus Data Out [4:11]	GPIO	40 MHz ^{(5),(6)}	
	mode ⁽⁴⁾	Route to CAL_MDO ⁽⁷⁾	Cal Nexus Data Out [0:3]	GPIO	Cal Nexus Data Out [4:11]	40 MHz ⁽³⁾	

Table 40. Nexus debug port operating frequency

1. NPC_PCR[FPM] = 0

2. NPC_PCR[NEXCFG] = 0

3. The Nexus AUX port runs up to 40 MHz. Set NPC_PCR[MCKO_DIV] to divide-by-two if the system frequency is greater than 40 MHz.

4. NPC_PCR[FPM] = 1

5. Set the NPC_PCR[MCKO_DIV] to divide by two if the system frequency is between 40 MHz and 80 MHz inclusive. Set the NPC_PCR[MCKO_DIV] to divide by four if the system frequency is greater than 80 MHz.

6. Pad restrictions limit the Maximum Operation Frequency in these configurations

7. NPC_PCR[NEXCFG] = 1



3.17.4 External Bus Interface (EBI) and calibration bus interface timing

Port Width	Multiplexed Mode	ADDR[12:15] Pin Usage	ADDR[16:31] Pin Usage	DATA[0:15] Pin Usage	Max. Operating Frequency
16-bit	Yes	ADDR[12:15]	GPIO	ADDR[16:31] DATA[0:15]	66 MHz ⁽¹⁾
16-bit	No	ADDR[12:15]	ADDR[16:31]	DATA[0:15]	33 MHz ^{(2),(3)}
32-bit	Yes	ADDR[12:15]	ADDR[16:31] DATA[16:31]	DATA[0:15]	33 MHz ^{(2),(3)}

Table 41. External Bus Interface maximum operating frequency

1. Set SIU_ECCR[EBDF] to divide by two or divide by four if the system frequency is greater than 66 MHz.

2. System Frequency must be \leq 132 MHz and SIU_ECCR[EBDF] set to divide by four.

3. Pad restrictions limit the maximum operating frequency.

Table 42. Calibration bus inte	rface maximum operat	ing frequency
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Port Width	Multiplexed Mode	CAL_ADDR[12:15] Pin Usage	CAL_ADDR[16:30] Pin Usage	CAL_DATA[0:15] Pin Usage	Max. Operating Frequency
16-bit	Yes	GPIO	GPIO	CAL_ADDR[12:30] CAL_DATA[0:15]	66 MHz ⁽¹⁾
16-bit	No	CAL_ADDR[12:15]	CAL_ADDR[16:30]	CAL_DATA[0:15]	66 MHz ⁽¹⁾
32-bit	Yes	CAL_WE[2:3] CAL_DATA[31]	CAL_ADDR[16:30] CAL_DATA[16:30]	CAL_ADDR[0:15] CAL_DATA[0:15]	66 MHz ⁽¹⁾

1. Set SIU_ECCR[EBDF] to divide by two or divide by four if the system frequency is greater than 66 MHz

Table 43. External bus interface (EBI) and calibration bus operation timing ⁽¹⁾

#	f Symbol		С	Characteristic	66 MHz (e	ext. bus) ⁽²⁾	Unit	Natas
#			C	Characteristic	Min	Max	Unit	Notes
1	т _с	сс	Ρ	CLKOUT Period	15.2	_	ns	Signals are measured at 50% V _{DDE} .
2	t _{CDC}	CC	D	CLKOUT duty cycle	45%	55%	Т _С	
3	t _{CRT}	CC	D	CLKOUT rise time		(3)	ns	
4	t _{CFT}	CC	D	CLKOUT fall time		(3)	ns	
5	t _{СОН}	сс	D	CLKOUT Posedge to Output Signal Invalid or High Z(Hold Time) – ADDR[8:31] – CS[0:3] – DATA[0:31] – OE – RD_WR – TS – WE[0:3]/BE[0:3]	1.3	_	ns	



#	Symbol		~	Characteristic	66 MHz (e	ext. bus) ⁽²⁾	Unit	Netes	
#	Symp	Symbol C		Symbol C Characteristic –		Min	Max	Unit	Notes
6	tcov	сс	D	CLKOUT Posedge to Output Signal Valid (Output Delay) ADDR[8:31] CS[0:3] DATA[0:31] OE RD_WR TS WE[0:3]/BE[0:3]		9	ns		
7	t _{CIS}	сс	D	Input Signal Valid to CLKOUT Posedge (Setup Time) DATA[0:31]	6.0	_	ns		
8	t _{СІН}	сс	D	CLKOUT Posedge to Input Signal Invalid (Hold Time) DATA[0:31]	1.0	_	ns		
9	t _{APW}	CC	D	ALE Pulse Width ⁽⁴⁾	6.5	—	ns		
10	t _{AAI}	CC	D	ALE Negated to Address Invalid ⁴	1.5 ⁽⁵⁾	—	ns		

Table 43. Extern	nal bus interface (EBI) and calibration bus	s operation timing ⁽¹⁾ (continued)
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1. External Bus and Calibration bus timing specified at f_{SYS} = 150 MHz and 100 MHz, V_{DD} = 1.14 V to 1.32 V, V_{DDE} = 3 V to 3.6 V (unless stated otherwise), T_A = T_L to T_H , and C_L = 30 pF with DSC = 0b10.

2. The external bus is limited to half the speed of the internal bus. The maximum external bus frequency is 66 MHz for 16-bit muxed mode and 33 MHz for non-muxed mode. For The EBI division factor should be set accordingly based on the internal frequency being used.

3. Refer to Fast Pad timing in *Table 35* and *Table 36* (different values for 1.8 V vs. 3.3 V).

4. Measured at 50% of ALE.

5. When CAL_TS pad is used for CAL_ALE function the hold time is 1 ns instead of 1.5 ns.



Figure 18. CLKOUT timing





Figure 19. Synchronous output timing





Figure 20. Synchronous input timing



Figure 21. ALE signal timing

3.17.5 External interrupt timing (IRQ pin)

#	Characteristic	Symbol	Min	Мах	Unit
1	IRQ Pulse Width Low	t _{IPWL}	3	_	t _{cyc}
2	IRQ Pulse Width High	t _{IPWH}	3		t _{cyc}
3	IRQ Edge to Edge Time ⁽²⁾	t _{ICYC}	6		t _{cyc}

1. IRQ timing specified at V_{DD} = 1.14 V to 1.32 V, V_{DDEH} = 3.0 V to 5.5 V, V_{DD33} and V_{DDSYN} = 3.0 V to 3.6 V, T_A = T_L to T_H .

2. Applies when IRQ pins are configured for rising edge or falling edge events, but not both.



Figure 22. External Interrupt Timing

3.17.6 eTPU timing

Table 45. eTPU timing⁽¹⁾

#	Characteristic	Symbol	Min	Max	Unit
1	eTPU Input Channel Pulse Width	t _{ICPW}	4	_	t _{cyc}
2	eTPU Output Channel Pulse Width	t _{OCPW}	2 ⁽²⁾		t _{cyc}

1. eTPU timing specified at V_{DD} = 1.08 V to 1.32 V, V_{DDEH} = 3.0 V to 5.5 V, V_{DD33} and V_{DDSYN} = 3.0 V to 3.6 V, T_A = T_L to T_H , and C_L = 200 pF with SRC = 0b00.

2. This specification does not include the rise and fall times. When calculating the minimum eTPU pulse width, include the rise and fall times defined in the slew rate control fields (SRC) of the pad configuration registers (PCR).



3.17.7 eMIOS timing

Table 46. eMIOS timing⁽¹⁾

#	# Symbol C		ymbol C Characteristic		Min. Value	Max. Value	Unit
1	t _{MIPW}	СС	D	eMIOS Input Pulse Width	4	—	t _{CYC}
2	t _{MOPW}	СС	D	eMIOS Output Pulse Width	1	—	t _{CYC}

1. eMIOS timing specified at f_{SYS} = 80 MHz, V_{DD} = 1.14 V to 1.32 V, V_{DDEH} = 4.5 V to 5.5 V, T_A = T_L to T_H , and C_L = 50 pF with SRC = 0b00.

3.17.8 DSPI timing

DSPI channel frequency support for the SPC564A80 MCU is shown in *Table 47*. Timing specifications are in *Table 48*.

System Clock (MHz)DSPI Use ModeMax. Usable Frequency (MHz)Note		Notes	
150	LVDS	37.5	Use sysclock /4 divide ratio.
150	Non-LVDS	18.75	Use sysclock /8 divide ratio.
120	LVDS	40	Use sysclock /3 divide ratio. Gives 33/66 duty cycle. Use DSPI configuration DBR=0b1 (double baud rate), BR=0b0000 (scaler value 2) and PBR=0b01 (prescaler value 3).
	Non-LVDS	20	Use sysclock /6 divide ratio.
80	LVDS	40	Use sysclock /2 divide ratio.
80	Non-LVDS	20	Use sysclock /4 divide ratio.

Table 47. DSPI channel frequency support

Table 48. DSPI timing $^{(1),(2)}$

#	Symbol		С	Characteristic	Characteristic Condition		Max.	Unit
1	t _{SCK}	СС	D	SCK Cycle Time ^{(3),(4),(5)}		24.4 ns	2.9 ms	_
2	t _{CSC}	СС	D	PCS to SCK Delay ⁽⁶⁾		22 ⁽⁷⁾	_	ns
3	t _{ASC}	СС	D	After SCK Delay ⁽⁸⁾		21 ⁽⁹⁾	_	ns
4	t _{SDC}	СС	D	SCK Duty Cycle		(½t _{SC})–2	(½t _{SC})+2	ns
5	t _A	сс	D	Slave Access Time (SS active to SOUT driven)		_	25	ns
6	t _{DIS}	сс	D	Slave SOUT Disable Time (SS inactive to SOUT High-Z or invalid)		_	25	ns
7	t _{PCSC}	СС	D	PCSx to PCSS time		4 ⁽¹⁰⁾	—	ns
8	t _{PASC}	СС	CC D PCSS to PCSx time			5 ⁽¹¹⁾	—	ns



r															
#	Sym	bol	С	Characteristic	Condition	Min.	Max.	Unit							
				Data	Setup Time for Inputs										
			D	Master (MTFE = 0)	V _{DDEH} =4.5–5.5 V	20	—								
		сс	D	Master(MTFE=0)	V _{DDEH} =3–3.6 V	23.5	—								
9	t _{SUI}		D	Slave		2	—								
	001				D	Master (MTFE = 1, CPHA = 0) ⁽¹²⁾		8	_	ns					
			D		V _{DDEH} =4.5–5.5 V	20	_								
			D	Master (MTFE = 1, CPHA = 1)	V _{DDEH} =3–3.6 V	23.5	—								
		CC	сс	cc		Data	Hold Time for Inputs			•					
										D	Master (MTFE = 0)		-4	_	
10 t _i	t _{HI}				D	Slave		7	—						
									D	Master (MTFE = 1, CPHA = 0) ⁽¹²⁾		21		ns	
			D	Master (MTFE = 1, CPHA = 1)		-4									
				Data	/alid (after SCK edge)			•							
					D	Master (MTFE = 0)	V _{DDEH} =4.5–5.5 V	_	5						
											D		V _{DDEH} =3–3.6 V	—	6.3
11	+	o cc	D	Slave	V _{DDEH} =4.5–5.5 V	_	25								
	t _{SUO}			SUO CC					CC	D	Slave	V _{DDEH} =3–3.6 V	_	27	ns
			D	Master (MTFE = 1, CPHA = 0)		_	21								
			D	Master (MTFE = 1, CPHA = 1)	V _{DDEH} =4.5–5.5 V	_	5								
			D		V _{DDEH} =3–3.6 V	_	6.3								
				Data	Hold Time for Outputs										
			D	Master (MTFE = 0)	V _{DDEH} =4.5–5.5 V	-5	—								
			D		V _{DDEH} =3 –3.6 V	-7.5	_								
12	t _{HO}	сс	D	Slave		5.5		ns							
			D	Master (MTFE = 1, CPHA = 0)		3	_	611							
			D	Master (MTFE = 1, CPHA = 1)	V _{DDEH} =4.5–5.5 V	-5	_	1							
			D		V _{DDEH} =3–3.6 V	-7.5									

Table 48. DSPI timing^{(1),(2)} (continued)

1. All DSPI timing specifications use the fastest slew rate (SRC = 0b11) on medium-speed pads. DSPI signals using slow pads have an additional delay based on the slew rate. DSPI timing is specified at $V_{DDEH} = 3$ to 3.6 V and $V_{DDEH} = 4.5$ to 5.5 V, $T_A = T_L$ to T_H , and $C_L = 50$ pF with SRC = 0b11.

2. Data is verified at f_{SYS} = 102 MHz and 153 MHz (100 MHz and 150 MHz + 2% frequency modulation).



- 3. The minimum DSPI Cycle Time restricts the baud rate selection for given system clock rate. These numbers are calculated based on two SPC564A80 devices communicating over a DSPI link.
- 4. The actual minimum SCK cycle time is limited by pad performance.
- 5. For DSPI channels using LVDS output operation, up to 40 MHz SCK cycle time is supported. For non-LVDS output, maximum SCK frequency is 20 MHz. Appropriate clock division must be applied.
- 6. The maximum value is programmable in DSPI_CTARx[PSSCK] and DSPI_CTARx[CSSCK].
- 7. Timing met when pcssck = 3(01), and cssck = 2 (0000).
- 8. The maximum value is programmable in DSPI_CTARx[PASC] and DSPI_CTARx[ASC].
- 9. Timing met when ASC = 2 (0000), and PASC = 3 (01).
- 10. Timing met when pcssck = 3.
- 11. Timing met when ASC = 3.
- 12. This number is calculated assuming the SMPL_PT bitfield in DSPI_MCR is set to 0b10.



Figure 23. DSPI classic SPI timing — master, CPHA = 0





Figure 24. DSPI classic SPI timing — master, CPHA = 1







Figure 25. DSPI classic SPI timing — slave, CPHA = 0









Figure 27. DSPI modified transfer format timing — master, CPHA = 0

Figure 28. DSPI modified transfer format timing — master, CPHA = 1





Figure 29. DSPI modified transfer format timing — slave, CPHA =0





Figure 30. DSPI modified transfer format timing — slave, CPHA =1



Figure 31. DSPI PCS strobe (PCSS) timing



3.17.9 eQADC SSI timing

			CLC	AD = 25 pF on all outputs. Pad o	drive strength se	t to maxin	num.					
#	Symbol		Symbol		Symbol		С	Rating	Min	Тур	Мах	Unit
1	f _{FCK}	СС	D	FCK Frequency ^{(2), (3)}	1/17		1/2	f _{SYS_CLK}				
1	t _{FCK}	СС	D	FCK Period (t _{FCK} = 1/ f _{FCK})	2		17	t _{SYS_CLK}				
2	t _{FCKHT}	CC	D	Clock (FCK) High Time	$t_{SYS_CLK} - 6.5$		_{9*} t _{SYS_CLK} + 6.5	ns				
3	t _{FCKLT}	CC	D	Clock (FCK) Low Time	$t_{SYS_CLK} - 6.5$		$_{8^{\star}}t_{SYS_CLK}$ + 6.5	ns				
4	t _{SDS_LL}	СС	D	SDS Lead/Lag Time	-7.5		7.5	ns				
5	t _{SDO_LL}	CC	D	SDO Lead/Lag Time	-7.5		7.5	ns				
6	t _{DVFE}	сс	D	Data Valid from FCK Falling Edge (t _{FCKLT+} t _{SDO_LL})	1			ns				
7	t _{EQ_SU}	сс	D	eQADC Data Setup Time (Inputs)	22			ns				
8	t_{EQ_HO}	CC	D	eQADC Data Hold Time (Inputs)	1			ns				

Table 49. eQADC SSI timing characteristics (pads at 3.3 V or at 5.0 V)⁽¹⁾

1. SS timing specified at f_{SYS} = 80 MHz, V_{DD} = 1.14 V to 1.32 V, V_{DDEH} = 4.5 V to 5.5 V, T_A = T_L to T_H , and C_L = 50 pF with SRC = 0b00.

2. Maximum operating frequency is highly dependent on track delays, master pad delays, and slave pad delays.

3. FCK duty is not 50% when it is generated through the division of the system clock by an odd number.



Figure 32. eQADC SSI timing



3.17.10 FlexCAN system clock source

lable	JU. FIEXU	AN engine system clock arriver timeshold			
#	Symbol	Characteristic	Value	Unit	
1	F _{CAN_TH}	FlexCAN engine system clock threshold	100	MHz	I

Table 50. FlexCAN engine system clock divider threshold

Table 51. FlexCAN engine system clock divider

System Frequency	Required SIU_SYSDIV[CAN_SRC] Value
<= F _{CAN_TH}	0 ^{(1),(2)}
> F _{CAN_TH}	1 ^{(2),(3)}

1. Divides system clock source for FlexCAN engine by 1.

2. System clock is only selected for FlexCAN when CAN_CR[CLK_SRC] = 1.

3. Divides system clock source for FlexCAN engine by 2.



4 Packages

4.1 ECOPACK[®]

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK[®] is an ST trademark.



4.2 Package mechanical data

4.2.1 LQFP176





Figure 33. LQFP176 package mechanical drawing

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Table 52. LQFP176 package mechanical data									
DEE	DATABOOK			МІ	MILLIMETERS ⁽¹⁾			INCHES	
REF.	ТҮР	MIN	МАХ	ТҮР	MIN	МАХ	ТҮР	MIN	МАХ
А						1.600			0.063
A1					0.050	0.150		0.002	
A2					1.350	1.450		0.053	0.057
b					0.170	0.270		0.007	0.011
С					0.090	0.200		0.004	0.008
D					23.900	24.100		0.941	0.949
Е					23.900	24.100		0.941	0.949
е				0.500			0.020		
HD					25.900	26.100		1.020	1.028
HE					25.900	26.100		1.020	1.028
L ⁽²⁾					0.450	0.750		0.018	0.030
L1				1.000			0.039		
ZD				1.250			0.049		
ZE				1.250			0.049		
CCC						0.080			0.003
ANGLE					0 ⁰	7 ⁰		0	7 ⁰

Table 52. LQFP176 package mechanical data

1. Controlling Dimension: MILLIMETER

2. L dimension is measured at gauge plane at 0.25 above the seating plane.



4.2.2 BGA208



 The terminal A1 corner must be identified on the top surface by using a corner chamfer, ink or metallized markings, or other feature of package body or integral heatslug. A distinguishing feature is allowable on the bottom surface of the package to identify the terminal A1 corner. Exact shape of each corner is optional.

Symbol		mm		inches ⁽¹⁾				
Symbol	Min	Тур	Max	Min	Тур	Max		
A ⁽²⁾			1.70			0.0669		
A1	0.30			0.0118				
A2		1.085			0.0427			
A3		0.30			0.0118			
A4			0.80			0.0315		
b ⁽³⁾	0.50	0.60	0.70	0.0197	0.0236	0.0276		

Table 53. LBGA208 mechanical data



)				
	mm		inches ⁽¹⁾				
Min	Тур	Max	Min	Тур	Max		
16.80	17.00	17.20	0.6614	0.6693	0.6772		
	15.00			0.5906			
16.80	17.00	17.20	0.6614	0.6693	0.6772		
	15.00			0.5906			
	1.00			0.0394			
	1.00			0.0394			
		0.20			0.0079		
		0.25			0.0098		
		0.10			0.0039		
	Min 16.80	Min Typ 16.80 17.00 16.80 17.00 16.80 17.00 16.80 17.00 16.80 17.00 16.80 17.00 16.80 17.00	mm Min Typ Max 16.80 17.00 17.20 16.80 17.00 17.20 16.80 17.00 17.20 16.80 17.00 17.20 16.80 17.00 17.20 16.80 17.00 0.20 0.20 0.25	Min Typ Max Min 16.80 17.00 17.20 0.6614 15.00 17.20 0.6614 16.80 17.00 17.20 0.6614 16.80 17.00 17.20 0.6614 16.80 17.00 17.20 0.6614 16.80 17.00 17.20 0.6614 15.00 11.00 10.00 10.00 1.00 0.20 0.25 10.02	mm inches ⁽¹⁾ Min Typ Max Min Typ 16.80 17.00 17.20 0.6614 0.6693 16.80 15.00 0.5906 0.5906 16.80 17.00 17.20 0.6614 0.6693 16.80 17.00 17.20 0.6614 0.6933 16.80 17.00 17.20 0.6614 0.6933 16.80 17.00 17.20 0.6614 0.6933 16.80 17.00 17.20 0.6614 0.6933 16.80 17.00 17.20 0.6614 0.6933 15.00 0.0394 0.0394 0.0394 1.00 0.20 0.25 0.25		

Table 53. LBGA208 mechanical data (continued)

1. Values in inches are converted from mm and rounded to 4 decimal digits.

 LBGA stands for Low profile Ball Grid Array.
 —Low profile: The total profile height (Dim A) is measured from the seating plane to the top of the component

The maximum total package height is calculated by the following methodology: A2 Typ+A1 Typ + $\sqrt{(A1^2+A3^2+A4^2 \text{ tolerance values})}$ — Low profile: 1.20mm < A \leq 1.70mm

3. The typical ball diameter before mounting is 0.60mm.

The tolerance of position that controls the location of the pattern of balls with respect to datums A and B. For each ball there is a cylindrical tolerance zone eee perpendicular to datum C and located on true position with respect to datums A and B as defined by e. The axis perpendicular to datum C of each ball 4. must lie within this tolerance zone.

5. The tolerance of position that controls the location of the balls within the matrix with respect to each other. For each ball there is a cylindrical tolerance zone fff perpendicular to datum C and located on true position as defined by e. The axis perpendicular to datum C of each ball must lie within this tolerance zone. Each tolerance zone fff in the array is contained entirely in the respective zone eee above. The axis of each ball must lie simultaneously in both tolerance zones.

4.2.3 **PBGA324**





Figure 34. PBGA324 package mechanical drawing

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14510 04.	i Benoz- puokage meonamen data								
Symbol		mm		inches					
Symbol	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.			
A ^{(1),(2),(3)}		1.720		1.620	1.720	1.820			
A1	0.270			0.350	0.400	0.450			
A2		1.320			1.320				
b	0.550	0.6000	0.650	0.550	0.600	0.650			
D	22.80	23.00	23.200	22.900	23.000	23.100			
D1		21.00			21.000				
E	22.800	23.000	23.200	22.900	23.000	23.100			
E1		21.000			21.000				
е	0.950	1.000	1.050	0.950	1.000	1.050			
f	0.875	1.000	1.125	0.875	1.000	1.125			
ddd			0.200			0.200			

Table 54.	PBGA324	package	mechanical	data
-----------	---------	---------	------------	------

1. Max mounted height is 1.77mm.Based on 0.35mm ball pad diameter. Solder paste is 0.15mm thickness and 0.35mm diameter.

2. PBGA stands for Plastic Ball Grid Array.

3. The terminal A1 corner must be identified on the top surface by using a corner chamfer, ink or metallized markings, or other feature of package body or integral heatslug. A distinguishing feature is allowable on the bottom surface of the package to identify the terminal A1corner. Exact shape of each corner is optional.


5 Ordering information

Table 55 shows the orderable part numbers for the SPC564A80 series.

Table 55.Order codes

Order code	Flash/SRAM	Package	Speed (MHz)
SPC564A74L7CFA	3 MB/160 KB	176LQFP	150
SPC564A74B2CFA	3 MB/160 KB	208LBGA	150
SPC564A74B4CFA	3 MB/160 KB	324PBGA	150
SPC564A80L7CFC	4 MB/192 KB	LQFP176	80
SPC564A80B2CFC	4 MB/192 KB	LBGA208	80
SPC564A80B4CFC	4 MB/192 KB	PBGA324	80
SPC564A80L7CFB	4 MB/192 KB	LQFP176	120
SPC564A80B2CFB	4 MB/192 KB	LBGA208	120
SPC564A80B4CFB	4 MB/192 KB	PBGA324	120
SPC564A80L7CFA	4 MB/192 KB	LQFP176	150
SPC564A80B2CFA	4 MB/192 KB	LBGA208	150
SPC564A80B4CFA	4 MB/192 KB	PBGA324	150
SPC564A80H1EFA	4 MB/192 KB	KGD	150





Figure 35. Product code structure



6 **Document revision history**

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Date	Revision	Changes
23-Feb-2009	1	Initial release
09-Dec-2009	2	Maximum device speed is 145 MHz (was 150 MHz) 16-entry Memory Protection Unit (MPU). Was incorrectly listed as 8-entry. 288-ball BGA package deleted Feature details section added Changes to signal summary table: - Added ANY function to AN[10] - Added ANW function to AN[8] Changes to 208 ball BGA ballmap: - A12 is AN12-SDS (was AN12) - A15 is VRC33 (was VDD33) - B12 is AN13-SDO (was AN13) - C12 is AN14SDI (was AN14) - C13 is AN15-FCK (was AN15) - D1 is VRC33 (was VDD33) - F13 is VDDEH6AB (was VDDEH6) - H13 is GPIO99 (was PCSA3) - J15 is GPIO98 (was PCSA2) - K4 is now VDDEH1AB (was VDDEH1) - N6 is now VRC33 (was VDD33) - P6 is now NC - T13 is VDDEF6X (was ND33) - P6 is now NC - T13 is VDDE5 (was NC) Changes to 324 ball BGA ballmap: - A6 is VDDA (was VDDA1) - A7 is VSSA (was VDA1) - A15 is VSSA (was VSA0) - A16 is AN12_SDS (was AN12) - A17 is MDO1_ETPUA27O (was MDO1)) - A19 is VMO8_ETPUA27O (was MDO1) - A19 is VRC33 (was VDD33) - B15 is VSA3 (was VD33) - B15 is VSA3 (was VD33) - B15 is VSA3 (was VDA3) - B16 is AN13_SDO (was AN13) - B17 is MD04_ETPUA20 (was MD07) - B19 is MD04_ETPUA20 (was MD04) - B22 is NIC (was VDEF7)

Date	Revision	Changes
		- C4 is VDD (was VDDEH1A)
		- C15 is VDDA (was VDDA0)
		- C16 is AN14_SDI (was AN14)
		- C17 is MDO5_ETPUA4O (was MDO5)
		- C21 is NIC1 (was VDDE7)
		– D15 is VDDEH7 (was VDDEH9)
		 – D16 is AN15_FCK (was AN15)
		- D17 is MDO6_ETPUA13O (was MDO6)
		– D20 is NIC (was VDDE7)
		– E19 is NIC (was VDDE7)
		– E22 is NIC (was NC)
		– F19 is NIC (was VDDE7)
		 H4 is VDDEH1AB (was VDDEH1A)
		 H19 is VDDEH6AB (was VDDEH10)
		– J14 is NIC (was VDDE7)
		- K19 is GPIO99 (was PCSA3)
		– M9 is VDDE2 (was VDD2)
		 M21 is GPIO98 (was PCSA2)
		– M22 is VDDREG (was NC)
		– N22 is NIC (was NC)
09-Dec-2009	2	 P2 is ADDR17 (was ADD17)
00 000 2000	2	– P4 is VRC33 (was VDD33)
		 R3 is VDDE-EH (was VDDE2)
		 T21 is VSS (was VRCVSS)
		– T22 is VSS (was VSSPLL)
		– U19 is VDDEH6AB (was VDDEH6A)
		– W2 is VDDE-EH (was VDDE2)
		– W7 is VRC33 (was VDD33)
		 W14 is VDDEH4AB (was VDDEH4B)
		– W21 is NIC (was VRC33)
		– Y22 is VRC33 (was VDD33)
		– AB22 is VSS (was VSSPLL)
		Recommended operating characteristics for power transistor updated
		Pad current specifications updated
		LVDS pad specifications updated. SRC does not apply to common mode voltage.
		Temperature sensor electrical characteristics added
		eQADC electrical characteristics updated with VGA gain specs
		Pad AC specifications updated
		Definition for RDY signal added to signal details
		V _{STBY} maximum is 5.5 V (was listed incorrectly as 6.0 V)
		I _{MAXA} maximum is 5 mA (was TBD)
		Analog differential input functions added to AN0–AN7 in signal summary



Date	Revision	Changes
02-Apr-2010	3	Internal release. Changes to Signal Properties table (changes apply to Revision 2 and later devices: EBI changes: - WE_BE[2] (A2) and CAL_WE_BE[2] (A3) signals added to CS[2] (PCR 2) - WE_BE[3] (A2) and CAL_WE_BE[3] (A3) signals added to CS[3] (PCR 3) Calibration bus changes: - CAL_WE[3/BE[2] (A2) signal added to CAL_CS[2] (PCR 338) - CAL_WE[3/BE[2] (A2) signal added to CAL_CS[3] (PCR 339) - CAL_ALE (A1) added to CAL_ADDR[15] (PCR 340) eQADC changes: - AN[8] and AN[38] pins swapped. AN[8] Is now on pins 9 (176-pin), B3 (208-ball) and D6 (324-ball). AN[8] was on C5 (324-ball) on previous devices. AN[38] Is now on C5 (324-ball). AN[8] was on pins 9 (176-pin), B3 (208-ball) and D6 (324-ball). AN[8] was on pins 9 (176-pin), B3 (208-ball) and D6 (324-ball). AN[38] was on pins 9 (176-pin), B3 (208-ball) and D6 (324-ball) on previous devices. - ANZ function added to AN11 pin Reaction channels added to ETPU_A[14] (PCR 128) - RCH0_A (A3) added to ETPU_A[12] (PCR 134) - RCH0_C (A2) added to ETPU_A[12] (PCR 135) - RCH1_A (A2) added to ETPU_A[13] (PCR 123) - RCH1_A (A2) added to ETPU_A[16] (PCR 123) - RCH1_C (A2) added to ETPU_A[16] (PCR 130) - RCH3_A (A2) added to ETPU_A[16] (PCR 130) - RCH4_A (A2) added to ETPU_A[17] (PCR 131) - RCH4_A (A2) added to ETPU_A[17] (PCR 132)) - RCH4_B (A2) added to ETPU_A[18] (PCR 132)) - RCH4_B (A2) added to ETPU_A[19] (PCR 133) - RCH4_B (A2) added to ETPU_A[28] (PCR 142) - RCH5_B (A2) added to ETPU_A[28] (PCR 143) - RCH5_B (A2) added to ETPU_A[28] (PCR 143) - RCH5_B (A2) added to ETPU_A[28] (PCR 143) - RCH5_B (A2) added to EMIOS[2] (PCR 183) - RCH3_B (A2) added to EMIOS[2] (PCR 183) - RCH3_B (A2) added to EMIOS[4] (PCR 189) - RCH3_B (A2) added to EMIOS[4] (PCR 189) - RCH3_B (A2) added to EMIOS[4] (PCR





Table 56. Re Date	Revision	story (continued) Changes
Baile		
		Added information to AC timings section: - New section added: Reset and configuration pin timing
		 New section added: External interrupt timing (IRQ pin) New section added: eTPU timing
		 Added Nexus debug port operating frequency table to Nexus timings section Added external bus interface maximum operating frequency table and calibration bus interface maximum operation frequency table
		 Added FlexCAN system clock source section
		Changes to Power management control (PMC) and power on reset (POR) electrical specifications:
		 Max value for parameter 2 (vddreg) is 5.25 V (was 5.5 V)
02-Apr-2010	3	Updated "Core voltage regulator controller external components preferred configuration" diagram.
(cont)	(cont)	Changes to DC electrical specifications table:
		 Slew rate on power supply pins (system requirement) changed to 25 V/ms (was 50 V/ms)
		Throughout the document the maximum frequency is now 150 MHz (was 145 MHz)
		Changes to DC electrical specifications:
		 Parameter classifications added
		 V_{DDREG} max value changed to 5.25 V (was 5.5 V)
		$-$ V _{OH_LS} min value changed to 2.0 V (was 2.7 V) with a load current of 0.5 mA
		$- V_{OL_{LS}}$ max value changed to 0.6 V (was 0.2*V _{DDEH}) with load current of 2 mA
		– V_{INDC} min value changed to V_{SSA} -0.3 (was V_{SSA} -1.0)
		 V_{INDC} max value changed to V_{DDA}+0.3 (was V_{DDA}+1.0)
		Added new section: Configuring SRAM wait states
		 VRCCTL external circuit updated.
		Updates to Nexus timings:
		 t_{MDOV} max value changed to 0.35 (was 0.2)
		 t_{MSEOV} max value changed to 0.35 (was 0.2)
		 t_{EVTOV} max value changed to 0.35 (was 0.2)
	4	Updates to DC electrical specifications:
		 V_{STBY} min value changed to 0.95 V (was 0.9 V)
		 V_{STBY} has two ranges—for regulated mode and unregulated mode
		Correction to PLLMRFM electrical specifications:
01 Oct 0010		 V_{DDPLL} range is from 1.08 V to 3.6 V (was 3.0 V to 3.6 V.
01-Oct-2010		Updates to pad AC specifications:
		 Specs with drive load = 200 pF deleted. DSC (drive strength control) values range from 10 – 50 pF.
		 I/O pad average I_{DDE} specifications updated (fast pad specs only)
		 I/O pad V_{RC33} average I_{DDE} specifications (fast pad specs only)
		Updates to Reset and configuration pin timings:
		 Footnote added: RESET pulse width is measured from 50% of the falling edge to 50% of the rising edge.
		- Timings are specified at V_{DD} = 1.14 V to 1.32 V (was 1.08 V to 1.32 V).



Date	Revision	Changes
01-Oct-2010 (cont)	4 (cont)	Updates to EBI timings: - Note added to t _{AAI} : When CAL_TS is used as CAL_ALE the hold time is 1 ns instead of 1.5 ns. - Correction: maximum calibration bus interface operating frequency is 66 MHz for all port configurations. - VDDE range in footnote 1 corrected to read, "External Bus and Calibration bus timing specified at f _{SYS} = 150 MHz and 100 MHz, VDD = 1.14 V to 1.32 V, VDDE = 3 V to 3.6 V (unless stated otherwise)" (VDDE range was 1.62 V to 3.6 V) Correction to IEEE 1149.1 timings: - SRC value in footnote 1 corrected to read, "JTAG timing specified at VDD = 1.14 V to 1.32 V, VDDEH = 4.5 V to 5.5 V with multi-voltage pads programmed to Low- Swing mode, TA = TL to TH, and CL = 30 pF with DSC = 0b10, SRC = 0b11." (SRC value was 0b00) Correction to External interrupt timing (IRQ pin) timings: - Timings are specified at V _{DD} = 1.14 V to 1.32 V (was 1.08 V to 1.32 V). Update to DSPI timings: - Some of the timing parameters can vary depending on the value of V _{DDE} . For these parameters, ranges are now defined for two ranges of V _{DDE} . Change in signal name notation for DSPI, CAN and SCI signals: - DSPI: PCS_x[n] is now DSPL_x_PCS[n] SOUT_x is now DSPL_x_SOUT SIN_x is now DSPL_x_SIN SCK_x is now CAN_x_TX CNTXx is now CAN_x_TX CNTXx is now CAN_x_TX CNTXx is now CAN_x_TX Updates to DC electrical specifications: - Slew rate on power supply pins specification changed to 25 V/ms (was 50 V/ms) V _{OH_LS} min spec changed to 2.0 V at 0.5 mA (was 2.7 V at 0.5 mA) Updated I/O pad V _{RC33} current specifications Corrections to Nexus timing: - Maximum Nexus debug port operating frequency is 40 MHz in all configurations - To route Nexus to MDO, clear NPC_PCR[NEXCFG] (formerly this was documented as NPC_PCR[CAL] - To route Nexus to CAL_MDO, set NPC_PCR[NEXCFG]=1 (formerly this was documented as NPC_PCR[CAL]
10-Feb-2011	5	 Minor editorial updates. Re-organized the first few subsections of the "Overview" section. Added ECSM to the block diagram. Added information on the REACM, SIU, and ECS modules to the "Block summary" section.



Revision Date Changes Added DATA[0:15] to V_{DDE5} in the "signal properties" table. - Updated VSTBY parameters in the "Power/ground segmentation" table. Updated the parameter symbols and classifications throughout the document. Updated footnote instances in the "Absolute maximum ratings" table. - Removed I_{MAXA} footnote in the "Absolute Maximum Ratings" table. Updated the format of the "EMI (electromagnetic interference) characteristics" table. - Removed the footnote on V_{DDREG} in the "Power management control (PMC) and power on reset (POR) electrical specifications" table. Updated values for Vbg, Idd3p3, Por3.3V_r, Por3.3V_f, Por5V_r, and Por5V_f in the "PMC electrical characteristics" table. Updated "Bandgap reference supply voltage variation" in the "PMC Electrical Characteristics" table. Removed the "VRC electrical specifications" table as it contained redundant information. Updated VCE_{SAT} and V_{BE}in the "Recommended power transistors" operating characteristics" table. Updated VIH_LS in the "DC electrical specifications" table. Updated the V_{OH LS} min value in the "DC electrical specifications" table. Updated I_{DDSTBY} and I_{DDSTBY150} in the "DC electrical specifications" table. Updated the I_{DDA}/I_{REF}/I_{DDREG} max value in the "DC electrical specifications" table. - Updated IACT F, IACT MV PU, IACT MV PD, RPUPD5K, RPUPDMTCH, and footnotes in the "DC electrical specifications" table. 10-Feb-2011 5 - Updated Medium pad type I_{DD33} values in the "I/O pad V_{BC33} average I_{DDE} (cont) (cont) specifications" table. Updated values for V_{OD} in the "DSPI LVDS pad specification" table. Removed the footnotes from the "DSPI LVDS pad specifications" table. Removed the redundant "XTAL Load Capacitance" parameter instance from the "PLLMRFM electrical specifications" table. Updated footnotes in the "PLLMRFM electrical specifications" table. - Updated values for OFFNC and GAINNC in the "eQADC conversion specifications (operating)" table. Added DIFF_{max}, DIFF_{max2}, DIFF_{max4}, and DIFF_{cmv} parameters to the "eQADC conversion specifications (operating)" table. Added the maximum operating frequency values in the "Cutoff frequency for additional SRAM wait state" table. Updated multiple entries in the "APC, RWSC, WWSC settings vs. frequency of operation" table. Removed footnote in the "APC, RWSC, WWSC settings vs. frequency of operation" table. Updated the Typical values for $T_{dwprogram}$, $T_{pprogram}$, and $T_{16kpperase}$, and updated the Initial Max values for T_{128kpperase} and T_{256kpperase} in the "Flash program and erase specifications" table. Changed the voltage in the "Pad AC specifications" table title from 4.5 V to 5.0 V. Added the maximum LH/HL output delay values for pad type MultiV in the "Pad AC specifications (V_{DDE} = 3.3 V)" table.



Date	Revision	Changes
03-Feb-2012	6	 Minor editorial changes. In Section 1.4: SPC564A80 feature list, moved "24 unified channels" after "1 x eMIOS". In Table 4 updated the following rows: DSPL_D_SCK /GPIO [98] -Changed "-" to CS[2] DSPL_D_SCK /GPIO [98] -Changed "-" to CS[3]. In Table 12 Column "Value" added conditional text. In Table 21 made the following changes: -For the value "VOL_S" parameter changed from "Slow/ medium/multi-voltage pad I/O output low voltage" to "Slow/medium pad I/O output low voltage". -Added a new row for "IDDSTBY27". -For row "IDDSTBY (operating current 0.95 -1.2V)" added max value "100" and changed tpy value from "125" to "35". -For row "IDDSTBY (operating current 2 - 5.5V)" added max value "2000", changed tpy value from "150" to "790", C cell changed from "T to "P" and for symbol "IDDSTBY (operating current 2 - 5.5V)" added max value "2000", changed tpy value from "1050" to "760", C cell changed from "T to "P" and for symbol "IDDSTBY (operating current 2 - 5.5V)" added max value "2000", changed tpy value from "1050" to "760", C cell changed from "T to "P". -Removed note 9 and note 10 (Characterization based capability) from symbol "VoL_HS". Splitted Table 28: eQADC conversion specifications (operating) into Table 29: eQADC differential ended conversion specifications (operating) In Table 30: eQADC differential ended conversion specifications (operating) In Table 31: Cutoff frequency for additional SRAM wait state made the following changes: -Added the note of DIFF_{cmv} on all of the DIFF specs. Min value changed from (YRH-VRL)/2-5% to (YRH+VRL)/2-5% and max value changed ifm (VRH-VRL)/2-5% to (VRH+VRL)/2-5% or 01FFcmv. In Table 31: Cutoff frequency changed from "Si" to "88" and "150" to "153". In Section 3.13: Configuring SRAM wait states, changed text from "SPC564A80 4M Microcontroller Reference Manual " to "device reference manual". In Table 33: Flash poperating Frequency (MH



Date	Revision	Changes
03-Feb-2012 (cont)	6 (cont)	 Added Table 17: SPC564A80 External network specification. Updated Figure 8: Core voltage regulator controller external components preferred configuration. Changed External Network Parameter Ce min value to "3*2.35 μ F+5 μ F" from "2*2.35 μ F+5 μ F" in Table 17: SPC564A80 External network specification. Changed Trans. Line (differential Zo) unit to Ω from W in Table 25: DSPI LVDS pad specification.
07-Mar-2012	7	- Update table footnotes in Table 21: DC electrical specifications.
21-Mar-2012	8	 Minor editorial changes. In Section 1.4, "SPC564A80 feature list, moved "24 unified channels" after "1 x eMIOS". In Table 4, "SPC564A80 signal properties"/Column "Name" updated the following rows: DSPL_D_SCK /GPIO [98] -Changed "-" to CS[2] DSPL_D_SIN /GPIO[99] -Changed "-" to CS[3]. In Table 12, "Thermal characteristics for 324-pin PBGA"/ Column "Value" added conditional text. In Table 21, "DC electrical specifications" made the following changes: For the value "VoL_S" parameter changed from "Slow/ medium/multi-voltage pad I/O output low voltage" to "Slow/medium pad I/O output low voltage". -Added a new row for "IDDSTBY27". For row "IDDSTBY (operating current 0.95 -1.2V)" added max value "100" and changed typ value from "135" to "45". For row "IDDSTBY (operating current 2 - 5.5V)" added max value "100" and changed typ value from "1050" to "760", C cell changed from "T" to "P" and for symbol "IDDSTBY to "760", C cell changed from "T" to "P". Removed note 9 and note 10 (Characterization based capability) from symbol "VoL_HS". Splitted Table 28, "eQADC conversion specifications (operating)" and Table 30, "eQADC differential ended conversion specifications (operating)" and Table 30, "eQADC differential ended conversion specifications (operating)" and Table 30, "eQADC differential ended conversion specifications (operating)" and Table 30, "eQADC differential ended conversion specifications (operating)" and Table 30, "eQADC differential ended conversion specifications (operating)" and the following changes: -Added the note of DIFF_{CTW} on all of the DIFF specs. Min value changed from (VRH-VRL)/2-5% to (VRH+VRL)/2-5% and max value changed from (VRH-VRL)/2-5% to (VRH+VRL)/2-5% and max value changed from (VRH-VRL)/2-5% to (VRH+VRL)/2-5% and max value changes: -Added note "Max frequencies including 2% PLL FM". Max operating frequency changed from "98" and "150" to "153"

 Table 56.
 Revision history (continued)



Date	Revision	Changes
21-Mar-2012	8 (cont.)	 In <i>Table 32, "APC, RWSC, WWSC settings vs. frequency of operation"</i> Added note for "Max Flash Operating Frequency(MHz). Changed values from 30, 60,120, 150 to 20,61,123, 153 respectively in Max Flash Operating Frequency (MHz). In <i>Table 33</i>,a, <i>"Flash program and erase specifications</i>"dded two parameter "T_{psrt}" and "T_{esrt}". In <i>Table 41, "External Bus Interface maximum operating frequency</i>", replacedthe <= symbol in notes with ≤ Added note "Refer to table DSPI timing for the numbers" in all the figures under <i>Section 3.17.8, "DSPI timing</i>. In <i>Table 55</i>, changed LBGA208 to MAPBGA and changed all packages to 123XXXX format. Added <i>Table 17, "SPC564A80 External network specification</i>". Updated <i>Figure 8</i>. Changed External Network Parameter Ce min value to "3*2.35 µ F+5 µ F" from "2*2.35 µ F+5 µ F" in <i>Table 17, "SPC564A80 External network specification</i>". Changed Trans. Line (differential Zo) unit to Ω from W in <i>Table 25, "DSPI LVDS pad specification</i>".
18-Sep-2013	9	- Updated Disclaimer.



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